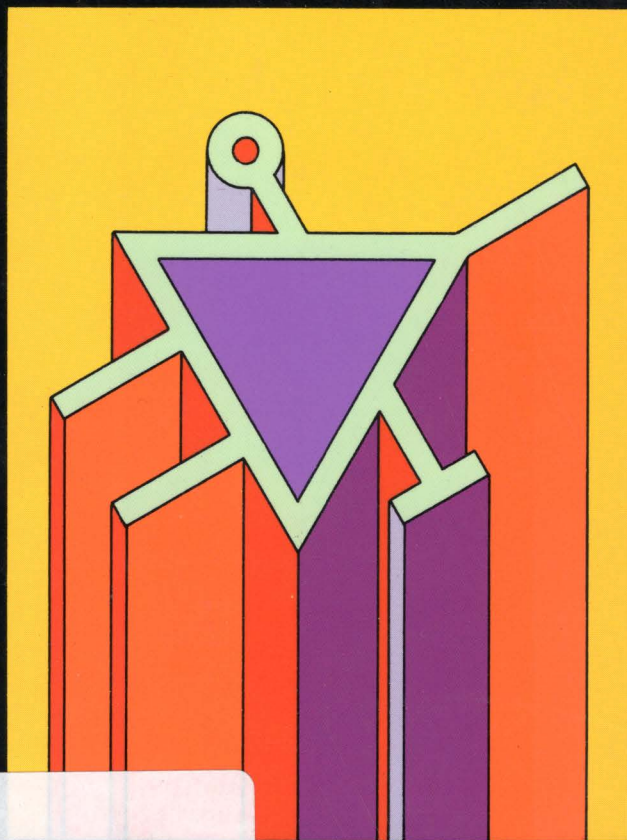


CMOS LINEAR - 3rd EDITION

CMOS LINEAR

3rd EDITION



000469

RYSTON Electronics

RYSTON
ELECTRONICS
spol. s r.o.
Křižkova ulice II 1062
147 00 Praha 4

CS-THOMSON
MICROELECTRONICS

CMOS LINEAR

MARCH 1992

USE IN LIFE SUPPORT DEVICES OR SYSTEMS MUST BE EXPRESSLY AUTHORIZED

SGS-THOMSON PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF SGS-THOMSON Microelectronics. As used herein:

1. Life support devices or systems are those which (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided with the product, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can reasonably be expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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INTRODUCTION

SGS-THOMSON Microelectronics can now offer you a complete range of CMOS LINEAR devices including :

- OPERATIONAL AMPLIFIERS
- COMPARATORS
- TIMERS

This family of monolithics CMOS circuits provides the designers with high performance operation at low supply current and very good speed to power ratio.

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Type Number	Function	Page Number
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PRODUCT GUIDE

THE CMOS PRODUCTS RANGE

1 - CMOS OPERATIONAL AMPLIFIERS

3 CONFIGURATIONS

TS271 SINGLE
TS27X2 DUAL
TS27X4 QUAD

3 PACKAGE TYPES

N DIP8 / DIP14
D SO8 / SO14

3 OFFSET VOLTAGE SELECTIONS

TS27X 10mV max.
TS27XA 5mV max.
TS27XB 2mV max.

SUPPLY CURRENT OPTIONS

TS271 PROGRAMMABLE
TS27X HIGH 1mA
TS27MX MEDIUM 150µA
TS27LX LOW 10µA

3 TEMPERATURE RANGES

TS27XC 0 to + 70°C
TS27XI - 40 to + 105°C
TS27XM - 55 to + 125°C

S90CMOS-01

2 - CMOS COMPARATORS

LOW POWER COMPs

TS372 DUAL
TS374 QUAD

MICROPOWER COMPs

TS3702 DUAL } Push Pull
TS3704 QUAD } Output
TS393 DUAL } Open Drain
TS339 QUAD } Output

3 TEMPERATURE RANGES

TS37XC / TS370XC / TS339C / TS393C 0 to + 70°C
TS37XI / TS370XI / TS339I / TS393I - 40 to +105°C
TS37XM / TS370XM / TS339M / TS393M - 55 to +125°C

3 PACKAGE TYPES

N DIP8 / DIP14
D SO8 / SO

S90CMOS-02

3 - CMOS TIMERS

2 CONFIGURATIONS

TS555 SINGLE
TS556 DUAL

3 TEMPERATURE RANGES

TS55XC 0 to + 70°C
TS55XI - 40 to +105°C
TS55XM - 55 to +125°C

3 PACKAGE TYPES

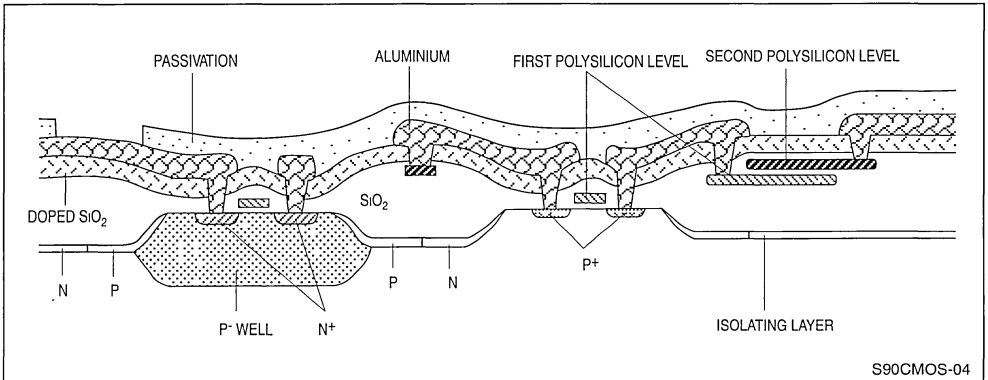
N DIP8 / DIP14
D SO8 / SO14

S90CMOS-03

TECHNOLOGY

1 - PROCESS

Figure 1.



S90CMOS-04

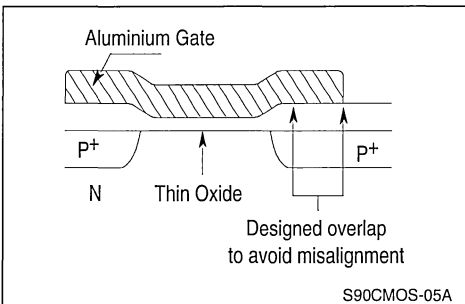
The SGS-THOMSON Microelectronics CMOS process uses for Standard Linear Products a 4µm P Well technology with dual layer polysilicon gate.

This process offers major advantages compared to traditional ones:

- The phosphorus doped polysilicon gate traps free sodium ions providing **ultra stable drift-free input MOS transistors**.
- Self aligned gate reduces **the gate-drain capacitance** and meanwhile **increases the speed** of the MOS transistors.

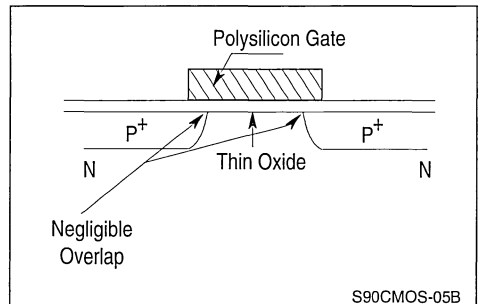
2. SELF ALIGNED GATE

Figure 2A : Drain/source diffusion is made **before** the gate's etching.



S90CMOS-05A

Figure 2B : Drain/source diffusion is made **after** the gate's etching. The gate is used as a mask during the diffusion.



S90CMOS-05B

These figures illustrate the differences between metal gate and polysilicon gate MOS transistors. The overlap which causes capacitance is considerably reduced and becomes negligible.

The self aligned polysilicon gate reduces the parasitic capacitance of the structure and also reduces the number of critical mask alignments which leads to cost reduction.

CMOS OPERATIONAL AMPLIFIERS

TS271 - TS27X2 series - TS27X4 series

FEATURES				
• VOLTAGE RANGE FROM 3 to 16V (MAX=18V)				
• SINGLE SUPPLY VOLTAGE				
• ADAPTABLE BIAS CURRENT				
• EXTREMELY LOW INPUT CURRENT (1pA)				
• OFFSET VOLTAGE STABILITY (0.7 μ V/°C)				
• ADAPTABLE BANDWIDTH AND SLEW RATE				
	TS27LX	TS27MX	TS27X	UNIT
Svo	0.04	0.6	5.5	V/ μ s
GBP	0.1	1	3.5	MHz
• DYNAMIC BEHAVIOUR - TS271 / TS272 / TS274 - TS271 / TS27M2 / TS27M4				
• SYMETRICAL OUTPUT CURRENTS				
• LOW OUTPUT DYNAMIC IMPEDANCE				
• LINEARITY OF THE TRANSFERT FUNCTION (IN SINGLE OR DUAL POWER SUPPLY UTILISATION)				
• EXCELLENT PHASE MARGIN (DUE TO INTERNAL COMPENSATION)				
• OFFSET NULL CAPABILITY (TS271)				
• LARGE AND CONTINUOUS PROGRAMMATION RANGE (FROM 1 μ A UP TO 200 μ A) (TS271)				

BENEFITS
• ALLOWS DESIGN IN WIDE APPLICATION RANGE (FROM BATTERY OPERATION TYPE UP TO USUAL 12V SUPPLY VOLTAGE TYPE)
• AVOIDS NEGATIVE TYPE POWER SUPPLY
• ALLOWS BEST CONSUMPTION/SPEED RATIO (COST EFFECTIVENESS)
• MINIMIZES STATIC ERROR IN HIGH IMPEDANCE APPLICATIONS
• ANSWERS TO INSTRUMENTATION MARKET NEEDS WITH GENERAL PURPOSE TYPE PRICING
• MORE PERFORMANCE REGARDING TO CONSUMPTION (0.35 MHz/mW) ALLOWS SMALL SIZE POWER SUPPLY, LESS HEAT DISSIPATION, HIGHER RELIABILITY
• EASY REPLACEMENT OF – JFET OPERATIONAL AMPLIFIERS FAMILY – BIPOLAR OPERATIONAL AMPLIFIERS FAMILY WITH BETTER BEHAVIOUR
• ALLOWS USE OF SAME LOADS ON BOTH SIDES OF THE OUTPUT
• REDUCES SETTLING TIME
• LOWERS GAIN DISPERSION IN OPEN-LOOP OPERATION MODE
• IMPROVES THE STABILITY FOR HIGH CAPACITANCE LOAD (MORE THAN 100pF)
• MINIMIZES STATIC ERROR (WHEN USED IN COMPARATOR MODE)
• ALLOWS HIGH OPTIMISATION FOR ALL TYPES OF APPLICATIONS

LOW POWER CMOS COMPARATORS

TS372 - TS374

FEATURES
• SINGLE or DUAL SUPPLY OVER A WIDE RANGE (3 to 16 V or ± 1.5 to $\pm 8V$)
• VERY LOW SUPPLY CURRENT : 150 μA / comparator
• FAST RESPONSE TIME : 200 ns WITH TTL INPUT
• VERY LOW INPUT BIAS CURRENT Typ : 1pA
• LM393 - LM339 PIN to PIN COMPATIBLE
• OPEN DRAIN CMOS OUTPUT

BENEFITS
• WIDE APPLICATION RANGE BATTERY OPERATION ABILITY
• POWER SAVING HALF OF LM339
• 1.5 \times LM339 SPEED
• MINIMIZED STATIC ERROR
• EASY OF UPGRADE IN REDESIGN
• LOGIC "AND" / "OR" FUNCTION POSSIBILITY

MICROPOWER CMOS COMPARATORS

TS393 - TS339

FEATURES
• SINGLE or DUAL SUPPLY OVER A WIDE RANGE (3 to 16 V or ± 1.5 to ± 8 V)
• EXTREMELY LOW SUPPLY CURRENT : $10 \mu\text{A}$ / Comparator
• FAST RESPONSE TIME : $1.1 \mu\text{s}$ WITH TTL INPUT
• VERY LOW INPUT BIAS CURRENT Typ : 1pA
• LM393 / 339 PIN TO PIN COMPATIBLE
• OPEN DRAIN CMOS OUTPUT

BENEFITS
• WIDE APPLICATION RANGE BATTERY OPERATION ABILITY
• 20 TIMES LESS THAN BIPOLAR LM339/393
• CONSUMPTION / SPEED RATIO OPTIMISATION
• MINIMIZED STATIC ERROR
• EASY OF UPGRADE IN REDESIGN
• LOGIC "AND" / "OR" FUNCTION POSSIBILITY

TS3702 - TS3704

FEATURES
• SINGLE or DUAL SUPPLY OVER A WIDE RANGE (3 to 16 V or ± 1.5 to ± 8 V)
• EXTREMELY LOW SUPPLY CURRENT : $10 \mu\text{A}$ / Comparator
• FAST RESPONSE TIME : $1.1 \mu\text{s}$ WITH TTL INPUT
• VERY LOW INPUT BIAS CURRENT Typ : 1pA
• LM393 / 339 PIN TO PIN COMPATIBLE
• PUSH PULL CMOS OUTPUT

BENEFITS
• WIDE APPLICATION RANGE BATTERY OPERATION ABILITY
• 20 TIMES LESS THAN BIPOLAR LM339/393
• CONSUMPTION / SPEED RATIO OPTIMISATION
• MINIMIZED STATIC ERROR
• EASY OF UPGRADE IN REDESIGN
• NO EXTERNAL PULL UP RESISTOR REQUIRED

CMOS TIMERS

TS555 - TS556

FEATURES
<ul style="list-style-type: none"> • SINGLE SUPPLY OVER A WIDE RANGE 2 to 16V
<ul style="list-style-type: none"> • VERY LOW SUPPLY CURRENT : 100 μA typ. / Timer
<ul style="list-style-type: none"> • VERY HIGH SPEED 2.7 MHz max. ASTABLE FREQUENCY
<ul style="list-style-type: none"> • NE555 / NE556 PIN-TO-PIN COMPATIBLE
<ul style="list-style-type: none"> • SUPPLY CURRENT SPIKES REDUCED DURING OUTPUT TRANSITIONS

BENEFITS
<ul style="list-style-type: none"> • WIDE APPLICATION RANGE
<ul style="list-style-type: none"> • 30 TIMES LESS THAN BIPOLAR NE555/6
<ul style="list-style-type: none"> • 30 TIMES FASTER THAN BIPOLAR NE555/6
<ul style="list-style-type: none"> • EASE OF UPGRADE IN REDESIGN
<ul style="list-style-type: none"> • LOWER DECOUPLING CAPACITORS REQUIRED

CMOS CROSS REFERENCE

1 - CMOS OPERATIONAL AMPLIFIERS

TEXAS INSTRUMENTS	SGS-THOMSON REPLACEMENT
TLC271ACD	TS271ACD
TLC271ACP	TS271ACN
TLC271AID	TS271AID
TLC271AIP	TS271AIN
TLC271BCD	TS271BCD
TLC271BCP	TS271BCN
TLC271BID	TS271BID
TLC271BIP	TS271BIN
TLC271CD	TS271CD
TLC271CP	TS271CN
TLC271ID	TS271ID
TLC271IP	TS271IN
TLC272ACD	TS272ACD
TLC272ACP	TS272ACN
TLC272AID	TS272AID
TLC272AIP	TS272AIN
TLC272BCD	TS272BCD
TLC272BCP	TS272BCN
TLC272BID	TS272BID
TLC272BIP	TS272BIN
TLC272CD	TS272CD
TLC272CP	TS272CN
TLC272ID	TS272ID
TLC272IP	TS272IN
TLC274ACD	TS274ACD
TLC274ACN	TS274ACN
TLC274AID	TS274AID

TEXAS INSTRUMENTS	SGS-THOMSON REPLACEMENT
TLC274AIN	TS274AIN
TLC274BCD	TS274BCD
TLC274BCN	TS274BCN
TLC274BID	TS274BID
TLC274BIN	TS274BIN
TLC274CD	TS274CD
TLC274CN	TS274CN
TLC274ID	TS274ID
TLC274IN	TS274IN
TLC27L2ACD	TS27L2ACD
TLC27L2ACP	TS27L2ACN
TLC27L2AID	TS27L2AID
TLC27L2AIP	TS27L2AIN
TLC27L2BCD	TS27L2BCD
TLC27L2BCP	TS27L2BCN
TLC27L2BID	TS27L2BID
TLC27L2BIP	TS27L2BIN
TLC27L2CD	TS27L2CD
TLC27L2CP	TS27L2CN
TLC27L2ID	TS27L2ID
TLC27L2IP	TS27L2IN
TLC27L4ACD	TS27L4ACD
TLC27L4ACN	TS27L4ACN
TLC27L4AID	TS27L4AID
TLC27L4AIN	TS27L4AIN
TLC27L4BCD	TS27L4BCD
TLC27L4BCN	TS27L4BCN

1 - CMOS OPERATIONAL AMPLIFIERS (continued)

TEXAS INSTRUMENTS	SGS-THOMSON REPLACEMENT
TLC27L4BID	TS27L4BID
TLC27L4BIN	TS27L4BIN
TLC27L4CD	TS27L4CD
TLC27L4CN	TS27L4CN
TLC27L4ID	TS27L4ID
TLC27L4IN	TS27L4IN
TLC27M2ACD	TS27M2ACD
TLC27M2ACP	TS27M2ACN
TLC27M2AID	TS27M2AID
TLC27M2AIP	TS27M2AIN
TLC27M2BCD	TS27M2BCD
TLC27M2BCP	TS27M2BCN
TLC27M2BID	TS27M2BID
TLC27M2BIP	TS27M2BIN
TLC27M2CD	TS27M2CD

TEXAS INSTRUMENTS	SGS-THOMSON REPLACEMENT
TLC27M2CP	TS27M2CN
TLC27M2ID	TS27M2ID
TLC27M2IP	TS27M2IN
TLC27M4ACD	TS27M4ACD
TLC27M4ACN	TS27M4ACN
TLC27M4AID	TS27M4AID
TLC27M4AIN	TS27M4AIN
TLC27M4BCD	TS27M4BCD
TLC27M4BCN	TS27M4BCN
TLC27M4BID	TS27M4BID
TLC27M4BIN	TS27M4BIN
TLC27M4CD	TS27M4CD
TLC27M4CN	TS27M4CN
TLC27M4ID	TS27M4ID
TLC27M4IN	TS27M4IN

NATIONAL SEMICONDUCTOR	SGS-THOMSON REPLACEMENT
LMC660CN	TS27M4ACN
LMC660AIN	TS27M4BIN
LMC660CM	TS27M4ACD
LMC660AIM	TS27M4BID

NATIONAL SEMICONDUCTOR	SGS-THOMSON REPLACEMENT
LMC662CN	TS27M2ACN
LMC662AIN	TS27M2BIN
LMC662CM	TS27M2ACD
LMC662AIM	TS27M2BID

2 - CMOS COMPARATORS

TEXAS INSTRUMENTS	SGS-THOMSON REPLACEMENT
TLC372CD	TS372CD
TLC372CP	TS372CN
TLC372ID	TS372ID
TLC372IP	TS372IN

TEXAS INSTRUMENTS	SGS-THOMSON REPLACEMENT
TLC374CD	TS374CD
TLC374CN	TS374CN
TLC374ID	TS374ID
TLC374IN	TS374IN

2 - CMOS COMPARATORS (continued)

TEXAS INSTRUMENTS	SGS-THOMSON REPLACEMENT
TLC3702CD	TS3702CD
TLC3702CP	TS3702CN
TLC3702ID	TS3702ID
TLC3702IP	TS3702IN
TLC3704CD	TS3704CD
TLC3704CN	TS3704CN
TLC3704ID	TS3704ID
TLC3704IN	TS3704IN

TEXAS INSTRUMENTS	SGS-THOMSON REPLACEMENT
TLC339CD	TS339CD
TLC339CN	TS339CN
TLC339ID	TS339ID
TLC339IN	TS339IN
TLC393CD	TS393CD
TLC393CP	TS393CN
TLC393ID	TS393ID
TLC393IP	TS393IN

3 - CMOS TIMERS

NATIONAL SEMICONDUCTOR	SGS-THOMSON REPLACEMENT
LMC555CM	TS555CD
LMC555CN	TS555CN

SIGNETICS	SGS-THOMSON REPLACEMENT
ICM7555CD	TS555CD
ICM7555CN	TS555CN
ICM7555ID	TS555ID
ICM7555IN	TS555IN

TEXAS INSTRUMENT	SGS-THOMSON REPLACEMENT
TLC555CD	TS555CD
TLC555CP	TS555CN
TLC555ID	TS555ID
TLC555IP	TS555IN
TLC556CD	TS556CD
TLC556CN	TS556CN
TLC556ID	TS556ID
TLC556IN	TS556IN

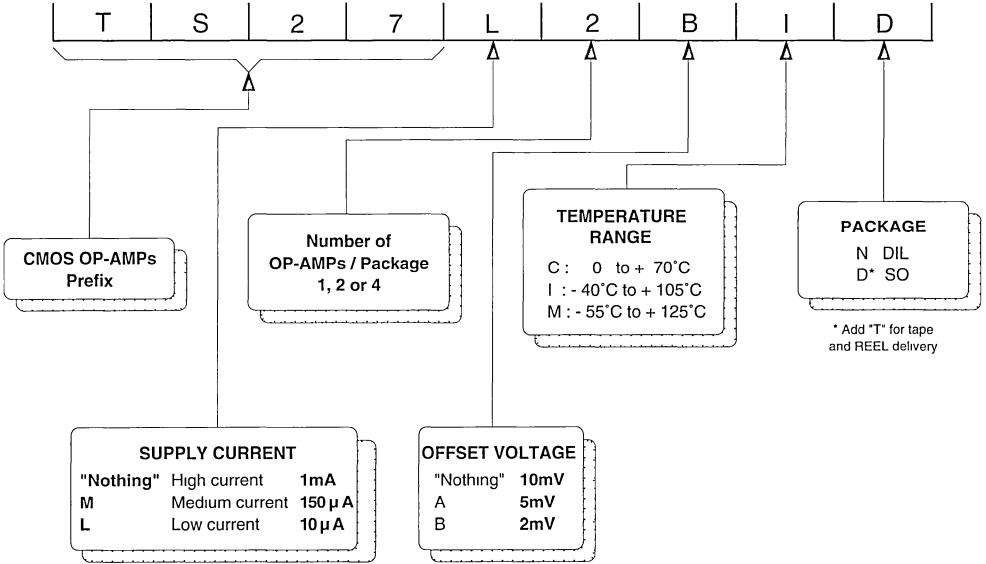
INTERSIL	SGS-THOMSON REPLACEMENT
ICM7555CBA	TS555CD
ICM7555IPA	TS555IN
ICM7556IPD	TS556IN

NEC	SGS-THOMSON REPLACEMENT
μ PD5555C	TS555CN
μ PD555G2	TS555CD
μ PD5556C	TS556CN
μ PD5556G2	TS556CD

SAMSUNG	SGS-THOMSON REPLACEMENT
KS555D	TS555ID
KS555N	TS555IN
KS555HD	TS555CD
KS555HN	TS555CN
KS556D	TS556CD
KS556N	TS556CN

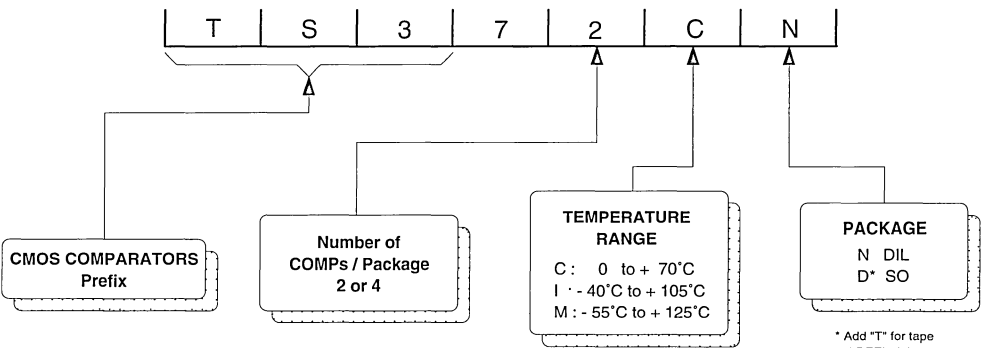
CMOS ORDERING INFORMATION

1 - CMOS OPERATIONAL AMPLIFIERS



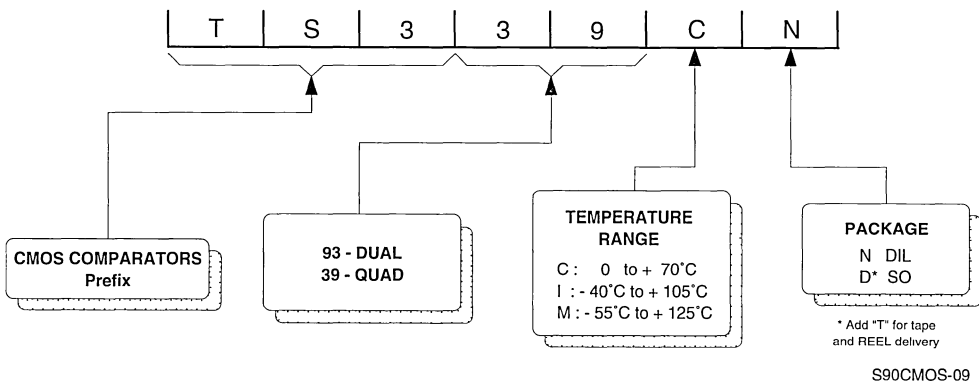
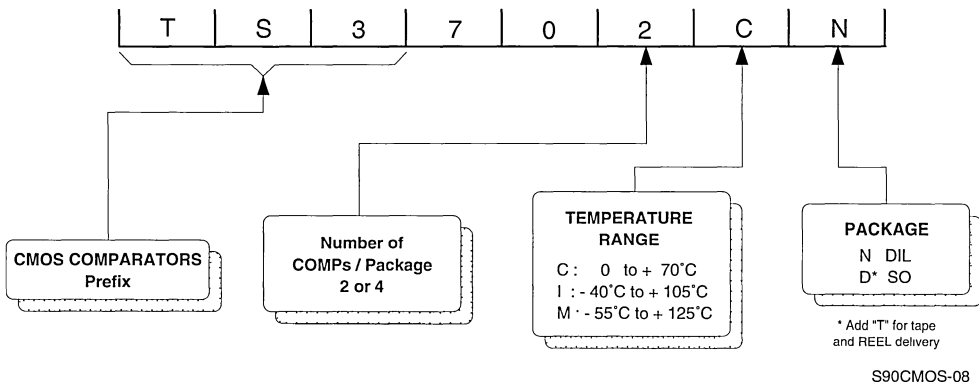
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2 - CMOS COMPARATORS

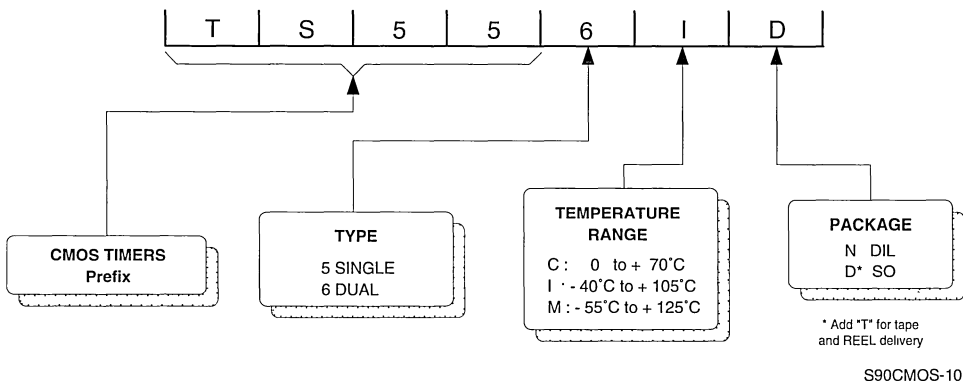


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2 - CMOS COMPARATORS (continued)



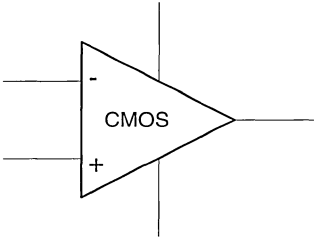
3 - CMOS TIMERS



APPLICATIONS

SINGLE SUPPLY VOLTAGE
 PORTABLE
 SENSORS (PRESSURE, LEVEL, VOLUMETRIC)

LOW INPUT OFFSET VOLTAGE
 COMPUTER



LOW SWITCH NOISE
 TELECOM
 INSTRUMENTATION

LOW INPUT CURRENT
 INSTRUMENTATION
 AUTO RADIO
 TELECOM
 SENSORS

LOW SUPPLY CURRENT
 TELECOM
 WHITE GOODS

LOW SUPPLY VOLTAGE
 TELECOM NETWORK

S90CMOS-11

MULTI SEGMENT POSITION

- TELECOM** SUBSCRIBER CARD (FILTER), EXCHANGE BOARD, MOBILE PHONE...
- CONSUMER** VCR, TV SET, CD PLAYER WHITE MARKET AND TOYS...
- AUTOMOTIVE** INJECTION CONTROL, ABS, CAR RADIO...
- COMPUTER** PERIPHERALS, DISK DRIVE...
- INDUSTRIAL** ELECTRICITY, GAZ AND WATER METERING, TEMPERATURE SENSORS...

SELECTION GUIDE

CMOS OPERATIONAL AMPLIFIERS

Characteristics specified at $V_{CC} = +10V$, $T_{AMB} = +25^{\circ}C$

Type	Configuration	Main Feature	Single Supply	Operating Voltage Range (V)	Supply Current Typ/amp (mA)	Input Offset Voltage Max (mV)	Gain Bandwidth Product Typ (MHz)	Slew Rate Typ ($V/\mu s$)
TS271	Single	Programmable	Yes	3* to 16	0.01 to 0.8	10	0.1 to 2.5	0.04 to 4.5
TS271A	Single	Programmable	Yes	3* to 16	0.01 to 0.8	5	0.1 to 2.5	0.04 to 4.5
TS271B	Single	Programmable	Yes	3* to 16	0.01 to 0.8	2	0.1 to 2.5	0.04 to 4.5
TS27L2	Dual	Very Low Power	Yes	3* to 16	0.01	10	0.1	0.04
TS27L2A	Dual	Very Low Power	Yes	3* to 16	0.01	5	0.1	0.04
TS27L2B	Dual	Very Low Power	Yes	3* to 16	0.01	2	0.1	0.04
TS27M2	Dual	Low Power	Yes	3* to 16	0.15	10	1	0.6
TS27M2A	Dual	Low Power	Yes	3* to 16	0.15	5	1	0.6
TS27M2B	Dual	Low Power	Yes	3* to 16	0.15	2	1	0.6
TS272	Dual	High Speed	Yes	3* to 16	1.0	10	3.5	5.5
TS272A	Dual	High Speed	Yes	3* to 16	1.0	5	3.5	5.5
TS272B	Dual	High Speed	Yes	3* to 16	1.0	2	3.5	5.5
TS27L4	Quad	Very Low Power	Yes	3* to 16	0.01	10	0.1	0.04
TS27L4A	Quad	Very Low Power	Yes	3* to 16	0.01	5	0.1	0.04
TS27L4B	Quad	Very Low Power	Yes	3* to 16	0.01	2	0.1	0.04
TS27M4	Quad	Low Power	Yes	3* to 16	0.15	10	1	0.6
TS27M4A	Quad	Low Power	Yes	3* to 16	0.15	5	1	0.6
TS27M4B	Quad	Low Power	Yes	3* to 16	0.15	2	1	0.6
TS274	Quad	High Speed	Yes	3* to 16	1.0	10	3.5	5.5
TS274A	Quad	High Speed	Yes	3* to 16	1.0	5	3.5	5.5
TS274B	Quad	High Speed	Yes	3* to 16	1.0	2	3.5	5.5

* For selected devices only.

CMOS COMPARATORS

Characteristics specified at $V_{CC} = +5V$, $T_{AMB} = +25^{\circ}C$

Type	Configuration	Main Feature	Single Supply	Operating Voltage Range (V)	Supply Current Typ/comp (μA)	Input Offset Voltage Max (mV)	Response Time (Typ) (with overdrive = 5mV) (ns)	Output Type
TS372	Dual	Low Power	Yes	3* to 16	150	10	600	Open Drain
TS374	Quad	Low Power	Yes	3* to 16	150	10	600	Open Drain
TS393	Dual	Micro Power	Yes	3* to 16	9	5	2100	Open Drain
TS339	Quad	Micro Power	Yes	3* to 16	9	5	2100	Open Drain
TS3702	Dual	Micro Power	Yes	3* to 16	9	5	2300	Push-Pull
TS3704	Quad	Micro Power	Yes	3* to 16	9	5	2300	Push-Pull

* For selected devices only.

CMOS TIMERS

Characteristics specified at $V_{CC} = +5V$, $T_{AMB} = +25^{\circ}C$

Type	Configuration	Main Feature	Single Supply	Operating Voltage Range (V)	Supply Current Typ/Timer (μA)	Max Frequency Astable Mode (MHz)
TS555	Single	Low Power	Yes	2 to 16	100	2.7
TS556	Dual	Low Power	Yes	2 to 16	100	2.7

OPERATIONAL AMPLIFIERS CMOS versus BIPOLAR & JFET

Characteristics specified at $T_{AMB} = +25^{\circ}\text{C}$

TS271 versus COMPETITIVE SINGLE OPERATIONAL AMPLIFIERS

Type	Technology	Main Feature	Single Supply	Operating Voltage Max (V)	Supply Current Typ (mA)	Adjustable	Input Offset Voltage Max (mV)	Bandwidth (MHz)	Slew Rate (V/ μs)
LF355	JFET	General Purpose	No	± 18	2	Offset	10	2.5	5
TL061	JFET	Low Power	No	± 18	0.2	Offset	15	1	3.5
TL071	JFET	Low Noise	No	± 18	1.4	Offset	8	4	16
TL081	JFET	General Purpose	No	± 18	1.4	Offset	8	4	16
TS271	CMOS	Single Supply	Yes	± 18	0.1-0.16	Offset	2-5 mV	0.1-10 MHz	0.12 to 1.2
LM301A	Bipolar	General Purpose	No	± 18	1.8	Offset Frequency	5	1	0.5
LM308A	Bipolar	Precision	No	± 18	0.3	Offset Frequency	0.5	0.8	0.15
LM318	Bipolar	Ultra-fast	No	± 20	5	Offset	10	15	70
TDB7910	Bipolar	Power	Yes	± 18	10	Offset Frequency	6	1	0.5
UA741	Bipolar	General Purpose	No	± 18	1.7	Offset	5	1	0.5
UA748	Bipolar	General Purpose	No	± 18	1.8	Offset Frequency	5	1	0.5
UA776	Bipolar	Programmable	No	± 18	0.02-0.16	Offset	5	0.01 to 1	0.03 to 0.8

TS27x2 versus COMPETITIVE DUAL OPERATIONAL AMPLIFIERS

Type	Technology	Main Feature	Single Supply	Operating Voltage Max (V)	Supply Current (per amplifier) Typ (mA)	Input Offset Voltage Max (mV)	Bandwidth (MHz)	Slew Rate (V/ μ s)
TL062	JFET	Low Power	No	± 18	0.2	15	1	3.5
TL072	JFET	Low Noise	No	± 18	1.4	8	4	16
TL082	JFET	General Purpose	No	± 18	1.4	8	4	16
TS27x2	C-MOS	Low Power	Yes	± 16	0.3	5	0.1 to 3.5	0.4 to 5.5
LM2904	Bipolar	Low Power	Yes	± 16 or 32	0.3	5	1.1	0.6
LM358	Bipolar	Low Power	Yes	± 16 or 32	0.3	5	1.1	0.6
LS204	Bipolar	High Performance	No	± 18	0.4	3.5	2.5	1
MC1458	Bipolar	General Purpose	No	± 18	1.6	5	1	0.8
MC4558	Bipolar	Wide Band	No	± 18	1.6	5	5.5	2.2
TEB1033	Bipolar	High Stability	No	± 18	0.5	1	2.5	1

TS27x4 versus COMPETITIVE QUAD OPERATIONAL AMPLIFIERS

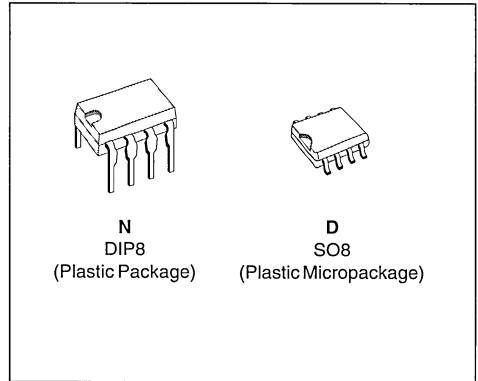
Type	Technology	Main Feature	Single Supply	Operating Voltage Max (V)	Supply Current (per amplifier) Typ (mA)	Input Offset Voltage Max (mV)	Bandwidth (MHz)	Slew Rate (V/ μ s)
TL064	JFET	Low Power	No	± 18	0.2	15	1	3.5
TL074	JFET	Low Noise	No	± 18	1.4	8	4	16
TL084	JFET	General Purpose	No	± 18	1.4	8	4	16
TS27x4	C-MOS	Low Power	Yes	± 16	0.3	5	0.1 to 3.5	0.4 to 5.5
LM2902	Bipolar	Low Power	Yes	± 16 or 32	0.3	5	1.3	0.4
LM324	Bipolar	Low Power	Yes	± 16 or 32	0.3	5	1.3	0.4
LM346	Bipolar	Programmable	No	± 18	0.25	3	1	0.5
LM348	Bipolar	Differential Output	No	± 18	0.5	5	1.3	0.5
LS404	Bipolar	High Performance	No	± 18	0.4	3.5	2.5	1
MC3403	Bipolar	Differential Output	Yes	± 18 or 36	0.7	5	1	0.6
TEB4033	Bipolar	High Stability	No	± 18	0.5	1	2.5	1

DATASHEETS

OPERATIONAL AMPLIFIERS

PROGRAMMABLE SINGLE CMOS OP-AMPS

- OFFSET NULL CAPABILITY (by external compensation)
- SYMMETRICAL OUTPUT CURRENTS
- HIGH GAIN BANDWIDTH PRODUCT
- THE TRANSFER FUNCTION IS LINEAR
- CONSUMPTION CURRENT AND DYNAMIC PARAMETERS ARE STABLE REGARDING THE VOLTAGE POWER SUPPLY VARIATIONS
- DYNAMIC CHARACTERISTICS ADJUSTABLE BY I_{SET}
- VERY LARGE I_{SET} RANGE
- PIN TO PIN COMPATIBLE WITH SINGLE OPERATIONAL AMPLIFIER (UA776)
- STABLE AND LOW OFFSET VOLTAGE
- INTERNAL ELECTROSTATIC DISCHARGE (ESD) PROTECTION CIRCUITS
- THREE INPUT OFFSET VOLTAGE SELECTIONS : STANDARD (10mV), A (5mV), B (2mV)



ORDER CODES

Part Number	Temperature Range	Package	
		N	D
TS271C/AC/BC	0°C to + 70°C	●	●
TS271I/AI/BI	- 40°C to + 105°C	●	●
TS271M/AM/BM	- 55°C to + 125°C	●	●
Example : TS271ACN			

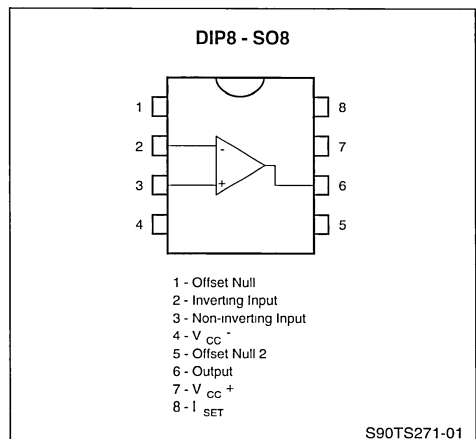
DESCRIPTION

The TS271 is low cost, low power single operational amplifier designed to operate with single or dual supplies. This operational amplifiers uses the SGS-THOMSON silicon gate LIN MOS process giving it an excellent consumption-speed ratio. This amplifier is ideally suited for low consumption applications.

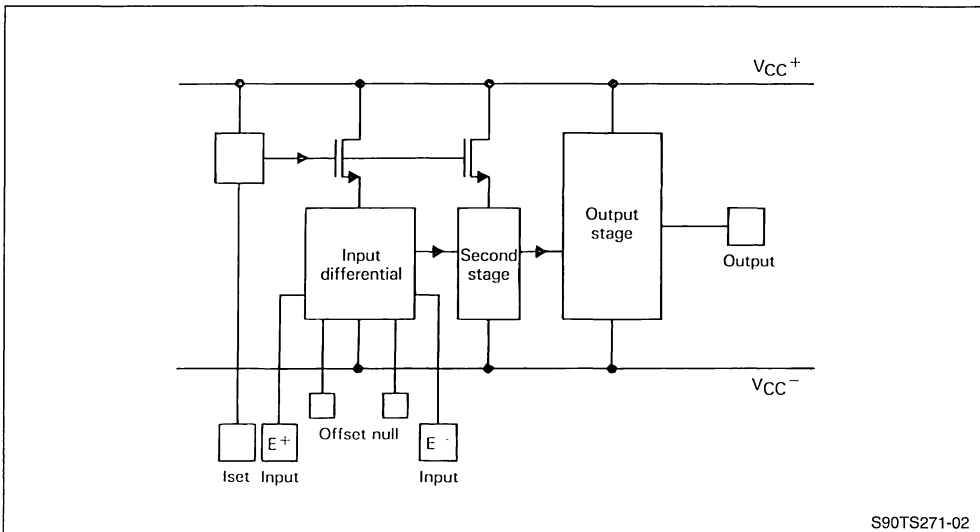
The power supply is externally programmable with a resistor connected between pins 8 and 4. It allows to choose the best consumption-speed ratio and the consumption can be minimized according to the required speed. These devices are specified for the following I_{SET} current values : 1.5 μ A, 25 μ A, 130 μ A.

The input impedance is similar to the J-FET input impedance : very high input impedance and extremely low input offset and bias currents. They allow to minimize the static errors in high impedance applications.

PIN CONNECTIONS (Top view)



BLOCK DIAGRAM



S90TS271-02

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage (Note 1)	18	V
V_{id}	Differential Input Voltage (Note 2)	± 18	V
V_i	Input Voltage (Note 3)	- 0.3 to 18	V
I_o	Output Current for $V_{CC}^+ \geq 15V$	± 30	mA
T_{oper}	Operating Free-Air Temperature Range	TS271C/AC/BC TS271I/AI/BI TS271M/AM/BM 0 to + 70 - 40 to + 105 - 55 to + 125	$^{\circ}C$
T_{stg}	Storage Temperature Range	- 65 to + 150	$^{\circ}C$

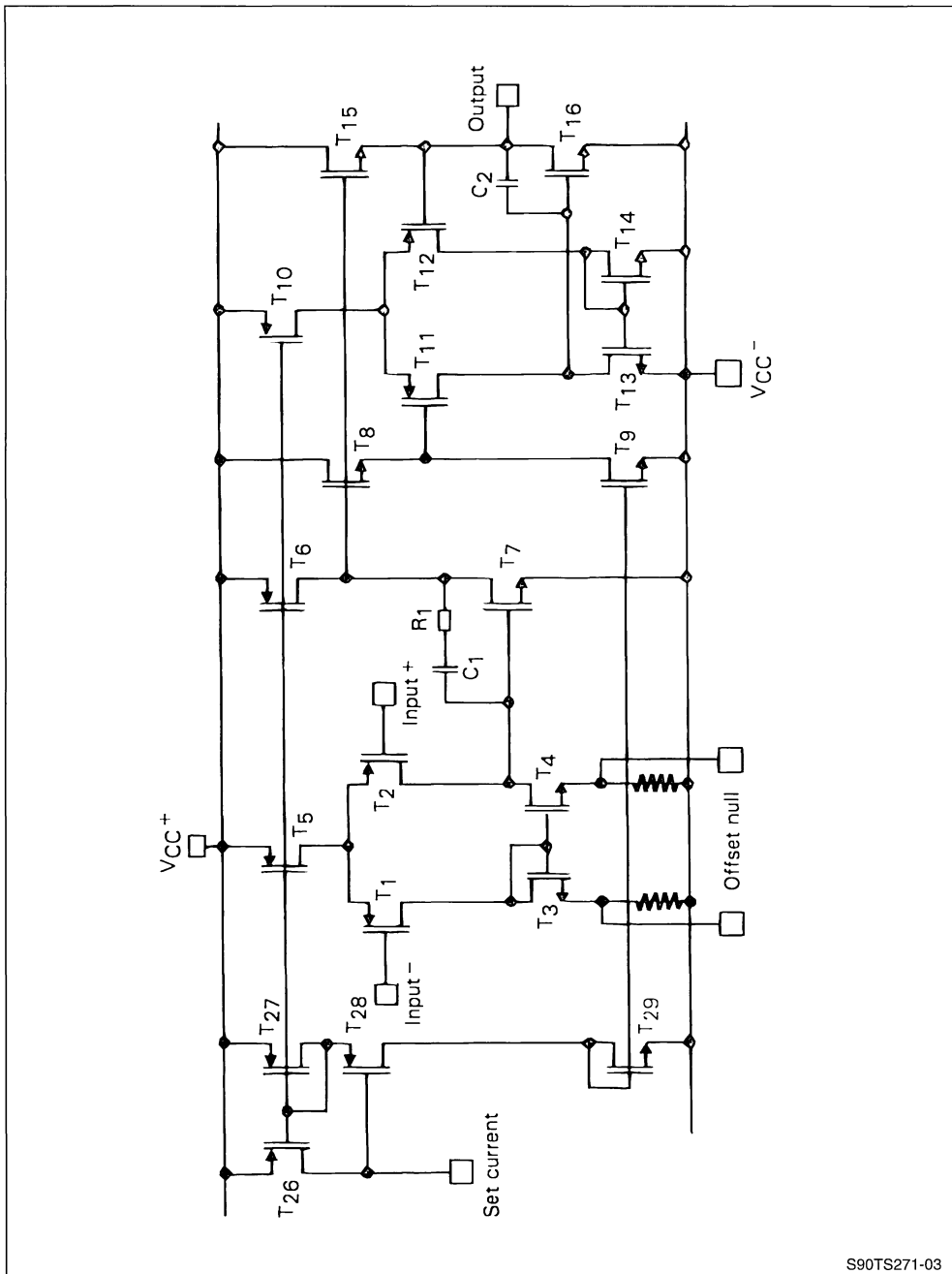
- Notes :
1. All voltage values, except differential voltage, are with respect to network ground terminal.
 2. Differential voltages are at the non-inverting input terminal with respect to the inverting input terminal
 3. The magnitude of the input and the output voltages must never exceed the magnitude of the positive supply voltage

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage	3* to 16	V
V_{ic}	Common Mode Input Voltage Range	0 to $V_{CC}^+ - 1.5$	V

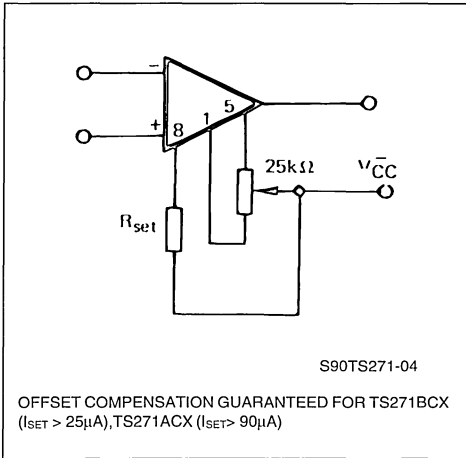
* Selected devices only.

SCHEMATIC DIAGRAM



S90TS271-03

OFFSET VOLTAGE NULL CIRCUIT



RESISTOR BIASING

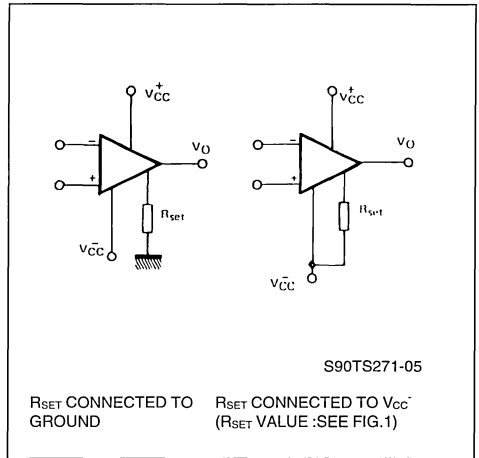
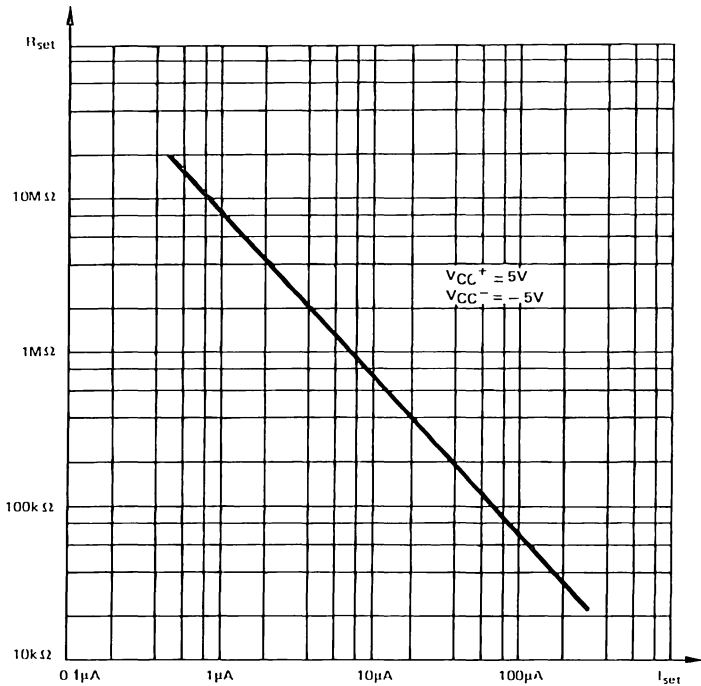


Figure 1 : R_{SET} Connected to V_{CC-} .



S90TS271-06

ELECTRICAL CHARACTERISTICS FOR I_{SET} = 1.5μA

V_{CC}⁺ = + 10V, V_{CC}⁻ = 0V, T_{AMB} = 25°C (unless otherwise specified)

Symbol	Parameter	TS271C/AC/BC			TS271I/AI/BI TS271M/AM/BM			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
V _{io}	Input Offset Voltage V _O = 1.4V, V _I = 0V		1.1	10		1.1	10	mV
	TS271C/I/M TS271AC/AI/AM TS271BC/BI/BM		0.9 0.25	5 2		0.9 0.25	5 2	
	T _{MIN} ≤ T _{AMB} ≤ T _{MAX}			12 6.5 3			12 6.5 3.5	
DV _{io}	Input Offset Voltage Drift		0.7			0.7		μV/°C
I _o	Input Offset Current V _I = 5V, V _O = 5V T _{MIN} ≤ T _{AMB} ≤ T _{MAX}		1			1		pA
				100			200	
I _b	Input Bias Current V _I = 5V, V _O = 5V T _{MIN} ≤ T _{AMB} ≤ T _{MAX}		1			1		pA
				150			300	
V _{OH}	High Level Output Voltage V _I = 10mV, R _L = 1MΩ T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	8.8 8.7	9		8.8 8.6	9		V
V _{OL}	Low Level Output Voltage (V _I = - 10mV)			50			50	mV
A _{vd}	Large Signal Voltage Gain V _O = 1V to 6V, R _L = 1MΩ, V _I = 5V T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	30 20	100		30 20	100		V/mV
GBP	Gain Bandwidth Product (A _v = 40dB, R _L = 1MΩ, C _L = 100pF, f _{in} = 10 kHz)		0.1			0.1		MHz
CMR	Common Mode Rejection Ratio V _O = 1.4V, V _I = 1V to 7.4V	60	80		60	80		dB
SVR	Supply Voltage Rejection Ratio V _{CC} ⁺ = 5V to 10V, V _O = 1.4V	60	80		60	80		dB
I _{CC}	Supply Current (per amplifier) A _v = 1, no load, V _O = 5V T _{MIN} ≤ T _{AMB} ≤ T _{MAX}		10	15 17		10	15 18	μA
I _o	Output Short Circuit Current V _I = 10mV, V _O = 0V	45	60	85	45	60	85	mA
I _{sink}	Output Sink Current V _I = - 10mV, V _O = V _{CC}	35	45	65	35	45	65	mA
S _{vo}	Slew-Rate at Unity Gain R _L = 1MΩ, C _L = 100pF		0.04			0.04		V/μs
∅ m	Phase Margin at Unity Gain A _v = 40 dB, R _L = 1MΩ C _L = 10pF C _L = 100pF		35 10			35 10		degrees
K _{ov}	Overshoot Factor C _L = 10pF C _L = 100pF		40 70			40 70		%
V _n	Equivalent Input Noise Voltage f = 1kHz, R _S = 10Ω		68			68		nV/√Hz

TYPICAL CHARACTERISTICS FOR $I_{SET} = 1.5\mu A$

Figure 2: Supply Current (each amplifier) versus Supply Voltage.

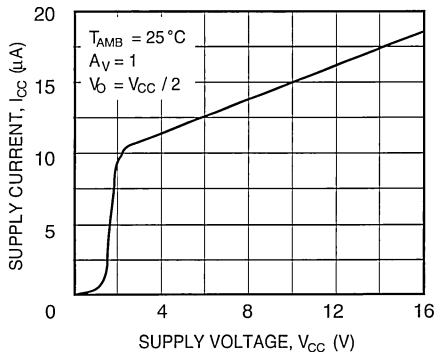


Figure 3: Input Bias Current versus Free Air Temperature.

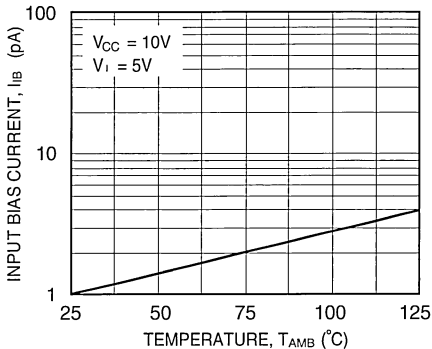


Figure 4a: High Level Output Voltage versus High Level Output Current.

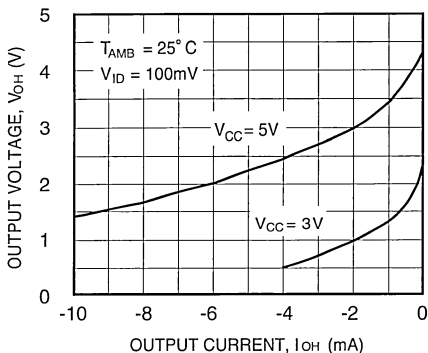


Figure 4b: High Level Output Voltage versus High Level Output Current.

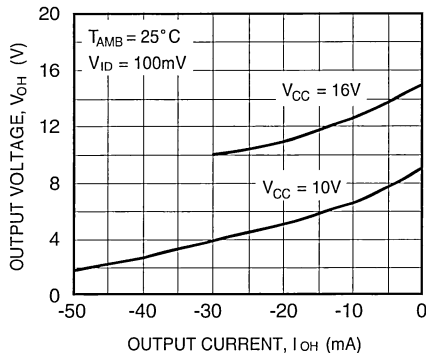


Figure 5a: Low Level Output Voltage versus Low Level Output Current.

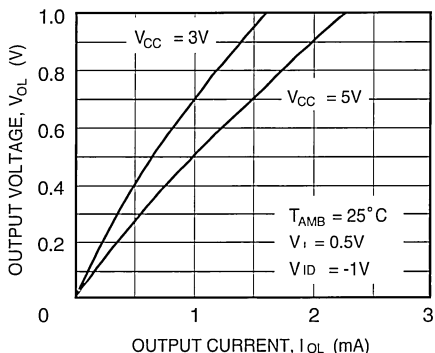
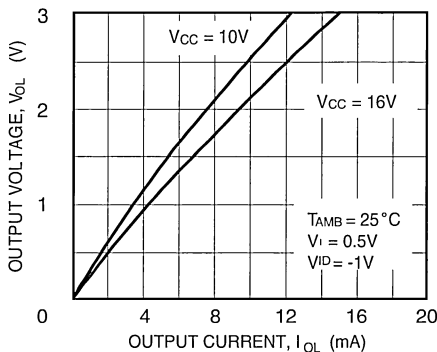


Figure 5b: Low Level Output Voltage versus Low Level Output Current.



TYPICAL CHARACTERISTICS FOR $I_{SET} = 1.5\mu A$ (continued)

Figure 6 : Open Loop Frequency Response and Phase Shift.

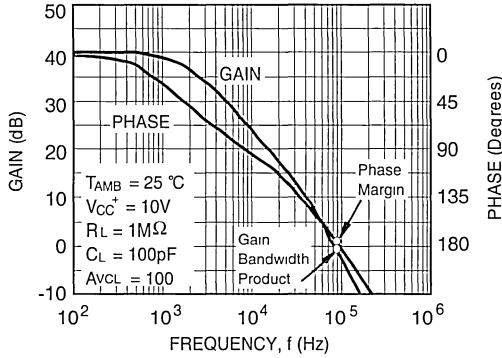


Figure 7 : Gain Bandwidth Product versus Supply Voltage.

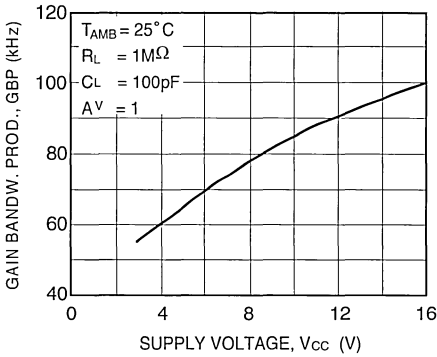


Figure 9 : Phase Margin versus Capacitive Load.

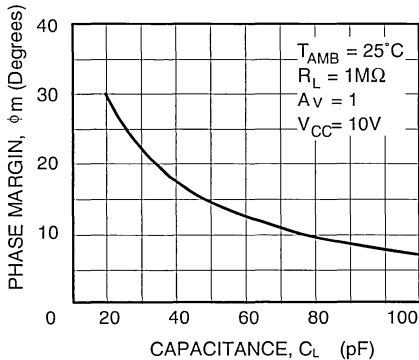


Figure 8 : Phase Margin versus Supply Voltage.

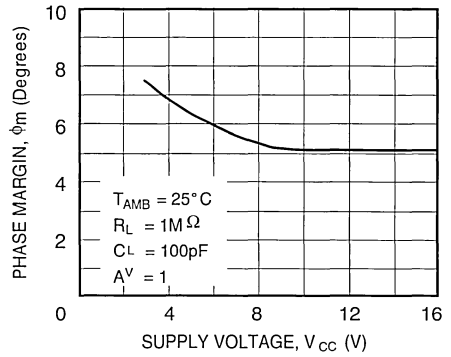
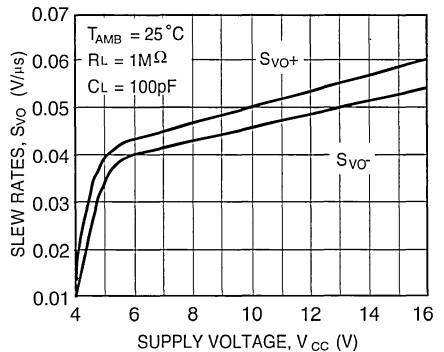


Figure 10 : Slew Rates versus Supply Voltage.



ELECTRICAL CHARACTERISTICS FOR I_{SET} = 25μA

V_{CC}⁺ = + 10V, V_{CC}⁻ = 0V, T_{AMB} = 25°C (unless otherwise specified)

Symbol	Parameter	TS271C/AC/BC			TS271I/AI/BI TS271M/AM/BM			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
V _{io}	Input Offset Voltage V _O = 1.4V, V _I = 0V T _{MIN} ≤ T _{AMB} ≤ T _{MAX}		1.1 0.9 0.25	10 5 2		1 0.9 0.25	10 5 2	mV
				12 6.5 3			12 6.5 3.5	
DV _{io}	Input Offset Voltage Drift		2			2		μV/°C
I _{io}	Input Offset Current V _I = 5V, V _O = 5V T _{MIN} ≤ T _{AMB} ≤ T _{MAX}		1	100		1	200	pA
I _{ib}	Input Bias Current V _I = 5V, V _O = 5V T _{MIN} ≤ T _{AMB} ≤ T _{MAX}		1	150		1	300	pA
V _{OH}	High Level Output Voltage V _I = 10mV, R _L = 100kΩ T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	8.7 8.6	8.9		8.7 8.5	8.9		V
V _{OL}	Low Level Output Voltage (V _I = - 10mV)			50			50	mV
A _{vd}	Large Signal Voltage Gain V _O = 1V to 6V, R _L = 100kΩ, V _I = 5V T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	30 20	50		30 10	50		V/mV
GBP	Gain Bandwidth Product (A _v = 40dB, R _L = 100kΩ, C _L = 100pF, f _{in} = 100 kHz)		0.7			0.7		MHz
CMR	Common Mode Rejection Ratio V _O = 1.4V, V _I = 1V to 7.4V	60	80		60	80		dB
SVR	Supply Voltage Rejection Ratio V _{CC} ⁺ = 5V to 10V, V _O = 1.4V	60	80		60	80		dB
I _{CC}	Supply Current (per amplifier) A _v = 1, no load, V _O = 5V T _{MIN} ≤ T _{AMB} ≤ T _{MAX}		150	200 250		150	200 300	μA
I _o	Output Short Circuit Current V _I = 10mV, V _O = 0V	45	60	85	45	60	85	mA
I _{sink}	Output Sink Current V _I = - 10mV, V _O = V _{CC}	35	45	65	35	45	65	mA
S _{vo}	Slew-Rate at Unity Gain R _L = 100kΩ, C _L = 100pF		0.6			0.6		V/μs
∅ m	Phase Margin at Unity Gain A _v = 40 dB, R _L = 100kΩ C _L = 10pF C _L = 100pF		50 30			50 30		degrees
K _{ov}	Overshoot Factor C _L = 10pF C _L = 100pF		30 50			30 50		%
V _n	Equivalent Input Noise Voltage f = 1kHz, R _S = 10Ω		38			38		nV/√Hz

TYPICAL CHARACTERISTICS FOR $I_{SET} = 25\mu A$

Figure 11 : Supply Current (each amplifier) versus Supply Voltage.

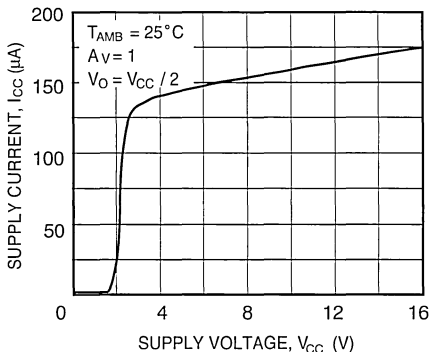


Figure 12 : Input Bias Current versus Free Air Temperature.

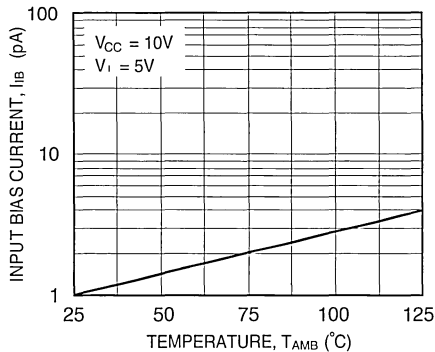


Figure 13a : High Level Output Voltage versus High Level Output Current.

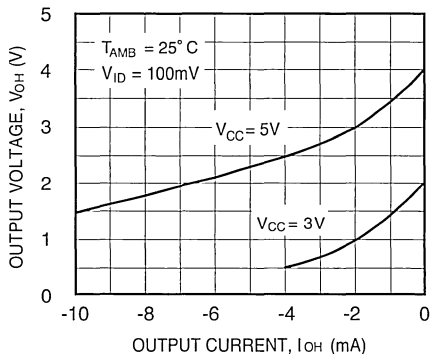


Figure 13b : High Level Output Voltage versus High Level Output Current.

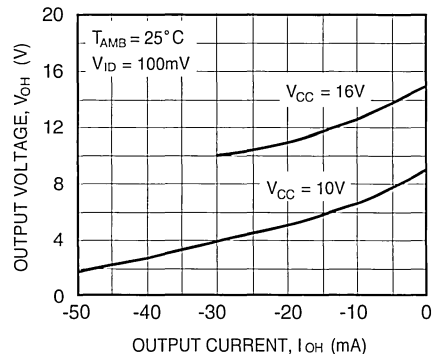


Figure 14a : Low Level Output Voltage versus Low Level Output Current.

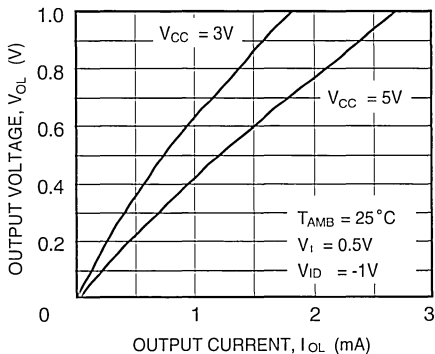
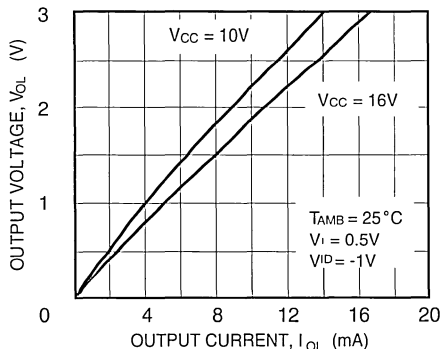


Figure 14b : Low Level Output Voltage versus Low Level Output Current.



TYPICAL CHARACTERISTICS FOR I_{SET} = 25μA (continued)

Figure 15 : Open Loop Frequency Response and Phase Shift.

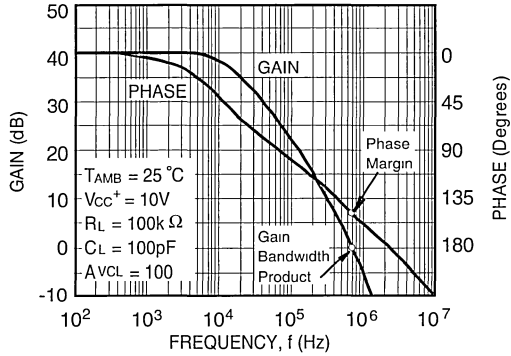


Figure 16 : Gain Bandwidth Product versus Supply Voltage.

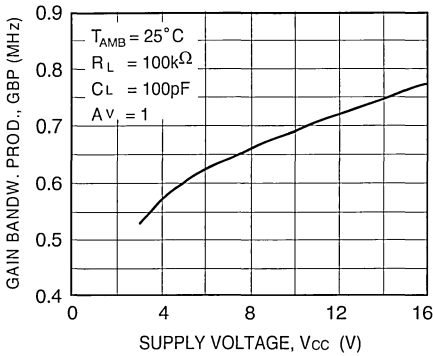


Figure 17 : Phase Margin versus Supply Voltage.

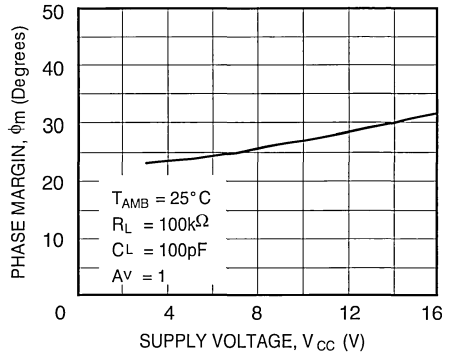


Figure 18 : Phase Margin versus Capacitive Load.

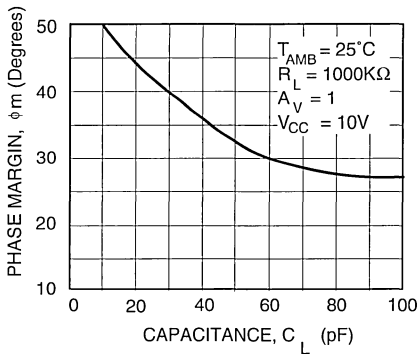
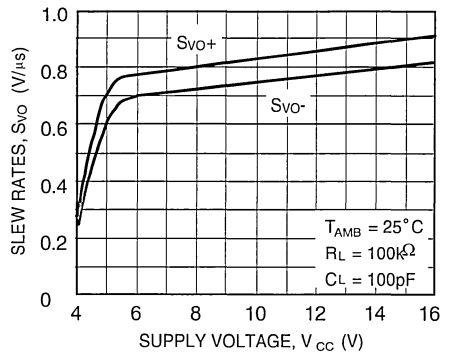


Figure 19 : Slew Rates versus Supply Voltage.



ELECTRICAL CHARACTERISTICS FOR $I_{SET} = 130\mu A$ $V_{CC}^+ = +10V$, $V_{CC}^- = 0V$, $T_{AMB} = 25^\circ C$ (unless otherwise specified)

Symbol	Parameter	TS271C/AC/BC			TS271I/AI/BI TS271M/AM/BM			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
V_{io}	Input Offset Voltage $V_O = 1.4V$, $V_I = 0V$	TS271C/I/M	1.1	10		1.1	10	mV
		TS271AC/AI/AM	0.9	5		0.9	5	
		TS271BC/BI/BM	0.25	2		0.25	2	
	$T_{MIN} \leq T_{AMB} \leq T_{MAX}$	TS271C/I/M		12			12	
		TS271AC/AI/AM		6.5			6.5	
		TS271BC/BI/BM		3			3.5	
DV_{io}	Input Offset Voltage Drift		2			2		$\mu V/^\circ C$
I_{io}	Input Offset Current $V_I = 5V$, $V_O = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		1			1		pA
				100			200	
I_{ib}	Input Bias Current $V_I = 5V$, $V_O = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		1			1		pA
				150			300	
V_{OH}	High Level Output Voltage $V_I = 10mV$, $R_L = 10k\Omega$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	8.2 8.1	8.4		8.2 8	8.4		V
V_{OL}	Low Level Output Voltage ($V_I = -10mV$)			50			50	mV
A_{vd}	Large Signal Voltage Gain $V_O = 1V$ to $6V$, $R_L = 10k\Omega$, $V_I = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	10 7	15		10 6	15		V/mV
GBP	Gain Bandwidth Product ($A_v = 40dB$, $R_L = 10k\Omega$, $C_L = 100pF$, $f_{in} = 200$ kHz)		2.3			2.3		MHz
CMR	Common Mode Rejection Ratio $V_O = 1.4V$, $V_I = 1V$ to $7.4V$	60	80		60	80		dB
SVR	Supply Voltage Rejection Ratio $V_{CC}^+ = 5V$ to $10V$, $V_O = 1.4V$	60	70		60	70		dB
I_{CC}	Supply Current (per amplifier) $A_v = 1$, no load, $V_O = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		800	1300 1400		800	1300 1500	μA
I_o	Output Short Circuit Current $V_I = 10mV$, $V_O = 0V$	45	60	85	45	60	85	mA
I_{sink}	Output Sink Current $V_I = -10mV$, $V_O = V_{CC}$	35	45	65	35	45	65	mA
S_{vo}	Slew-Rate at Unity Gain $R_L = 10k\Omega$, $C_L = 100pF$		4.5			4.5		V/ μs
ϕ_m	Phase Margin at Unity Gain $A_v = 40$ dB, $R_L = 10k\Omega$ $C_L = 10pF$ $C_L = 100pF$			65 50		65 50		degrees
K_{ov}	Overshoot Factor $C_L = 10pF$ $C_L = 100pF$		30 30			30 30		%
V_n	Equivalent Input Noise Voltage $f = 1kHz$, $R_S = 10\Omega$		30			30		nV/ \sqrt{Hz}

TYPICAL CHARACTERISTICS FOR $I_{SET} = 130\mu A$

Figure 20 : Supply Current (each amplifier) versus Supply Voltage.

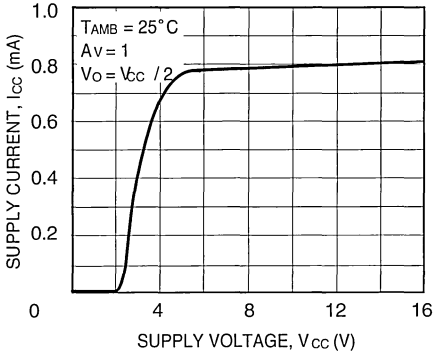


Figure 21 : Input Bias Current versus Free Air Temperature.

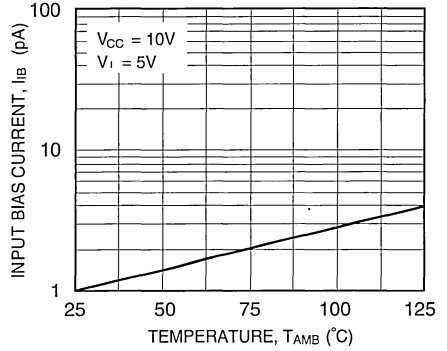


Figure 22a : High Level Output Voltage versus High Level Output Current.

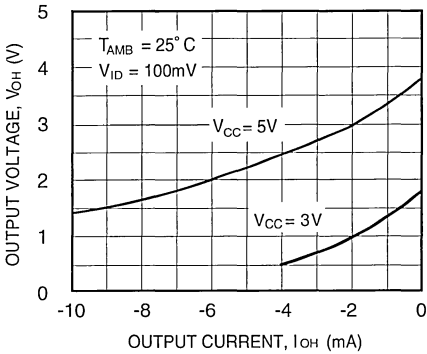


Figure 22b : High Level Output Voltage versus High Level Output Current.

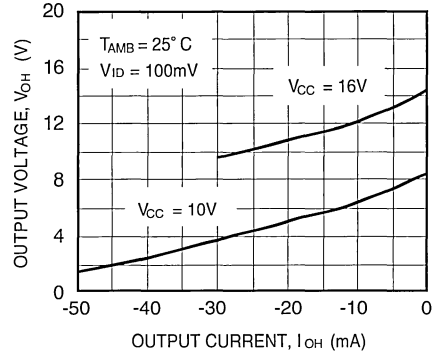


Figure 23a : Low Level Output Voltage versus Low Level Output Current.

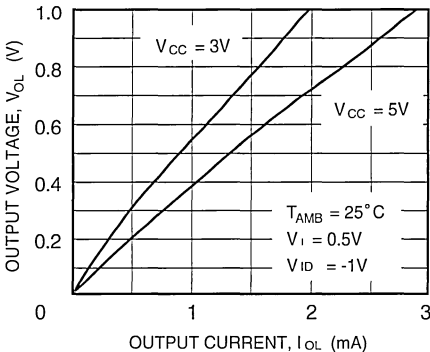
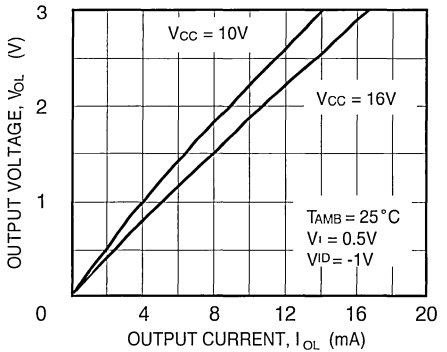


Figure 23b : Low Level Output Voltage versus Low Level Output Current.



TYPICAL CHARACTERISTICS FOR $I_{SET} = 130\mu A$ (continued)

Figure 24 : Open Loop Frequency Response and Phase Shift.

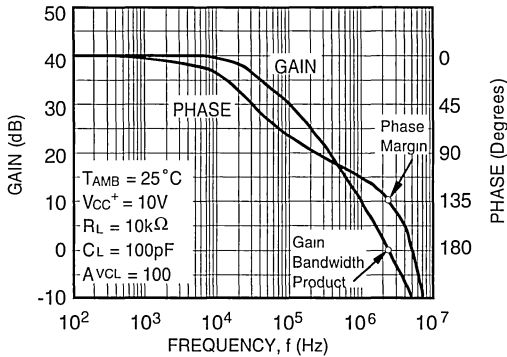


Figure 25 : Gain Bandwidth Product versus Supply Voltage.

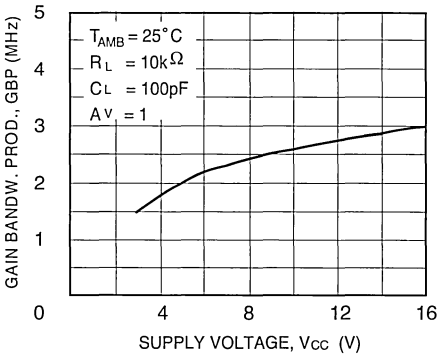


Figure 26 : Phase Margin versus Supply Voltage.

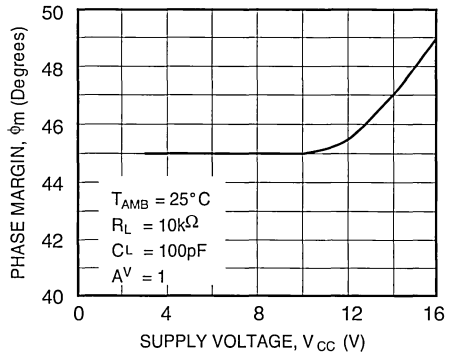


Figure 27 : Phase Margin versus Capacitive Load.

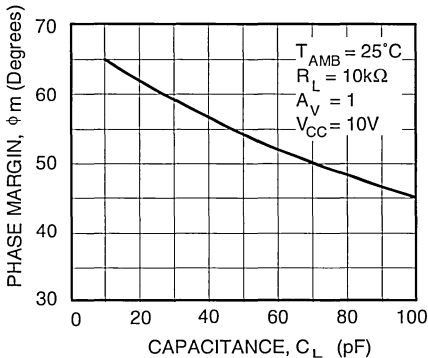
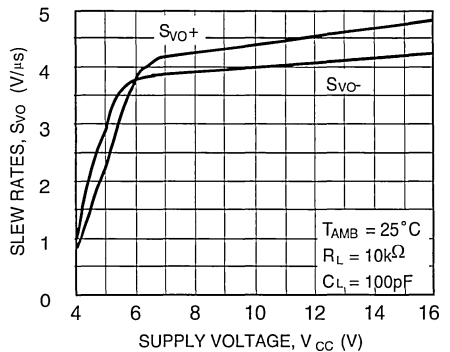
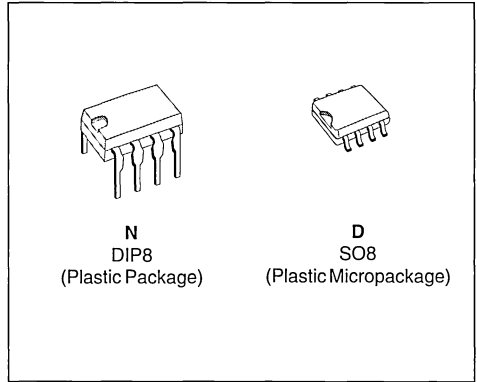


Figure 28 : Slew Rates versus Supply Voltage.



HIGH SPEED DUAL CMOS OP-AMPS

- EXCELLENT PHASE MARGIN ON CAPACITIVE LOADS
- SYMMETRICAL OUTPUT CURRENTS
- HIGH GAIN BANDWIDTH PRODUCT
- LOW OUTPUT DYNAMIC IMPEDANCE
- THE TRANSFER FUNCTION IS LINEAR
- PIN TO PIN COMPATIBLE WITH STANDARD DUAL OP-AMPS (TL082 -LM358)
- STABLE AND LOW OFFSET VOLTAGE
- INTERNAL ELECTROSTATIC DISCHARGE (ESD) PROTECTION CIRCUITS
- THREE INPUT OFFSET VOLTAGE SELECTIONS : STANDARD (10mV), A (5mV), B (2mV)



ORDER CODES

Part Number	Temperature Range	Package	
		N	D
TS272C/AC/BC	0°C to + 70°C	○	○
TS272I/AI/BI	- 40°C to + 105°C	○	○
TS272M/AM/BM	- 55°C to + 125°C	○	○
Example : TS272ACN			

DESCRIPTION

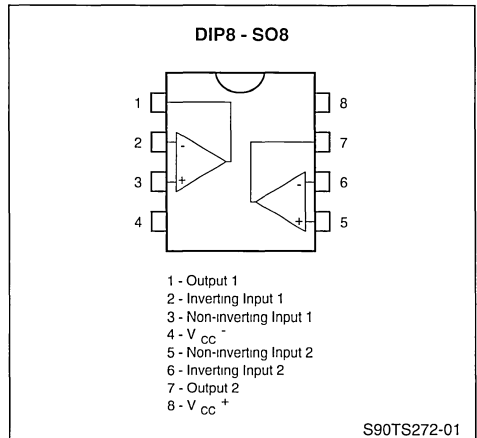
The TS272 series are low cost, low power dual operational amplifiers designed to operate with single or dual supplies. These operational amplifiers use the SGS-THOMSON silicon gate LIN MOS process giving them an excellent consumption-speed ratio. These series are ideally suited for low consumption applications.

Three power consumptions are available allowing to have always the best consumption-speed ratio :

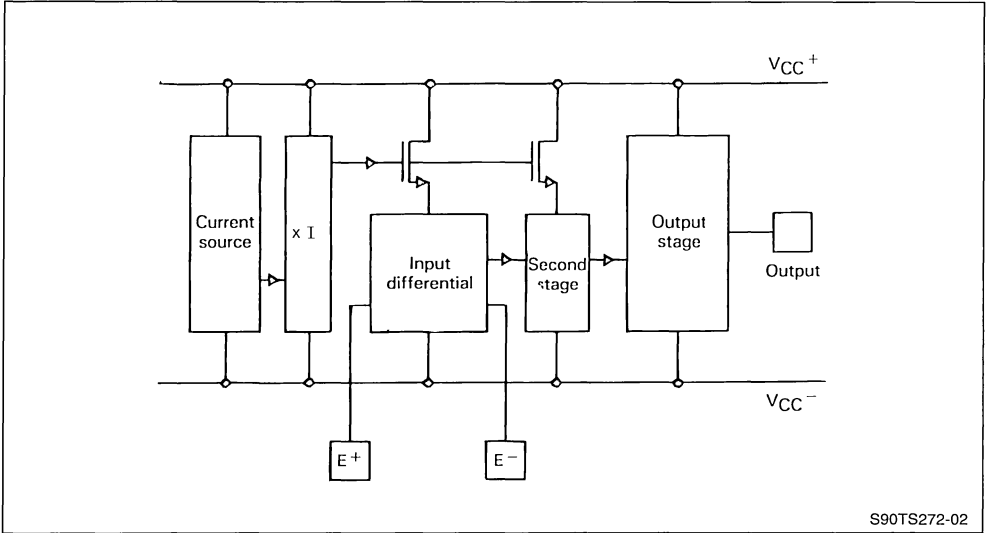
- $I_{CC} = 10\mu\text{A}/\text{amp.}$: TS27L2 (very low power)
- $I_{CC} = 150\mu\text{A}/\text{amp.}$: TS27M2 (low power)
- $I_{CC} = 1\text{mA}/\text{amp.}$: TS272 (high speed)

The input impedance is similar to the J-FET input impedance : very high input impedance and extremely low input offset and bias currents. They allow to minimize the static errors in high impedance applications.

PIN CONNECTIONS (Top view)



BLOCK DIAGRAM



MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage (Note 1)	18	V
V_{id}	Differential Input Voltage (Note 2)	± 18	V
V_i	Input Voltage (Note 3)	- 0.3 to 18	V
I_o	Output Current for $V_{CC}^+ \geq 15V$	± 30	mA
T_{oper}	Operating Free-Air Temperature Range	TS272C/AC/BC TS272I/AI/BI TS272M/AM/BM 0 to + 70 - 40 to + 105 - 55 to + 125	$^{\circ}C$
T_{stg}	Storage Temperature Range	- 65 to + 150	$^{\circ}C$

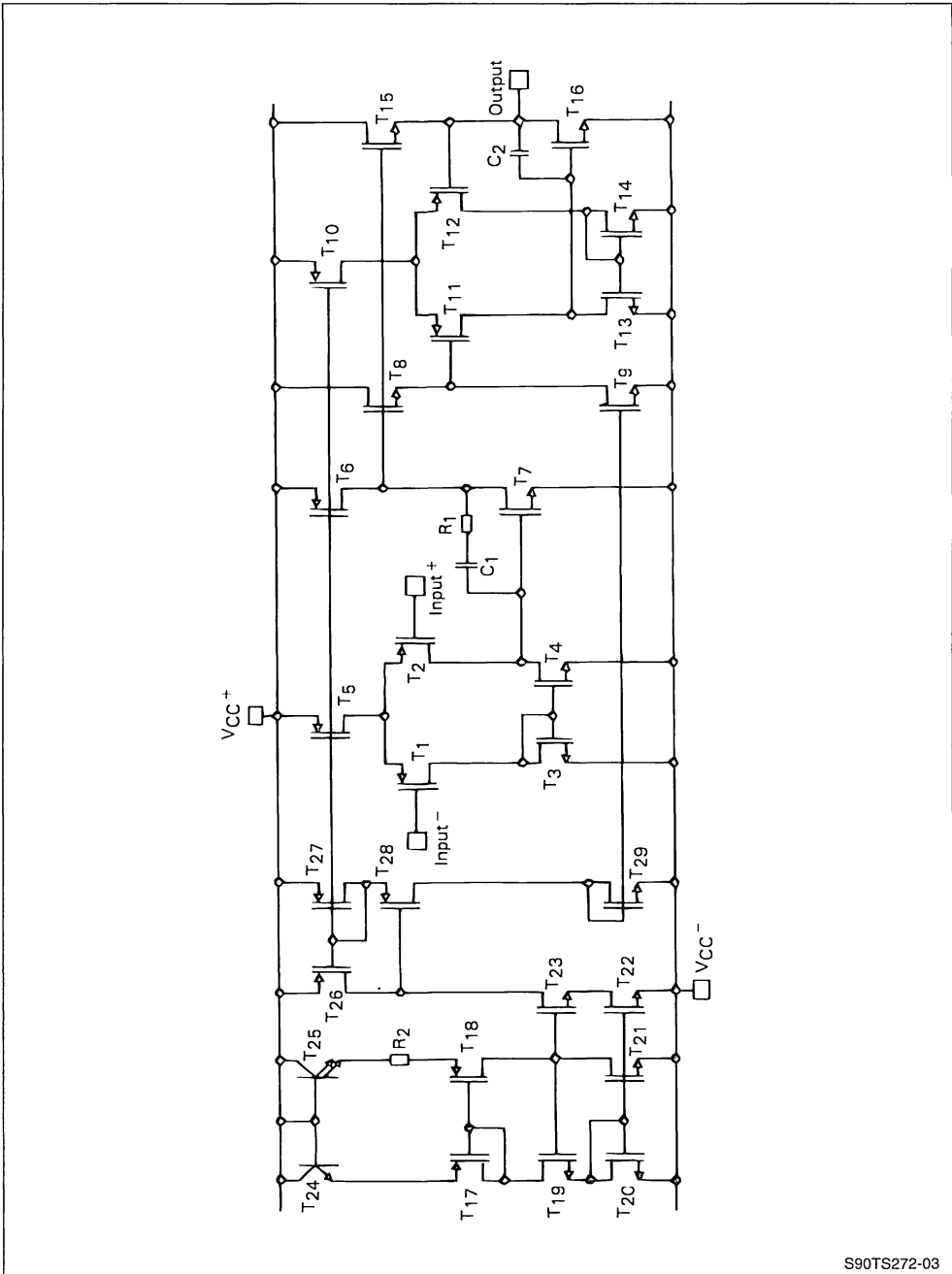
- Notes : 1. All voltage values, except differential voltage, are with respect to network ground terminal.
 2. Differential voltages are at the non-inverting input terminal with respect to the inverting input terminal.
 3. The magnitude of the input and the output voltages must never exceed the magnitude of the positive supply voltage.

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage	3 * to 16	V
V_{ic}	Common Mode Input Voltage Range	0 to $V_{CC}^+ - 1.5$	V

* Selected devices only.

SCHEMATIC DIAGRAM (for 1/2 TS272)



S90TS272-03

ELECTRICAL CHARACTERISTICS

$V_{CC}^+ = +10V$, $V_{CC}^- = 0V$, $T_{AMB} = 25^{\circ}C$ (unless otherwise specified)

Symbol	Parameter	TS272C/AC/BC			TS272I/AI/BI TS272M/AM/BM			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
V_{io}	Input Offset Voltage $V_o = 1.4V$, $V_i = 0V$ TS272C/I/M TS272AC/AI/AM TS272BC/BI/BM $T_{MIN} \leq T_{AMB} \leq T_{MAX}$ TS272C/I/M TS272AC/AI/AM TS272BC/BI/BM		1.1 0.9 0.25	10 5 2		1.1 0.9 0.25	10 5 2	mV
DV_{io}	Input Offset Voltage Drift		2			2		$\mu V/^{\circ}C$
I_{io}	Input Offset Current $V_i = 5V$, $V_o = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		1	100		1	200	pA
I_{ib}	Input Bias Current $V_i = 5V$, $V_o = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		1	150		1	300	pA
V_{OH}	High Level Output Voltage $V_i = 10mV$, $R_L = 10k\Omega$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	8.2 8.1	8.4		8.2 8	8.4		V
V_{OL}	Low Level Output Voltage $V_i = -10mV$			50			50	mV
A_{vd}	Large Signal Voltage Gain $V_o = 1V$ to $6V$, $R_L = 10k\Omega$, $V_i = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	10 7	15		10 6	15		V/mV
GBP	Gain Bandwidth Product $A_v = 40dB$, $R_L = 10k\Omega$, $C_L = 100pF$ $f_{in} = 200kHz$		3.5			3.5		MHz
CMR	Common Mode Rejection Ratio $V_o = 1.4V$, $V_i = 1V$ to $7.4V$	65	80		65	80		dB
SVR	Supply Voltage Rejection Ratio $V_{CC}^+ = 5V$ to $10V$, $V_o = 1.4V$	60	70		60	70		dB
I_{CC}	Supply Current (per amplifier) $A_v = 1$, no load, $V_o = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		1000	1500 1600		1000	1500 1700	μA
I_o	Output Short Circuit Current $V_i = 10mV$, $V_o = 0V$	45	60	85	45	60	85	mA
I_{sink}	Output Sink Current $V_i = -10mV$, $V_o = V_{CC}$	35	45	65	35	45	65	mA
S_{vo}	Slew-Rate at Unity Gain $R_L = 10k\Omega$, $C_L = 100pF$		5.5			5.5		V/ μs
ϕ_m	Phase Margin at Unity Gain $A_v = 40dB$, $R_L = 10k\Omega$, $C_L = 100pF$		40			40		degrees
K_{ov}	Overshoot Factor		30			30		%
V_n	Equivalent Input Noise Voltage $f = 1kHz$, $R_S = 10\Omega$		30			30		nV/ \sqrt{Hz}
$VO1/VO2$	Cross Talk Attenuation		120			120		dB

TYPICAL CHARACTERISTICS

Figure 1 : Supply Current (each amplifier) versus Supply Voltage.

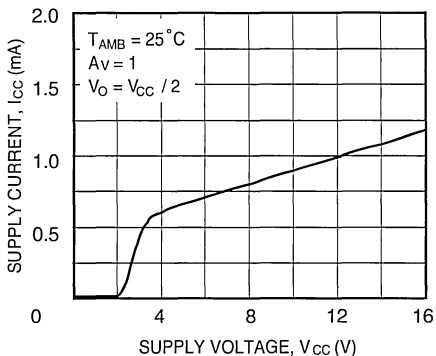


Figure 2 : Input Bias Current versus Free Air Temperature.

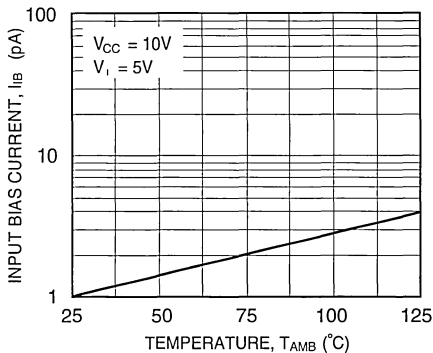


Figure 3a : High Level Output Voltage versus High Level Output Current.

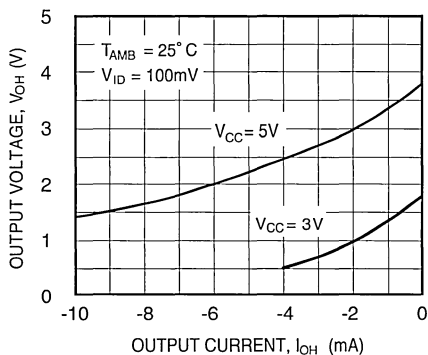


Figure 3b : High Level Output Voltage versus High Level Output Current.

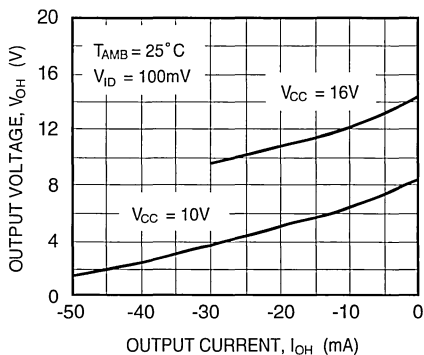


Figure 4a : Low Level Output Voltage versus Low Level Output Current.

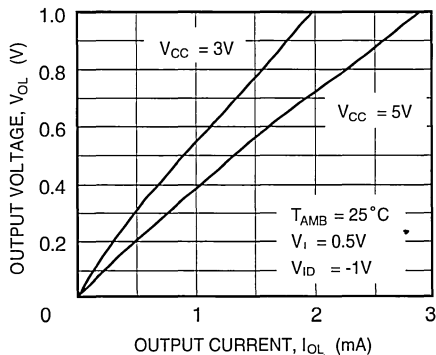
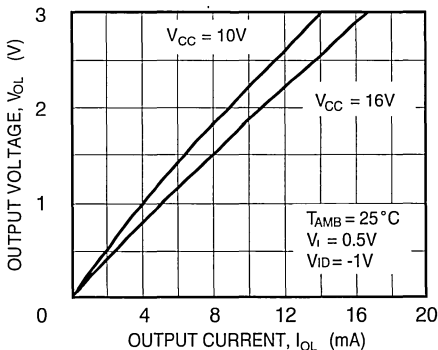


Figure 4b : Low Level Output Voltage versus Low Level Output Current.



TYPICAL CHARACTERISTICS (continued)

Figure 5 : Open Loop Frequency Response and Phase Shift.

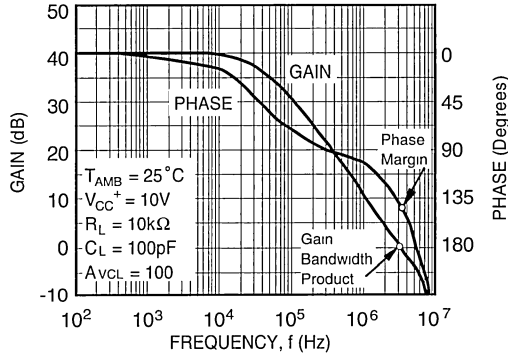


Figure 6 : Gain Bandwidth Product versus Supply Voltage.

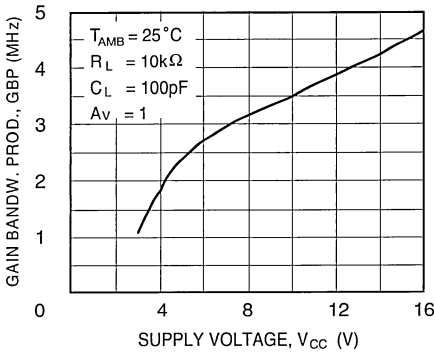


Figure 7 : Phase Margin versus Supply Voltage.

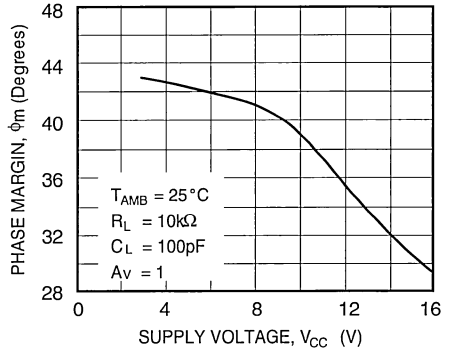


Figure 8 : Phase Margin versus Capacitive Load.

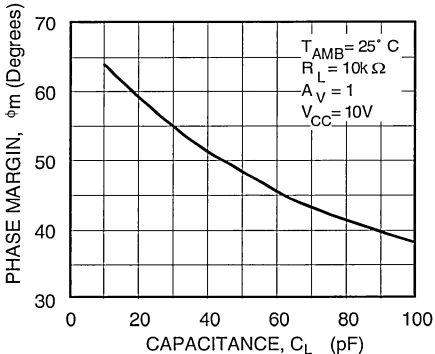
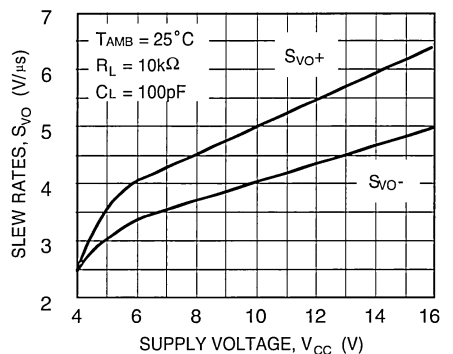
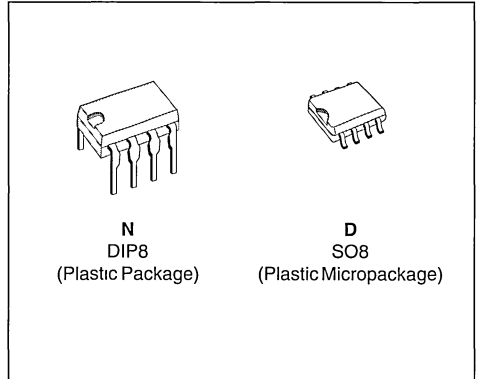


Figure 9 : Slew Rates versus Supply Voltage.



VERY LOW POWER DUAL CMOS OP-AMPS

- EXCELLENT PHASE MARGIN ON CAPACITIVE LOADS
- SYMMETRICAL OUTPUT CURRENTS
- LOW OUTPUT DYNAMIC IMPEDANCE
- THE TRANSFER FUNCTION IS LINEAR
- PIN TO PIN COMPATIBLE WITH STANDARD DUAL OP-AMPS (TL082 -LM358)
- STABLE AND LOW OFFSET VOLTAGE
- INTERNAL ELECTROSTATIC DISCHARGE (ESD) PROTECTION CIRCUITS
- THREE INPUT OFFSET VOLTAGE SELECTIONS : STANDARD (10mV), A (5mV), B (2mV)



ORDER CODES

Part Number	Temperature Range	Package	
		N	D
TS27L2C/AC/BC	0°C to + 70°C	●	●
TS27L2I/AI/BI	- 40°C to + 105°C	●	●
TS27L2M/AM/BM	- 55°C to + 125°C	●	●

Example : TS27L2ACN

DESCRIPTION

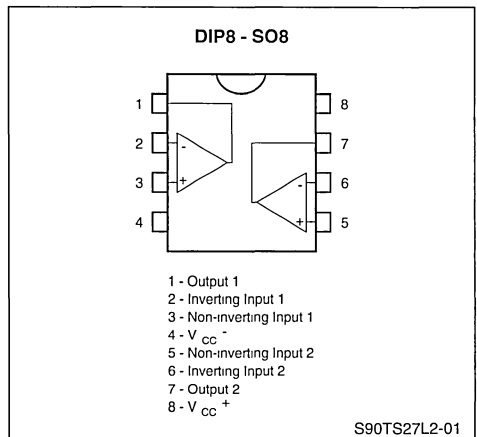
The TS272 series are low cost, low power dual operational amplifiers designed to operate with single or dual supplies. These operational amplifiers use the SGS-THOMSON silicon gate LIN MOS process giving them an excellent consumption-speed ratio. These series are ideally suited for low consumption applications.

Three power consumptions are available allowing to have always the best consumption-speed ratio :

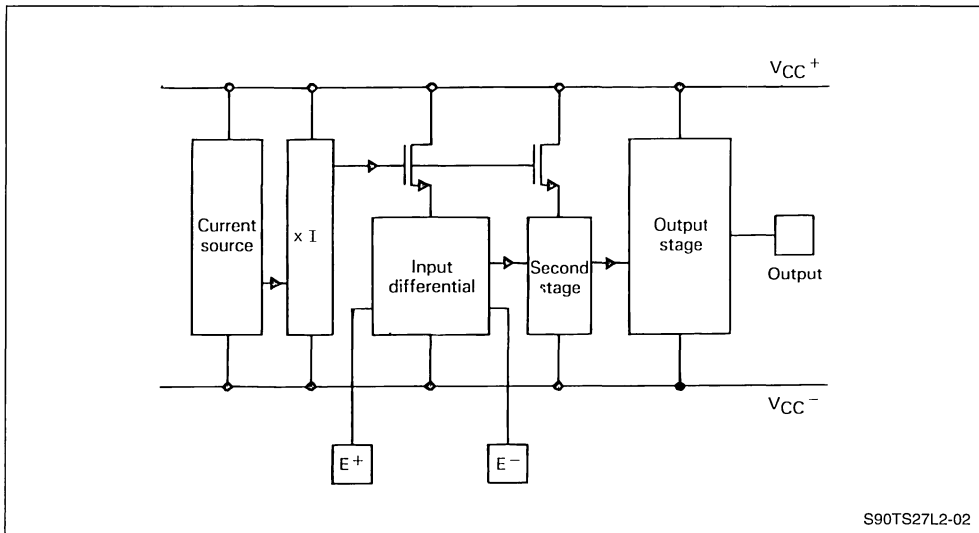
- $I_{CC} = 10\mu\text{A}/\text{amp.}$: TS27L2 (very low power)
- $I_{CC} = 150\mu\text{A}/\text{amp.}$: TS27M2 (low power)
- $I_{CC} = 1\text{mA}/\text{amp.}$: TS272 (high speed)

The input impedance is similar to the J-FET input impedance : very high input impedance and extremely low input offset and bias currents. They allow to minimize the static errors in high impedance applications.

PIN CONNECTIONS (Top view)



BLOCK DIAGRAM



MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage (Note 1)	18	V
V_{id}	Differential Input Voltage (Note 2)	± 18	V
V_i	Input Voltage (Note 3)	- 0.3 to 18	V
I_o	Output Current for $V_{CC}^+ \geq 15V$	± 30	mA
T_{oper}	Operating Free-Air Temperature Range	TS27L2C/AC/BC TS27L2I/AI/BI TS27L2M/AM/BM 0 to + 70 - 40 to + 105 - 55 to + 125	$^{\circ}C$
T_{stg}	Storage Temperature Range	- 65 to + 150	$^{\circ}C$

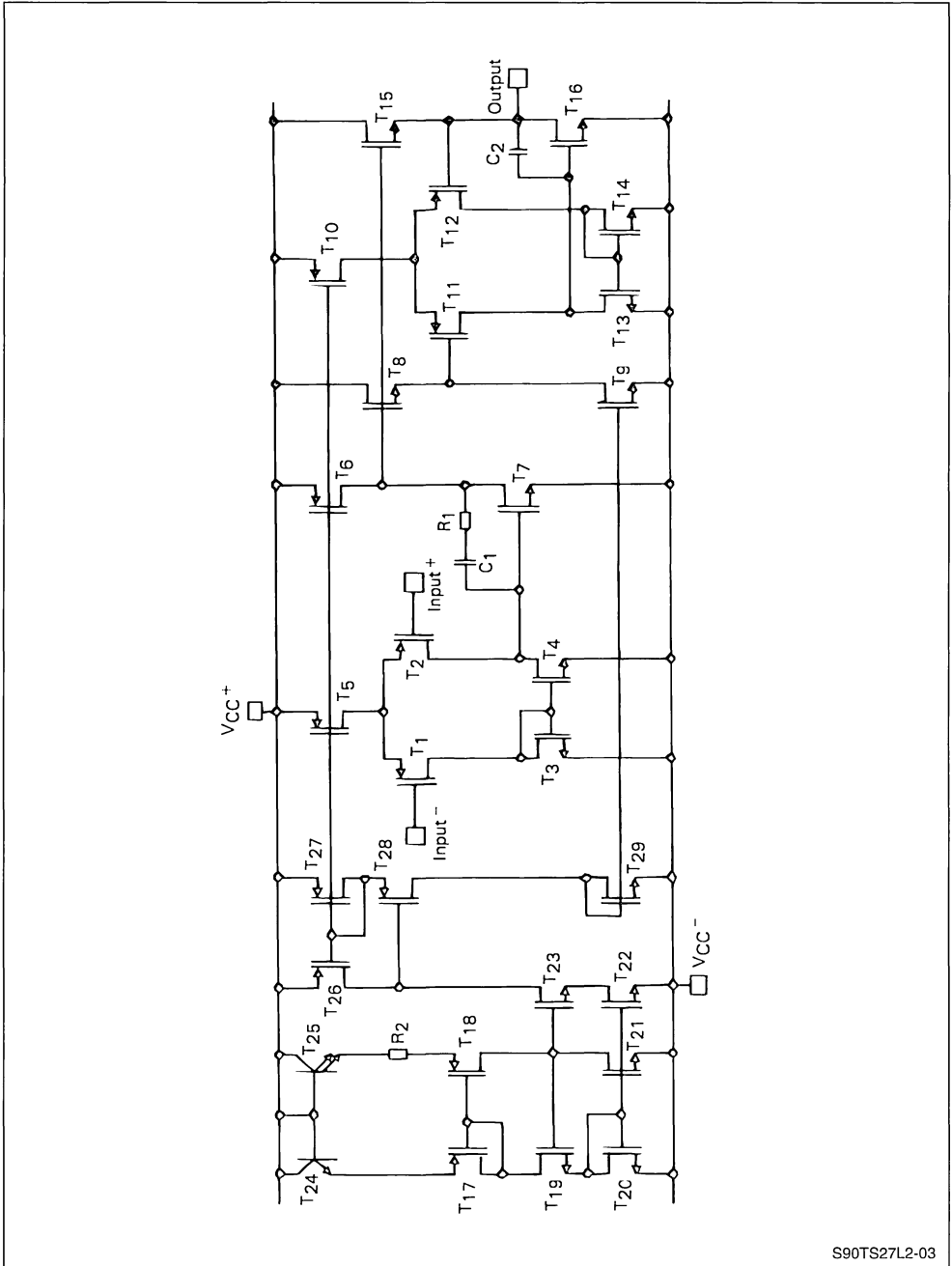
- Notes :
1. All voltage values, except differential voltage, are with respect to network ground terminal.
 2. Differential voltages are at the non-inverting input terminal with respect to the inverting input terminal.
 3. The magnitude of the input and the output voltages must never exceed the magnitude of the postive supply voltage.

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage	3* to 16	V
V_{ic}	Common Mode Input Voltage Range	0 to $V_{CC}^+ - 1.5$	V

* Selected devices only.

SCHEMATIC DIAGRAM (for 1/2 TS27L2)



S90TS27L2-03

ELECTRICAL CHARACTERISTICS

$V_{CC}^+ = +10V$, $V_{CC}^- = 0V$, $T_{AMB} = 25^{\circ}C$ (unless otherwise specified)

Symbol	Parameter	TS27L2C/AC/BC			TS27L2I/AI/BI TS27L2M/AM/BM			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
V_{io}	Input Offset Voltage $V_o = 1.4V$, $V_i = 0V$ TS27L2C/I/M TS27L2AC/AI/AM TS27L2BC/BI/BM $T_{MIN} \leq T_{AMB} \leq T_{MAX}$ TS27L2C/I/M TS27L2AC/AI/AM TS27L2BC/BI/BM		1.1	10		1.1	10	mV
			0.9	5		0.9	5	
			0.25	2		0.25	2	
				12			12	
				6.5			6.5	
				3			3.5	
DV_{io}	Input Offset Voltage Drift		0.7			0.7		$\mu V/^{\circ}C$
I_{io}	Input Offset Current $V_i = 5V$, $V_o = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		1			1		pA
				100			200	
I_{ib}	Input Bias Current $V_i = 5V$, $V_o = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		1			1		pA
				150			300	
V_{OH}	High Level Output Voltage $V_i = 10mV$, $R_L = 1M\Omega$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	8.8	9		8.8	9		V
		8.7			8.6			
V_{OL}	Low Level Output Voltage $V_i = -10mV$			50			50	mV
A_{vd}	Large Signal Voltage Gain $V_o = 1V$ to $6V$, $R_L = 1M\Omega$, $V_i = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	60	100		60	100		V/mV
		45			40			
GBP	Gain Bandwidth Product $A_v = 40dB$, $R_L = 1M\Omega$, $C_L = 100pF$ $f_{in} = 10$ kHz		0.1			0.1		MHz
CMR	Common Mode Rejection Ratio $V_o = 1.4V$, $V_i = 1V$ to $7.4V$	65	80		65	80		dB
SVR	Supply Voltage Rejection Ratio $V_{CC}^+ = 5V$ to $10V$, $V_o = 1.4V$	60	80		60	80		dB
I_{CC}	Supply Current (per amplifier) $A_v = 1$, no load, $V_o = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		10	15		10	15	μA
				17			18	
I_o	Output Short Circuit Current $V_i = 10mV$, $V_o = 0V$	45	60	85	45	60	85	mA
I_{sink}	Output Sink Current $V_i = -10mV$, $V_o = V_{CC}$	35	45	65	35	45	65	mA
S_{vo}	Slew-Rate at Unity Gain $R_L = 1M\Omega$, $C_L = 100pF$		0.04			0.04		V/ μs
ϕ_m	Phase Margin at Unity Gain $A_v = 40$ dB, $R_L = 1M\Omega$, $C_L = 100pF$		45			45		degrees
K_{ov}	Overshoot Factor		30			30		%
V_n	Equivalent Input Noise Voltage $f = 1kHz$, $R_S = 10\Omega$		68			68		nV/\sqrt{Hz}
$VO1/VO2$	Cross Talk Attenuation		120			120		dB

TYPICAL CHARACTERISTICS

Figure 1 : Supply Current (each amplifier) versus Supply Voltage.

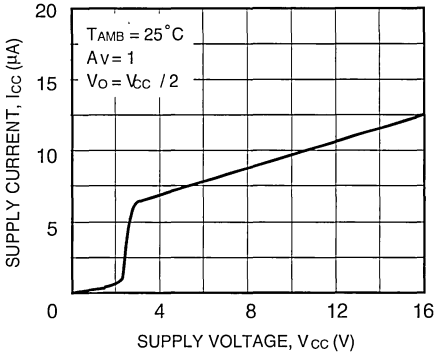


Figure 2 : Input Bias Current versus Free Air Temperature.

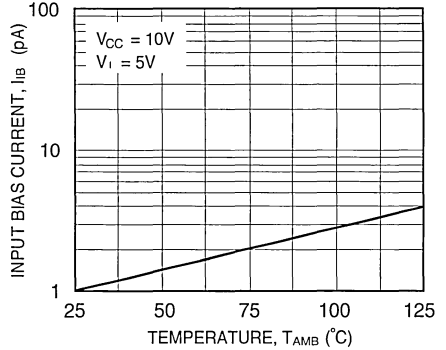


Figure 3a : High Level Output Voltage versus High Level Output Current.

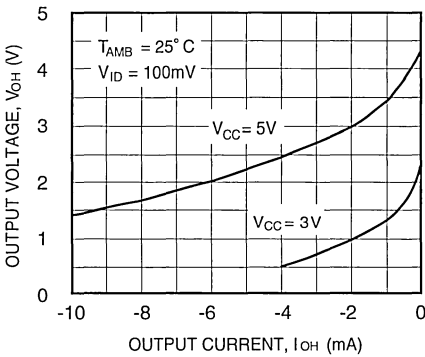


Figure 3b : High Level Output Voltage versus High Level Output Current.

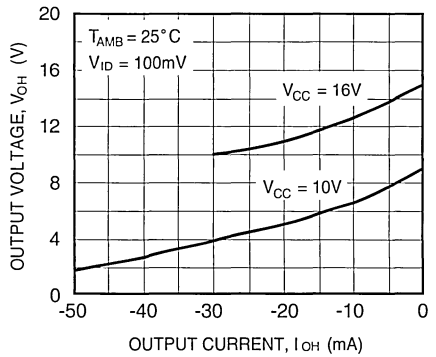


Figure 4a : Low Level Output Voltage versus Low Level Output Current.

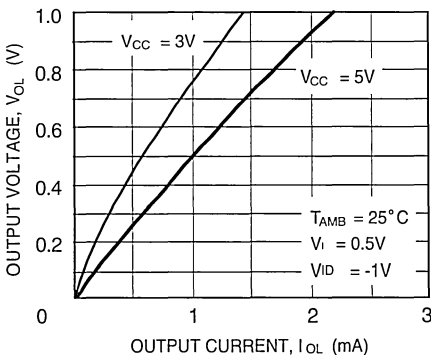
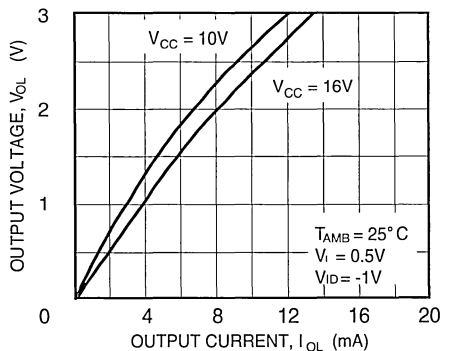


Figure 4b : Low Level Output Voltage versus Low Level Output Current.



TYPICAL CHARACTERISTICS (continued)

Figure 5 : Open Loop Frequency Response and Phase Shift.

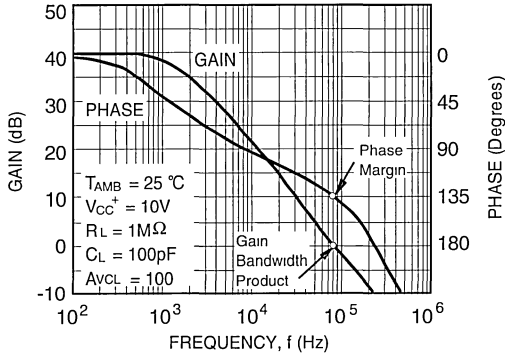


Figure 6 : Gain Bandwidth Product versus Supply Voltage.

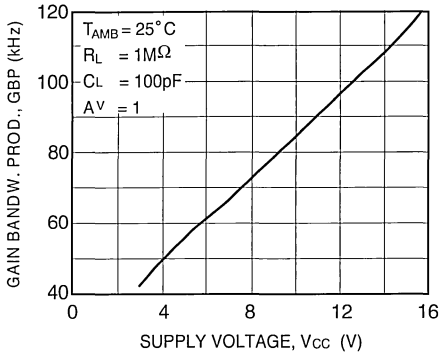


Figure 7 : Phase Margin versus Supply Voltage.

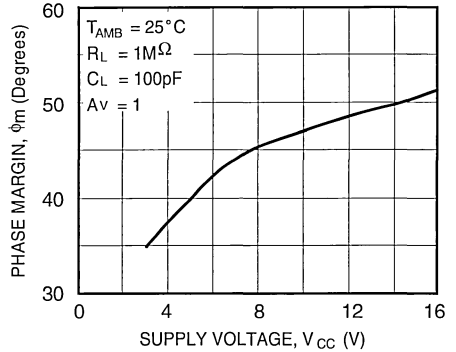


Figure 8 : Phase Margin versus Capacitive Load.

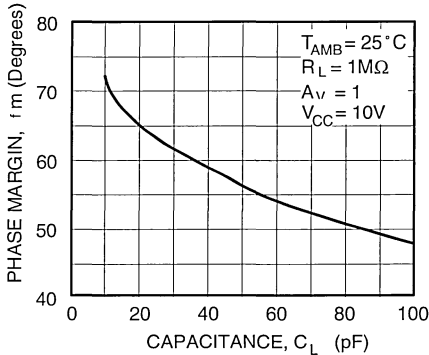
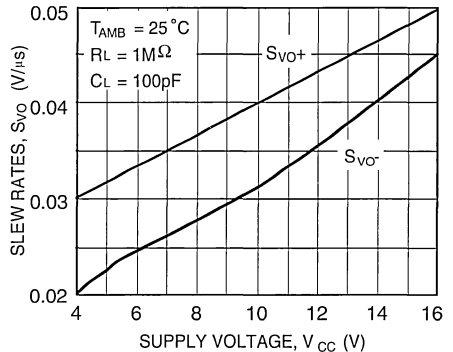
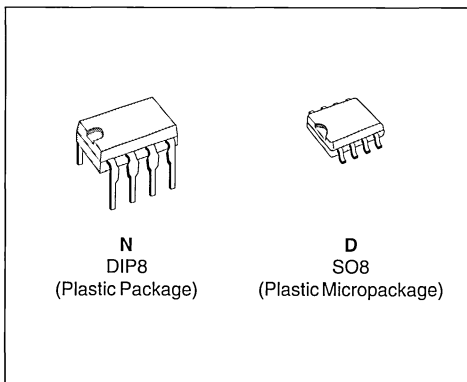


Figure 9 : Slew Rates versus Supply Voltage.



LOW POWER DUAL CMOS OP-AMPS

- EXCELLENT PHASE MARGIN ON CAPACITIVE LOADS
- SYMETRICAL OUTPUT CURRENTS
- LOW OUTPUT DYNAMIC IMPEDANCE
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- PIN TO PIN COMPATIBLE WITH STANDARD DUAL OP-AMPS (TL082 -LM358)
- STABLE AND LOW OFFSET VOLTAGE
- INTERNAL ELECTROSTATIC DISCHARGE (ESD) PROTECTION CIRCUITS
- THREE INPUT OFFSET VOLTAGE SELECTIONS : STANDARD (10mV), A (5mV), B (2mV)



ORDER CODES

Part Number	Temperature Range	Package	
		N	D
TS27M2C/AC/BC	0°C to + 70°C	●	●
TS27M2I/AI/BI	- 40°C to + 105°C	●	●
TS27M2M/AM/BM	- 55°C to + 125°C	●	●

Example : TS27M2ACN

DESCRIPTION

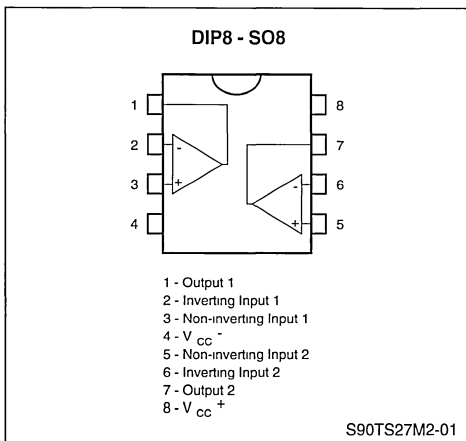
The TS272 series are low cost, low power dual operational amplifiers designed to operate with single or dual supplies. These operational amplifiers use the SGS-THOMSON silicon gate LIN MOS process giving them an excellent consumption-speed ratio. These series are ideally suited for low consumption applications.

Three power consumptions are available allowing to have always the best consumption-speed ratio :

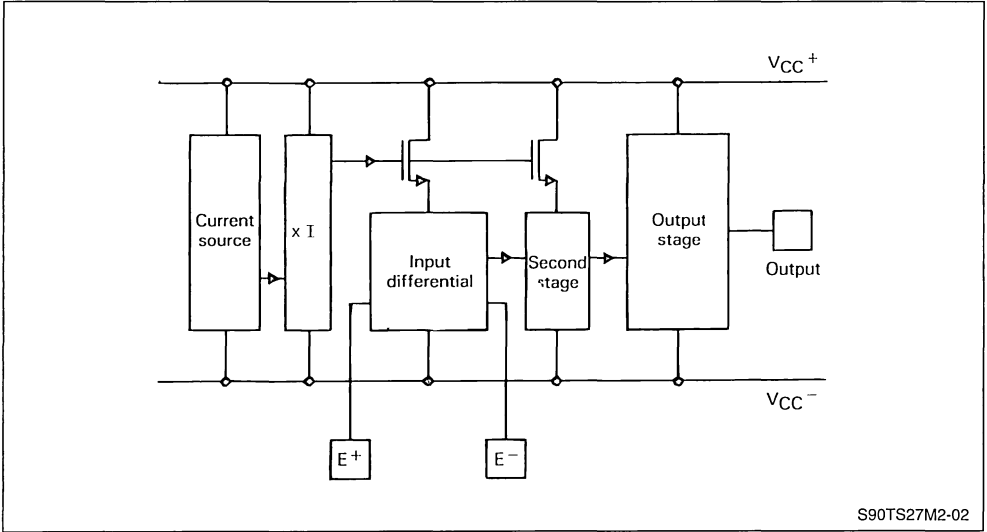
- $I_{CC} = 10\mu A/amp.$: TS27L2 (very low power)
- $I_{CC} = 150\mu A/amp.$: TS27M2 (low power)
- $I_{CC} = 1mA/amp.$: TS272 (high speed)

The input impedance is similar to the J-FET input impedance : very high input impedance and extremely low input offset and bias currents. They allow to minimize the static errors in high impedance applications.

PIN CONNECTIONS (Top view)



BLOCK DIAGRAM



S90TS27M2-02

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage (Note 1)	18	V
V_{id}	Differential Input Voltage (Note 2)	± 18	V
V_i	Input Voltage (Note 3)	- 0.3 to 18	V
I_o	Output Current for $V_{CC}^+ \geq 15V$	± 30	mA
T_{oper}	Operating Free-Air Temperature Range	TS27M2C/AC/BC 0 to + 70 TS27M2I/AI/BI - 40 to + 105 TS27M2M/AM/BM - 55 to + 125	$^{\circ}C$
T_{stg}	Storage Temperature Range	- 65 to + 150	$^{\circ}C$

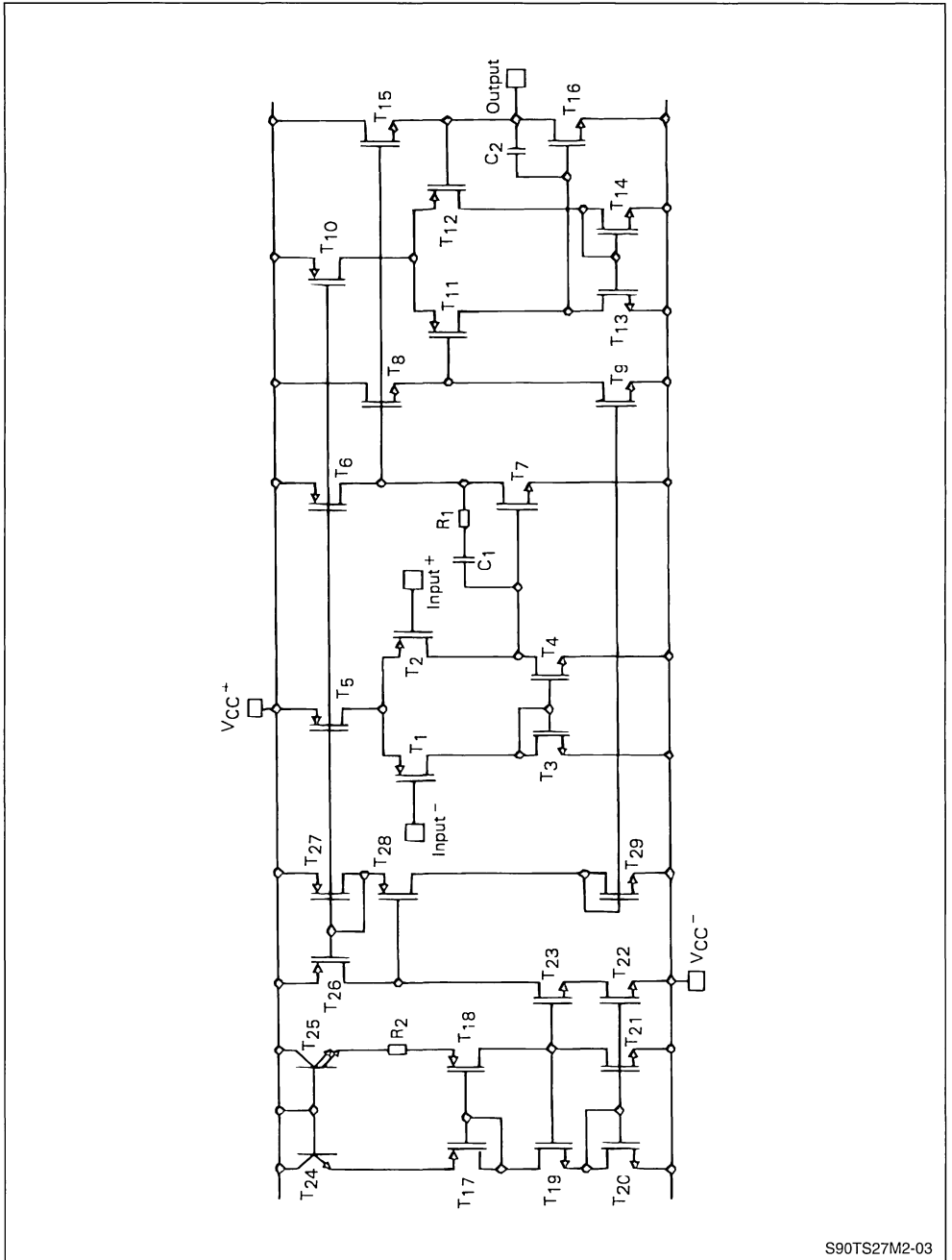
- Notes :
1. All voltage values, except differential voltage, are with respect to network ground terminal
 2. Differential voltages are at the non-inverting input terminal with respect to the inverting input terminal
 3. The magnitude of the input and the output voltages must never exceed the magnitude of the positive supply voltage

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage	3* to 16	V
V_{ic}	Common Mode Input Voltage Range	0 to $V_{CC}^+ - 1.5$	V

* Selected devices only.

SCHEMATIC DIAGRAM (for 1/2 TS27M2)



S90TS27M2-03

ELECTRICAL CHARACTERISTICS

$V_{CC}^+ = +10V$, $V_{CC}^- = 0V$, $T_{AMB} = 25^{\circ}C$ (unless otherwise specified)

Symbol	Parameter	TS27M2C/AC/BC			TS27M2I/AI/BI TS27M2M/AM/BM			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
V_{io}	Input Offset Voltage $V_o = 1.4V$, $V_i = 0V$ TS27M2C/I/M TS27M2AC/AI/AM TS27M2BC/BI/BM $T_{MIN} \leq T_{AMB} \leq T_{MAX}$ TS27M2C/I/M TS27M2AC/AI/AM TS27M2BC/BI/BM		1.1 0.9 0.25	10 5 2		1.1 0.9 0.25	10 5 2	mV
DV_{io}	Input Offset Voltage Drift		2			2		$\mu V/^{\circ}C$
I_{io}	Input Offset Current $V_i = 5V$, $V_o = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		1	100		1	200	pA
I_{ib}	Input Bias Current $V_i = 5V$, $V_o = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		1	150		1	300	pA
V_{OH}	High Level Output Voltage $V_i = 10mV$, $R_L = 100k\Omega$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	8.7 8.6	8.9		8.7 8.5	8.9		V
V_{OL}	Low Level Output Voltage $V_i = -10mV$			50			50	mV
A_{vd}	Large Signal Voltage Gain $V_o = 1V$ to $6V$, $R_L = 100k\Omega$, $V_i = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	30 20	50		30 10	50		V/mV
GBP	Gain Bandwidth Product $A_v = 40dB$, $R_L = 100k\Omega$, $C_L = 100pF$ $f_{in} = 100$ kHz		1			1		MHz
CMR	Common Mode Rejection Ratio $V_o = 1.4V$, $V_i = 1V$ to $7.4V$	65	80		65	80		dB
SVR	Supply Voltage Rejection Ratio $V_{CC}^+ = 5V$ to $10V$, $V_o = 1.4V$	60	80		60	80		dB
I_{CC}	Supply Current (per amplifier) $A_v = 1$, no load, $V_o = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		150	200 250		150	200 300	μA
I_o	Output Short Circuit Current $V_i = 10mV$, $V_o = 0V$	45	60	85	45	60	85	mA
I_{sink}	Output Sink Current $V_i = -10mV$, $V_o = V_{CC}$	35	45	65	35	45	65	mA
S_{vo}	Slew-Rate at Unity Gain $R_L = 100k\Omega$, $C_L = 100pF$		0.6			0.6		V/ μs
ϕ_m	Phase Margin at Unity Gain $A_v = 40$ dB, $R_L = 100k\Omega$, $C_L = 100pF$		45			45		degrees
K_{ov}	Overshoot Factor		30			30		%
V_n	Equivalent Input Noise Voltage $f = 1kHz$, $R_S = 10\Omega$		38			38		nV/\sqrt{Hz}
VO_1/VO_2	Cross Talk Attenuation		120			120		dB

TYPICAL CHARACTERISTICS

Figure 1 : Supply Current (each amplifier) versus Supply Voltage.

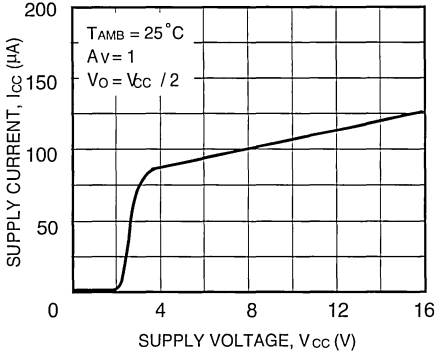


Figure 2 : Input Bias Current versus Free Air Temperature.

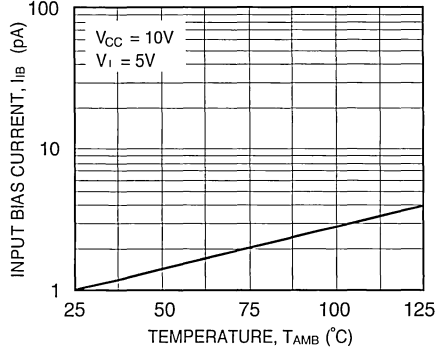


Figure 3a : High Level Output Voltage versus High Level Output Current.

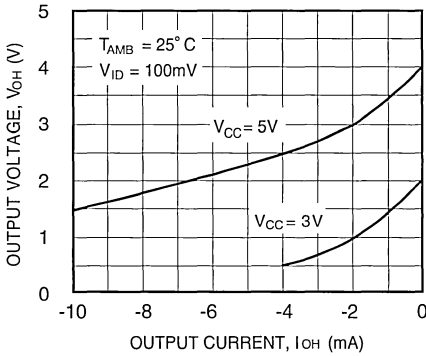


Figure 3b : High Level Output Voltage versus High Level Output Current.

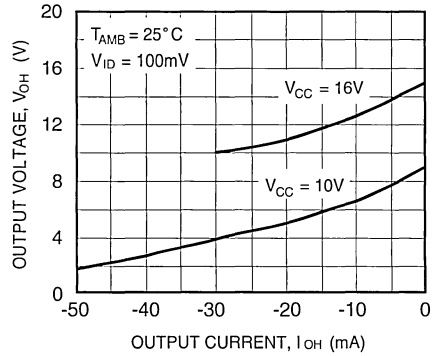


Figure 4a : Low Level Output Voltage versus Low Level Output Current.

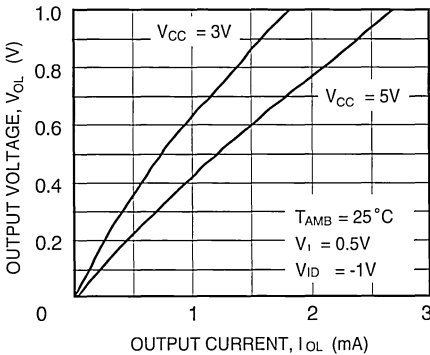
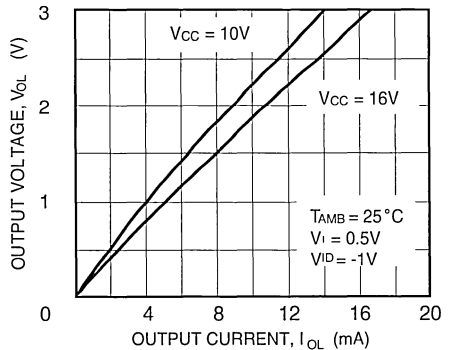


Figure 4b : Low Level Output Voltage versus Low Level Output Current.



TYPICAL CHARACTERISTICS (continued)

Figure 5 : Open Loop Frequency Response and Phase Shift.

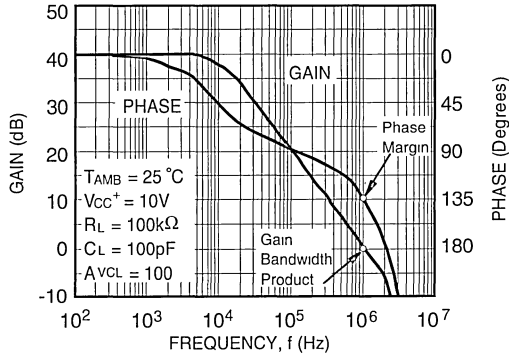


Figure 6 : Gain Bandwidth Product versus Supply Voltage.

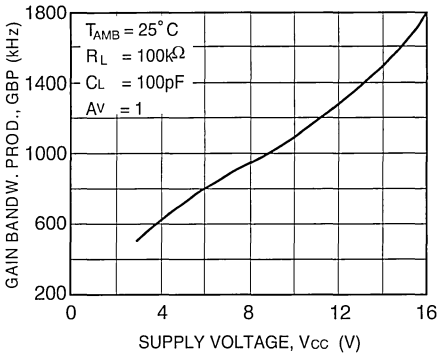


Figure 7 : Phase Margin versus Supply Voltage.

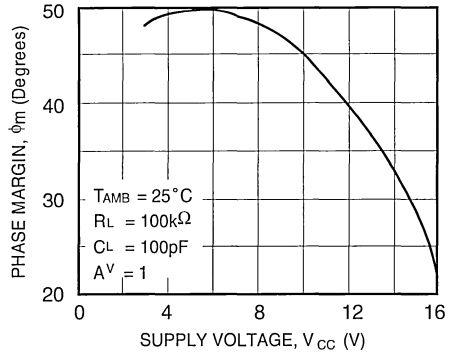


Figure 8 : Phase Margin versus Capacitive Load.

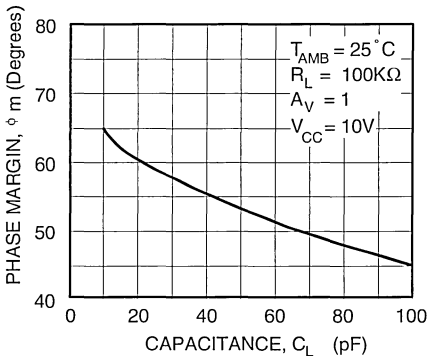
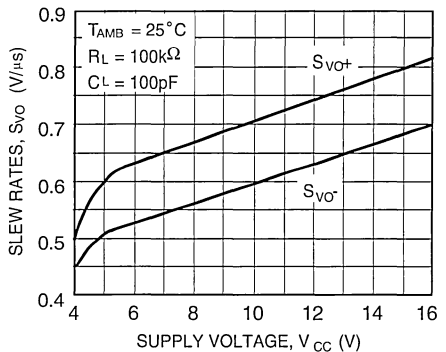


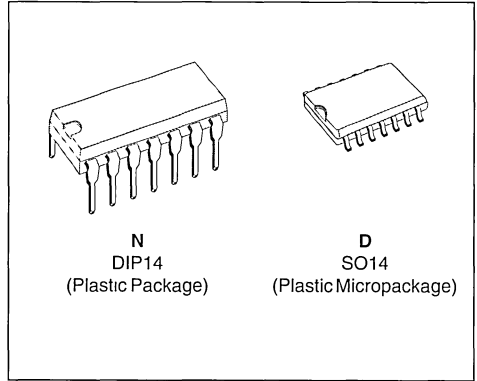
Figure 9 : Slew Rates versus Supply Voltage.





HIGH SPEED QUAD CMOS OP-AMPS

- ▣ EXCELLENT PHASE MARGIN ON CAPACITIVE LOADS
- ▣ SYMETRICAL OUTPUT CURRENTS
- ▣ HIGH GAIN BANDWIDTH PRODUCT
- ▣ LOW OUTPUT DYNAMIC IMPEDANCE
- ▣ THE TRANSFER FUNCTION IS LINEAR
- ▣ PIN TO PIN COMPATIBLE WITH STANDARD QUAD OP-AMPS (TL084 -LM324)
- ▣ STABLE AND LOW OFFSET VOLTAGE
- ▣ INTERNAL ELECTROSTATIC DISCHARGE (ESD) PROTECTION CIRCUITS
- ▣ THREE INPUT OFFSET VOLTAGE SELECTIONS : STANDARD (10mV), A (5mV), B (2mV)



ORDER CODES

Part Number	Temperature Range	Package	
		N	D
TS274C/AC/BC	0°C to + 70°C	○	○
TS274I/AI/BI	- 40°C to + 105°C	○	○
TS274M/AM/BM	- 55°C to + 125°C	○	○

Example : TS274ACN

DESCRIPTION

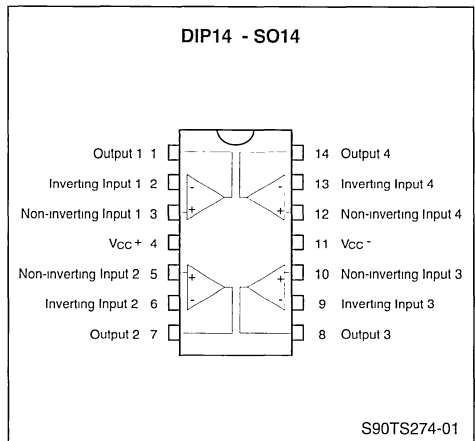
The TS274 series are low cost, low power quad operational amplifiers designed to operate with single or dual supplies. These operational amplifiers use the SGS-THOMSON silicon gate LIN MOS process giving them an excellent consumption-speed ratio. These series are ideally suited for low consumption applications.

Three power consumptions are available allowing to have always the best consumption-speed ratio :

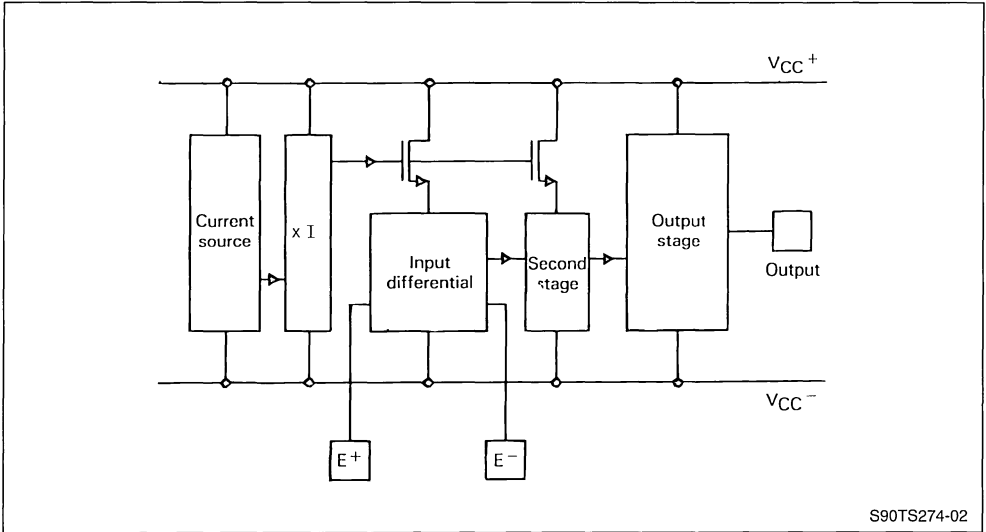
- $I_{CC} = 10\mu A/amp.$: TS27L4 (very low power)
- $I_{CC} = 150\mu A/amp.$: TS27M4 (low power)
- $I_{CC} = 1mA/amp.$: TS274 (high speed)

The input impedance is similar to the J-FET input impedance : very high input impedance and extremely low input offset and bias currents. They allow to minimize the static errors in high impedance applications.

PIN CONNECTIONS (Top view)



BLOCK DIAGRAM



MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V_{CC}^+	Supply Voltage (Note 1)	18	V	
V_{id}	Differential Input Voltage (Note 2)	± 18	V	
V_i	Input Voltage (Note 3)	- 0.3 to 18	V	
I_o	Output Current for $V_{CC}^+ \geq 15V$	± 30	mA	
T_{oper}	Operating Free-Air Temperature Range	TS274C/AC/BC TS274I/AI/BI TS274M/AM/BM	0 to + 70 - 40 to + 105 - 55 to + 125	$^{\circ}C$
T_{slg}	Storage Temperature Range	- 65 to + 150	$^{\circ}C$	

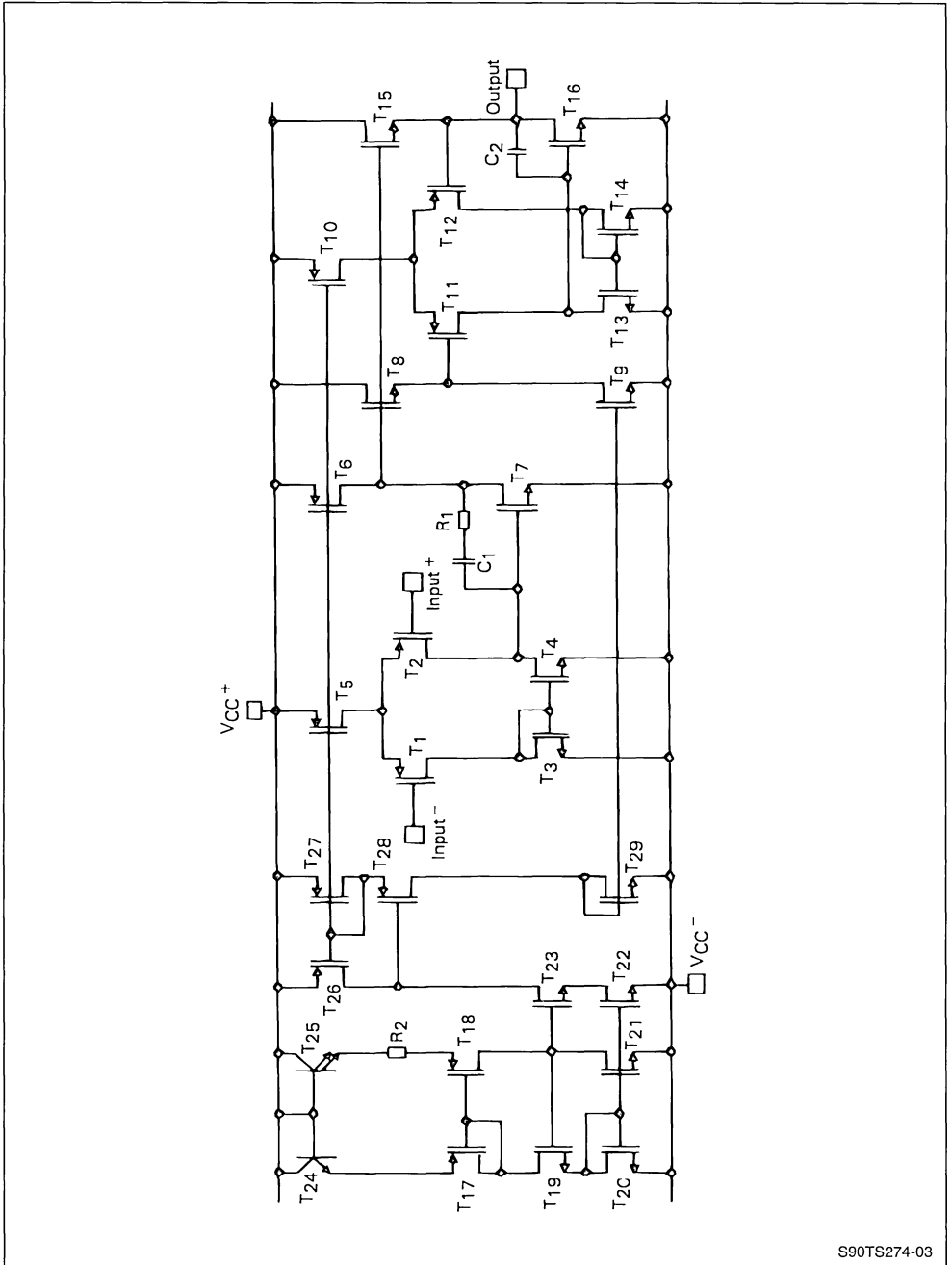
- Notes :
1. All voltage values, except differential voltage, are with respect to network ground terminal.
 2. Differential voltages are at the non-inverting input terminal with respect to the inverting input terminal
 3. The magnitude of the input and the output voltages must never exceed the magnitude of the positive supply voltage

OPTIMAL OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage	3* to 16	V
V_{ic}	Common Mode Input Voltage Range	0 to $V_{CC}^+ - 1.5$	V

* Selected devices only

SCHEMATIC DIAGRAM (for 1/4 TS274)



S90TS274-03

ELECTRICAL CHARACTERISTICS
 $V_{CC}^+ = +10V$, $V_{CC}^- = 0V$, $T_{AMB} = 25^\circ C$ (unless otherwise specified)

Symbol	Parameter	TS274C/AC/BC			TS274I/AI/BI TS274M/AM/BM			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
V_{io}	Input Offset Voltage $V_o = 1.4V$, $V_i = 0V$		1.1	10		1.1	10	mV
	TS274C/I/M TS274AC/AI/AM TS274BC/BI/BM		0.9 0.25	5 2		0.9 0.25	5 2	
	$T_{MIN} \leq T_{AMB} \leq T_{MAX}$			12 6.5 3			12 6.5 3.5	
DV_{io}	Input Offset Voltage Drift		2			2		$\mu V/^\circ C$
I_{io}	Input Offset Current $V_i = 5V$, $V_o = 5V$		1	100		1	200	pA
	$T_{MIN} \leq T_{AMB} \leq T_{MAX}$							
I_{ib}	Input Bias Current $V_i = 5V$, $V_o = 5V$		1	150		1	300	pA
	$T_{MIN} \leq T_{AMB} \leq T_{MAX}$							
V_{OH}	High Level Output Voltage $V_i = 10mV$, $R_L = 10k\Omega$	8.2 8.1	8.4		8.2 8	8.4		V
V_{OL}	Low Level Output Voltage $V_i = -10mV$			50			50	mV
A_{vd}	Large Signal Voltage Gain $V_o = 1V$ to $6V$, $R_L = 10k\Omega$, $V_i = 5V$	10 7	15		10 6	15		V/mV
	$T_{MIN} \leq T_{AMB} \leq T_{MAX}$							
GBP	Gain Bandwidth Product $A_v = 40dB$, $R_L = 10k\Omega$, $C_L = 100pF$ $f_{in} = 200$ kHz		3.5			3.5		MHz
CMR	Common Mode Rejection Ratio $V_o = 1.4V$, $V_i = 1V$ to $7.4V$	65	80		65	80		dB
SVR	Supply Voltage Rejection Ratio $V_{CC}^+ = 5V$ to $10V$, $V_o = 1.4V$	60	70		60	70		dB
I_{CC}	Supply Current (per amplifier) $A_v = 1$, no load, $V_o = 5V$		1000	1500 1600		1000	1500 1700	μA
	$T_{MIN} \leq T_{AMB} \leq T_{MAX}$							
I_o	Output Short Circuit Current $V_i = 10mV$, $V_o = 0V$	45	60	85	45	60	85	mA
I_{sink}	Output Sink Current $V_i = -10mV$, $V_o = V_{CC}$	35	45	65	35	45	65	mA
S_{vo}	Slew-Rate at Unity Gain $R_L = 10k\Omega$, $C_L = 100pF$		5.5			5.5		V/ μs
ϕ_m	Phase Margin at Unity Gain $A_v = 40$ dB, $R_L = 10k\Omega$, $C_L = 100pF$		40			40		degrees
K_{ov}	Overshoot Factor		30			30		%
V_n	Equivalent Input Noise Voltage $f = 1kHz$, $R_S = 10\Omega$		30			30		nV/ \sqrt{Hz}
V_{O1}/V_{O2}	Cross Talk Attenuation		120			120		dB

TYPICAL CHARACTERISTICS

Figure 1 : Supply Current (each amplifier) versus Supply Voltage.

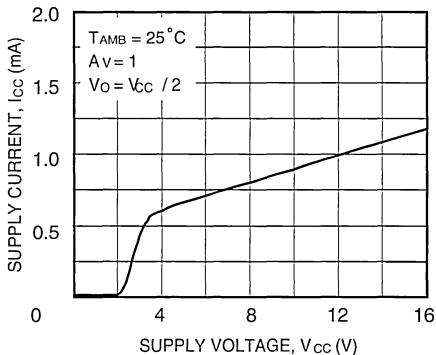


Figure 2 : Input Bias Current versus Free Air Temperature.

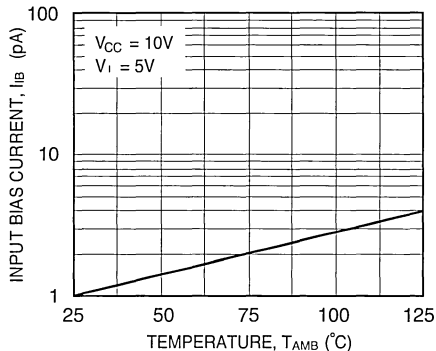


Figure 3a : High Level Output Voltage versus High Level Output Current.

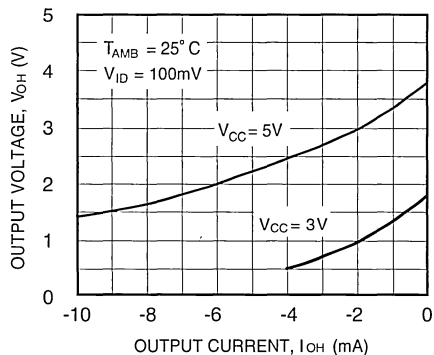


Figure 3b : High Level Output Voltage versus High Level Output Current.

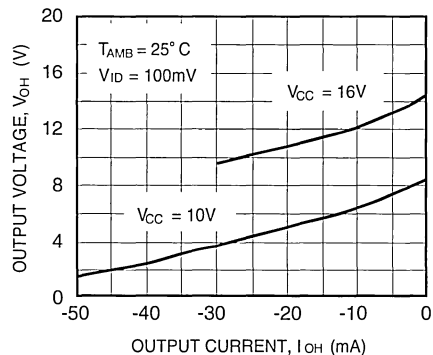


Figure 4a : Low Level Output Voltage versus Low Level Output Current.

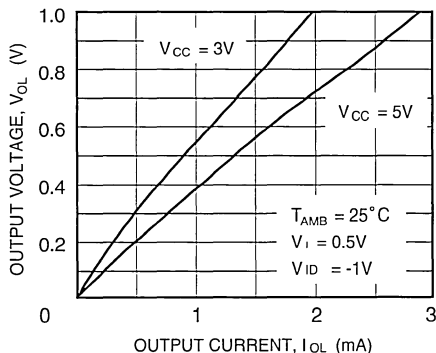
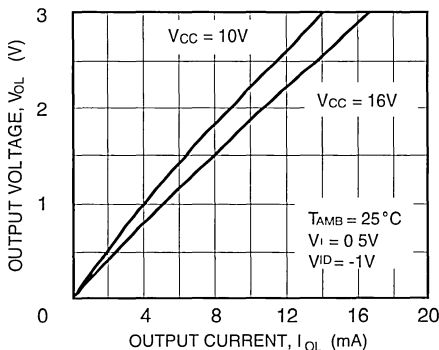


Figure 4b : Low Level Output Voltage versus Low Level Output Current.



TYPICAL CHARACTERISTICS (continued)

Figure 5 : Open Loop Frequency Response and Phase Shift.

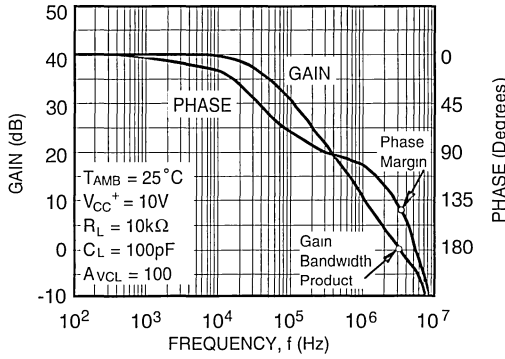


Figure 6 : Gain Bandwidth Product versus Supply Voltage.

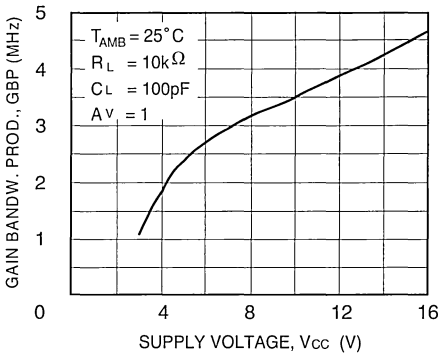


Figure 7 : Phase Margin versus Supply Voltage.

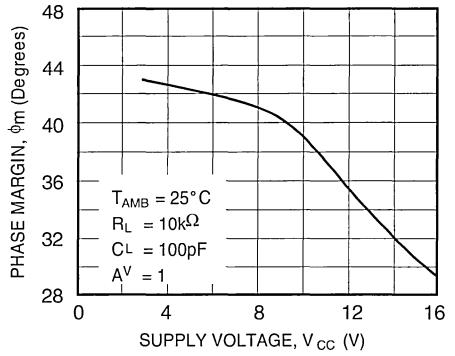


Figure 8 : Phase Margin versus Capacitive Load.

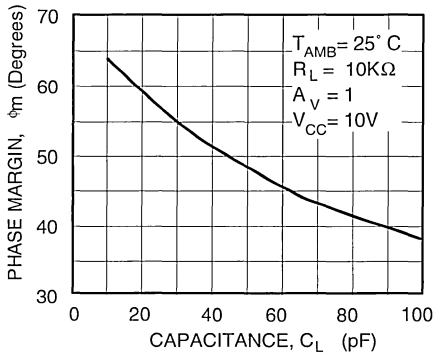
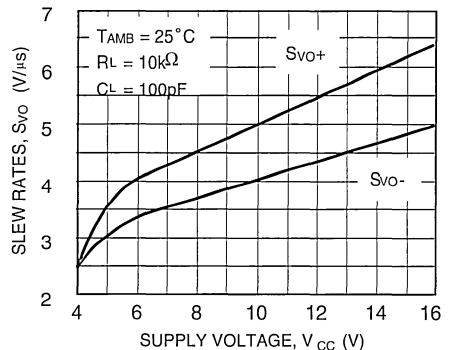
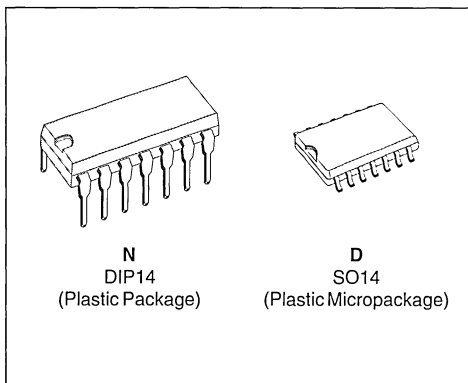


Figure 9 : Slew Rates versus Supply Voltage.



VERY LOW POWER QUAD CMOS OP-AMPS

- EXCELLENT PHASE MARGIN ON CAPACITIVE LOADS
- SYMMETRICAL OUTPUT CURRENTS
- LOW OUTPUT DYNAMIC IMPEDANCE
- THE TRANSFER FUNCTION IS LINEAR
- PIN TO PIN COMPATIBLE WITH STANDARD QUAD OP-AMPS (TL084 -LM324)
- STABLE AND LOW OFFSET VOLTAGE
- INTERNAL ELECTROSTATIC DISCHARGE (ESD) PROTECTION CIRCUITS
- THREE INPUT OFFSET VOLTAGE SELECTIONS : STANDARD (10mV), A (5mV), B (2mV)



ORDER CODES

Part Number	Temperature Range	Package	
		N	D
TS27L4C/AC/BC	0°C to + 70°C	○	○
TS27L4I/AI/BI	- 40°C to + 105°C	○	○
TS27L4M/AM/BM	- 55°C to + 125°C	○	○
Example : TS27L4ACN			

DESCRIPTION

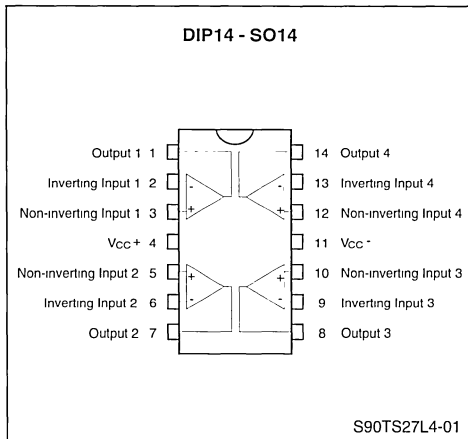
The TS274 series are low cost, low power quad operational amplifiers designed to operate with single or dual supplies. These operational amplifiers use the SGS-THOMSON silicon gate LIN MOS process giving them an excellent consumption-speed ratio. These series are ideally suited for low consumption applications.

Three power consumptions are available allowing to have always the best consumption-speed ratio :

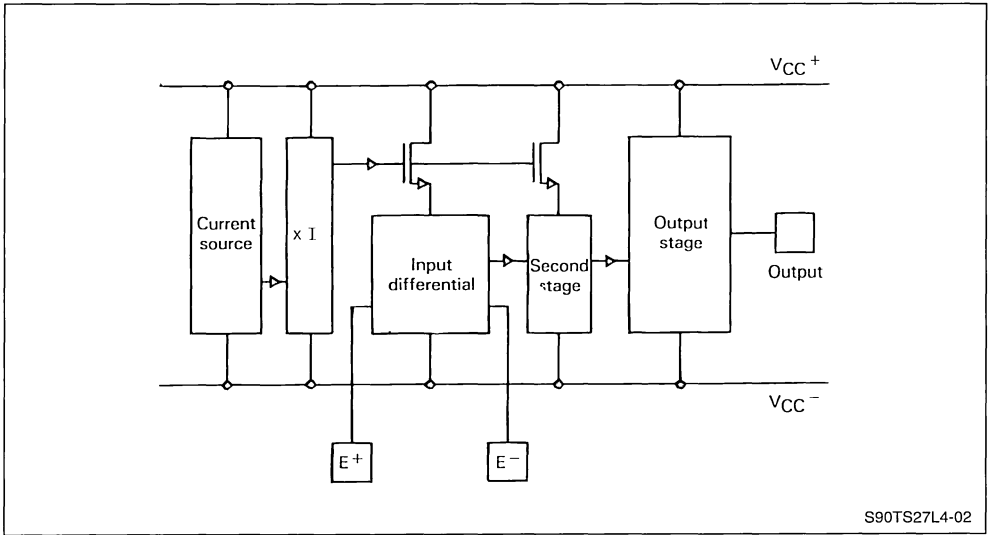
- $I_{CC} = 10\mu\text{A}/\text{amp.}$: TS27L4 (very low power)
- $I_{CC} = 150\mu\text{A}/\text{amp.}$: TS27M4 (low power)
- $I_{CC} = 1\text{mA}/\text{amp.}$: TS274 (high speed)

The input impedance is similar to the J-FET input impedance : very high input impedance and extremely low input offset and bias currents. They allow to minimize the static errors in high impedance applications.

PIN CONNECTIONS (Top view)



BLOCK DIAGRAM



S90TS27L4-02

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage (Note 1)	18	V
V_{id}	Differential Input Voltage (Note 2)	± 18	V
V_i	Input Voltage (Note 3)	- 0.3 to 18	V
I_o	Output Current for $V_{CC}^+ \geq 15V$	± 30	mA
T_{oper}	Operating Free-Air Temperature Range	TS27L4C/AC/BC TS27L4I/AI/BI TS27L4M/AM/BM 0 to + 70 - 40 to + 105 - 55 to + 125	$^{\circ}C$
T_{slg}	Storage Temperature Range	- 65 to + 150	$^{\circ}C$

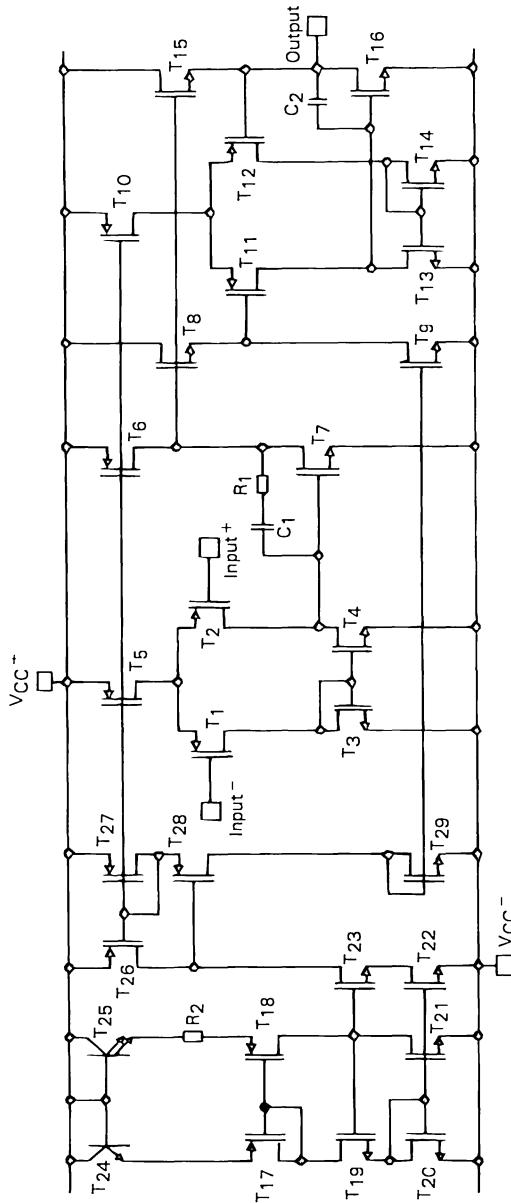
- Notes :
1. All voltage values, except differential voltage, are with respect to network ground terminal
 2. Differential voltages are at the non-inverting input terminal with respect to the inverting input terminal
 3. The magnitude of the input and the output voltages must never exceed the magnitude of the positive supply voltage.

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage	3* to 16	V
V_{ic}	Common Mode Input Voltage Range	0 to $V_{CC}^+ - 1.5$	V

* Selected devices only

SCHEMATIC DIAGRAM (for 1/4 TS27L4)



S90TS27L4-03

ELECTRICAL CHARACTERISTICS
 $V_{CC}^+ = +10V$, $V_{CC}^- = 0V$, $T_{AMB} = 25^{\circ}C$ (unless otherwise specified)

Symbol	Parameter	TS27L4C/AC/BC			TS27L4I/AI/BI TS27L4M/AM/BM			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
V_{io}	Input Offset Voltage $V_o = 1.4V$, $V_i = 0V$							mV
	TS27L4C/I/M TS27L4AC/AI/AM TS27L4BC/BI/BM		1.1 0.9 0.25	10 5 2		1.1 0.9 0.25	10 5 2	
	$T_{MIN} \leq T_{AMB} \leq T_{MAX}$			12 6.5 3			12 6.5 3.5	
DV_{io}	Input Offset Voltage Drift		0.7			0.7		$\mu V/^{\circ}C$
I_{io}	Input Offset Current $V_i = 5V$, $V_o = 5V$		1			1		pA
	$T_{MIN} \leq T_{AMB} \leq T_{MAX}$			100			200	
I_{ib}	Input Bias Current $V_i = 5V$, $V_o = 5V$		1			1		pA
	$T_{MIN} \leq T_{AMB} \leq T_{MAX}$			150			300	
V_{OH}	High Level Output Voltage $V_i = 10mV$, $R_L = 1M\Omega$	8.8 8.7	9		8.8 8.6	9		V
	$T_{MIN} \leq T_{AMB} \leq T_{MAX}$							
V_{OL}	Low Level Output Voltage $V_i = -10mV$			50			50	mV
A_{vd}	Large Signal Voltage Gain $V_o = 1V$ to $6V$, $R_L = 1M\Omega$, $V_i = 5V$	60 45	100		60 40	100		V/mV
	$T_{MIN} \leq T_{AMB} \leq T_{MAX}$							
GBP	Gain Bandwidth Product $A_v = 40dB$, $R_L = 1M\Omega$, $C_L = 100pF$ $f_{in} = 10$ kHz		0.1			0.1		MHz
CMR	Common Mode Rejection Ratio $V_o = 1.4V$, $V_i = 1V$ to $7.4V$	65	80		65	80		dB
SVR	Supply Voltage Rejection Ratio $V_{CC}^+ = 5V$ to $10V$, $V_o = 1.4V$	60	80		60	80		dB
I_{CC}	Supply Current (per amplifier) $A_v = 1$, no load, $V_o = 5V$		10	15 17		10	15 18	μA
	$T_{MIN} \leq T_{AMB} \leq T_{MAX}$							
I_o	Output Short Circuit Current $V_i = 10mV$, $V_o = 0V$	45	60	85	45	60	85	mA
I_{sink}	Output Sink Current $V_i = -10mV$, $V_o = V_{CC}$	35	45	65	35	45	65	mA
S_{vo}	Slew-Rate at Unity Gain $R_L = 1M\Omega$, $C_L = 100pF$		0.04			0.04		V/ μs
$\emptyset m$	Phase Margin at Unity Gain $A_v = 40$ dB, $R_L = 1M\Omega$, $C_L = 100pF$		45			45		degrees
K_{ov}	Overshoot Factor		30			30		%
V_n	Equivalent Input Noise Voltage $f = 1kHz$, $R_S = 10\Omega$		68			68		nV/\sqrt{Hz}
$VO1/VO2$	Cross Talk Attenuation		120			120		dB

TYPICAL CHARACTERISTICS

Figure 1 : Supply Current (each amplifier) versus Supply Voltage.

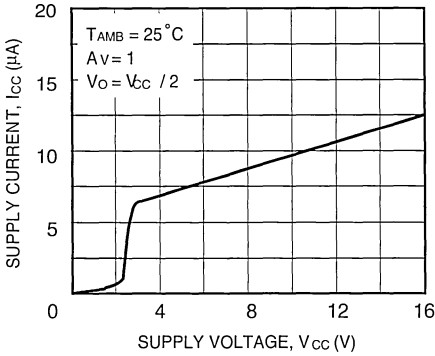


Figure 2 : Input Bias Current versus Free Air Temperature.

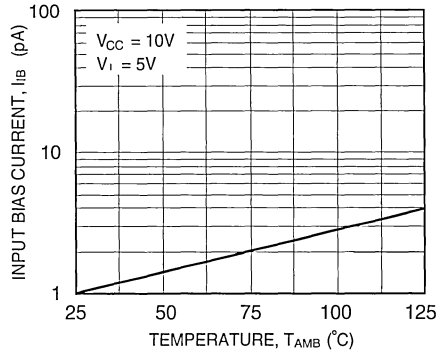


Figure 3a : High Level Output Voltage versus High Level Output Current.

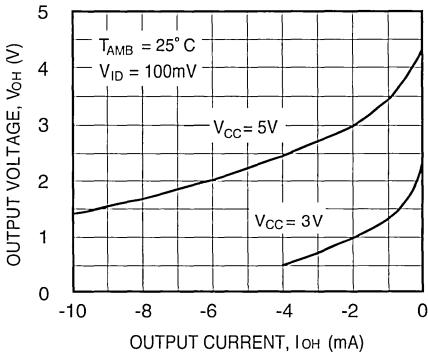


Figure 3b : High Level Output Voltage versus High Level Output Current.

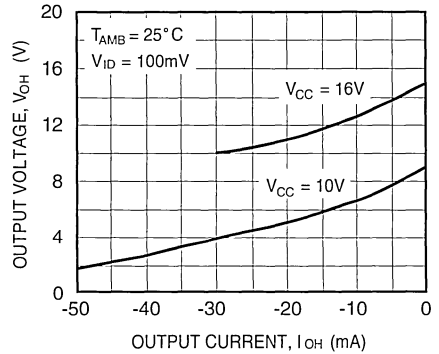


Figure 4a : Low Level Output Voltage versus Low Level Output Current.

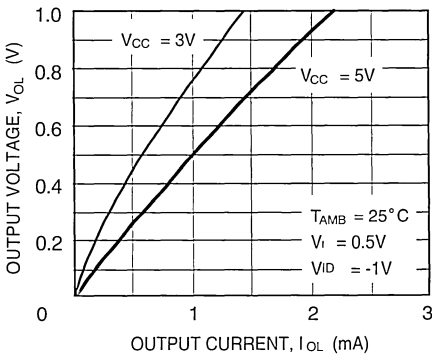
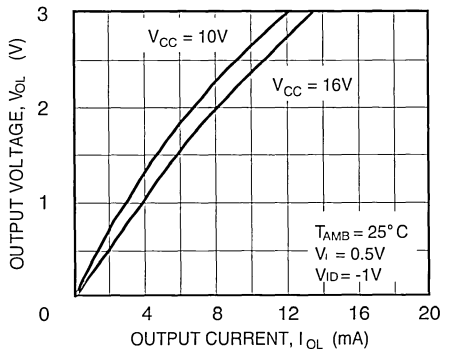


Figure 4b : Low Level Output Voltage versus Low Level Output Current.



TYPICAL CHARACTERISTICS (continued)

Figure 5 : Open Loop Frequency Response and Phase Shift.

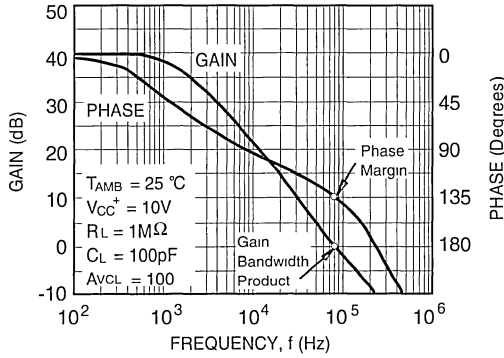


Figure 6 : Gain Bandwidth Product versus Supply Voltage.

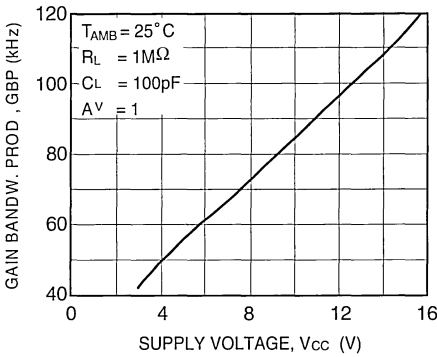


Figure 7 : Phase Margin versus Supply Voltage.

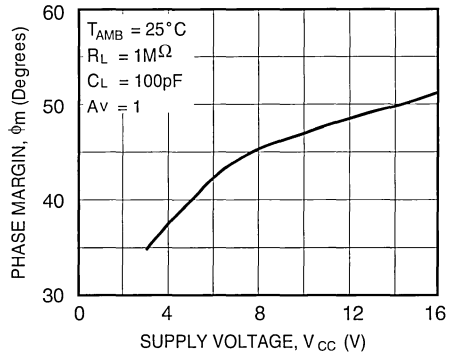


Figure 8 : Phase Margin versus Capacitive Load.

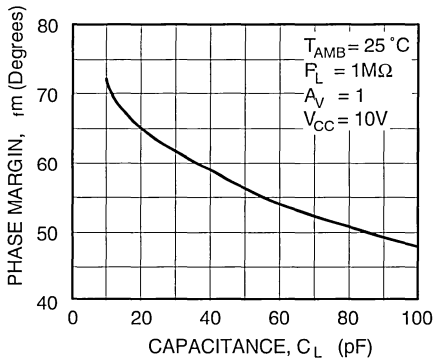
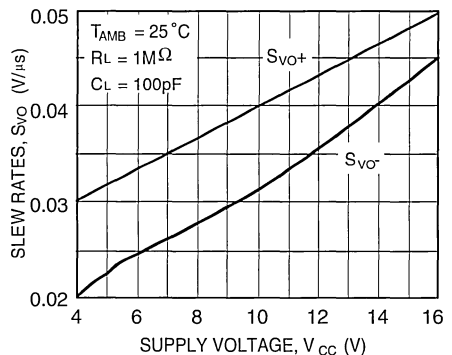


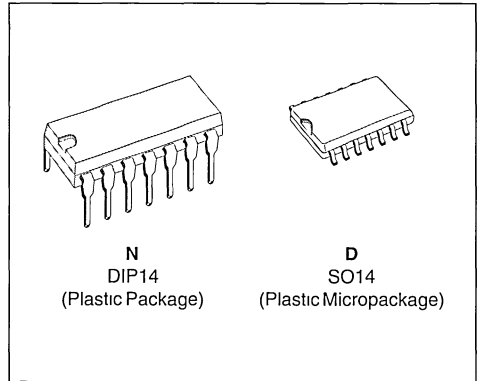
Figure 9 : Slew Rates versus Supply Voltage.





LOW POWER QUAD CMOS OP-AMPS

- EXCELLENT PHASE MARGIN ON CAPACITIVE LOADS
- SYMMETRICAL OUTPUT CURRENTS
- LOW OUTPUT DYNAMIC IMPEDANCE
- THE TRANSFER FUNCTION IS LINEAR
- PIN TO PIN COMPATIBLE WITH STANDARD QUAD OP-AMPS (TL084 -LM324)
- STABLE AND LOW OFFSET VOLTAGE
- INTERNAL ELECTROSTATIC DISCHARGE (ESD) PROTECTION CIRCUITS
- THREE INPUT OFFSET VOLTAGE SELECTIONS : STANDARD (10mV), A (5mV), B (2mV)



ORDER CODES

Part Number	Temperature Range	Package	
		N	D
TS27M4C/AC/BC	0°C to + 70°C	•	•
TS27M4I/AI/BI	- 40°C to + 105°C	•	•
TS27M4M/AM/BM	- 55°C to + 125°C	•	•

Example : TS27M4ACN

DESCRIPTION

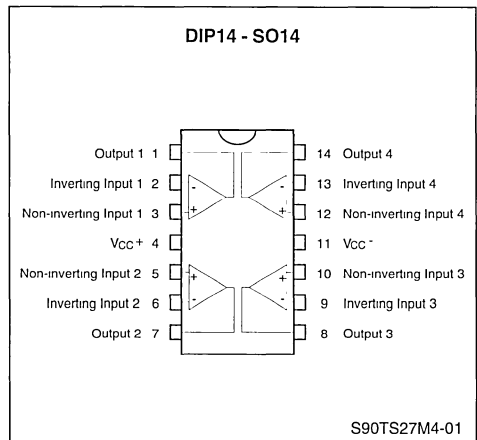
The TS274 series are low cost, low power quad operational amplifiers designed to operate with single or dual supplies. These operational amplifiers use the SGS-THOMSON silicon gate LIN MOS process giving them an excellent consumption-speed ratio. These series are ideally suited for low consumption applications.

Three power consumptions are available allowing to have always the best consumption-speed ratio :

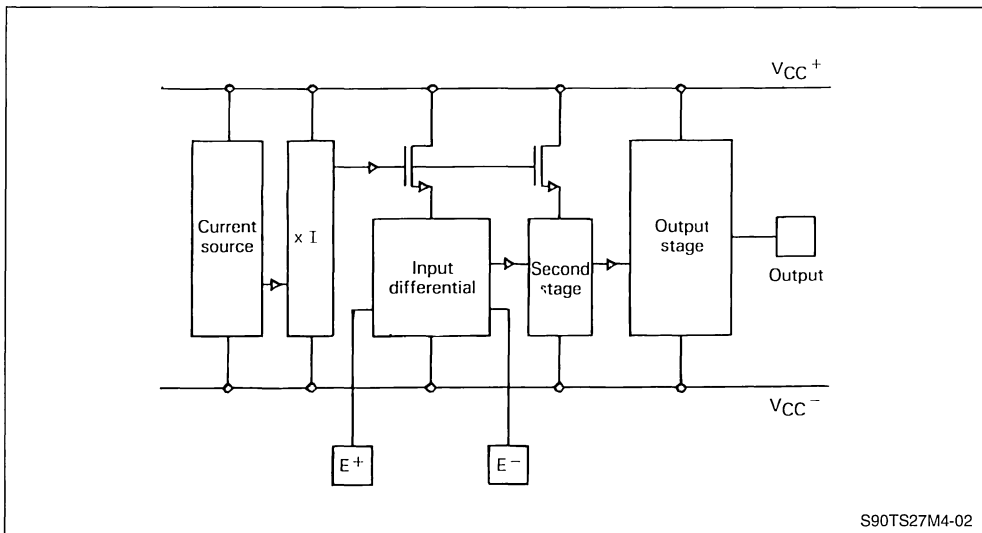
- $I_{CC} = 10\mu\text{A/amp.}$: TS27L4 (very low power)
- $I_{CC} = 150\mu\text{A/amp.}$: TS27M4 (low power)
- $I_{CC} = 1\text{mA/amp.}$: TS274 (high speed)

The input impedance is similar to the J-FET input impedance : very high input impedance and extremely low input offset and bias currents. They allow to minimize the static errors in high impedance applications.

PIN CONNECTIONS (Top view)



BLOCK DIAGRAM



MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC+}	Supply Voltage (Note 1)	18	V
V_{id}	Differential Input Voltage (Note 2)	± 18	V
V_i	Input Voltage (Note 3)	- 0.3 to 18	V
I_o	Output Current for $V_{CC+} \geq 15V$	± 30	mA
T_{oper}	Operating Free-Air Temperature Range	TS27M4C/AC/BC 0 to + 70 TS27M4I/AI/BI - 40 to + 105 TS27M4M/AM/BM - 55 to + 125	$^{\circ}C$
T_{slg}	Storage Temperature Range	- 65 to + 150	$^{\circ}C$

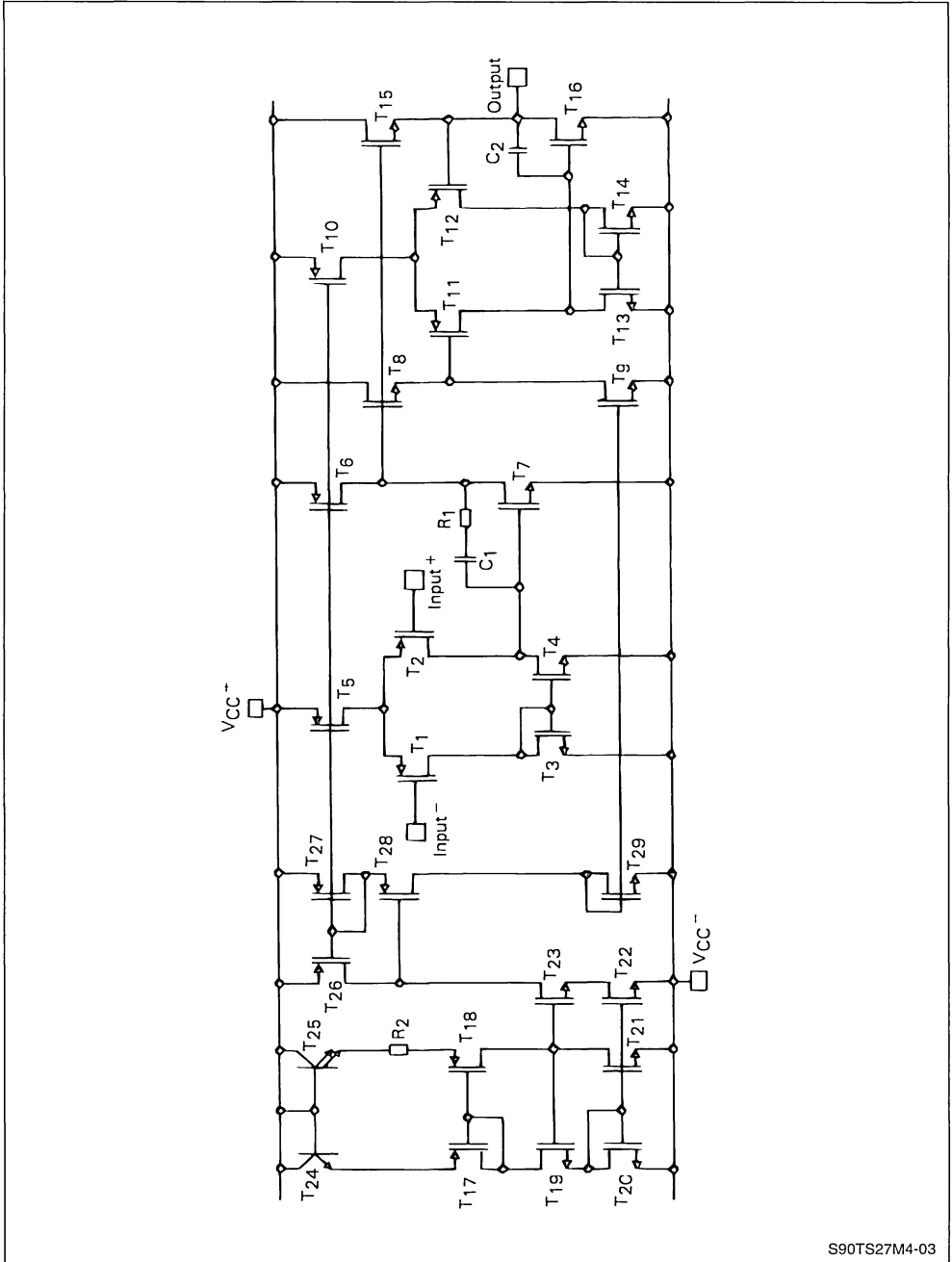
- Notes :
- 1 All voltage values, except differential voltage, are with respect to network ground terminal
 - 2 Differential voltages are at the non-inverting input terminal with respect to the inverting input terminal
 - 3 The magnitude of the input and the output voltages must never exceed the magnitude of the positive supply voltage.

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC+}	Supply Voltage	3* to 16	V
V_{ic}	Common Mode Input Voltage Range	0 to $V_{CC+} - 1.5$	V

* Selected devices only.

SCHEMATIC DIAGRAM (for 1/4 TS27M4)



S90TS27M4-03

ELECTRICAL CHARACTERISTICS

$V_{CC}^+ = +10V$, $V_{CC}^- = 0V$, $T_{AMB} = 25^{\circ}C$ (unless otherwise specified)

Symbol	Parameter	TS27M4C/AC/BC			TS27M4I/AI/BI TS27M4M/AM/BM			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
V_{io}	Input Offset Voltage $V_o = 1.4V$, $V_i = 0V$ TS27M4C/I/M TS27M4AC/AI/AM TS27M4BC/BI/BM $T_{MIN} \leq T_{AMB} \leq T_{MAX}$ TS27M4C/I/M TS27M4AC/AI/AM TS27M4BC/BI/BM		1.1 0.9 0.25	10 5 2		1.1 0.9 0.25	10 5 2	mV
DV_{io}	Input Offset Voltage Drift		2			2		$\mu V/^{\circ}C$
I_{io}	Input Offset Current $V_i = 5V$, $V_o = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		1	100		1	200	pA
I_{ib}	Input Bias Current $V_i = 5V$, $V_o = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		1	150		1	300	pA
V_{OH}	High Level Output Voltage $V_i = 10mV$, $R_L = 100k\Omega$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	8.7 8.6	8.9		8.7 8.5	8.9		V
V_{OL}	Low Level Output Voltage $V_i = -10mV$			50			50	mV
A_{vd}	Large Signal Voltage Gain $V_o = 1V$ to $6V$, $R_L = 100k\Omega$, $V_i = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	30 20	50		30 10	50		V/mV
GBP	Gain Bandwidth Product $A_v = 40dB$, $R_L = 100k\Omega$, $C_L = 100pF$ $f_{in} = 100$ kHz		1			1		MHz
CMR	Common Mode Rejection Ratio $V_o = 1.4V$, $V_i = 1V$ to $7.4V$	65	80		65	80		dB
SVR	Supply Voltage Rejection Ratio $V_{CC}^+ = 5V$ to $10V$, $V_o = 1.4V$	60	80		60	80		dB
I_{CC}	Supply Current (per amplifier) $A_v = 1$, no load, $V_o = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		150	200 250		150	200 300	μA
I_o	Output Short Circuit Current $V_i = 10mV$, $V_o = 0V$	45	60	85	45	60	85	mA
I_{sink}	Output Sink Current $V_i = -10mV$, $V_o = V_{CC}$	35	45	65	35	45	65	mA
S_{vo}	Slew-Rate at Unity Gain $R_L = 100k\Omega$, $C_L = 100pF$		0.6			0.6		V/ μs
ϕ_m	Phase Margin at Unity Gain $A_v = 40$ dB, $R_L = 100k\Omega$, $C_L = 100pF$		45			45		degrees
K_{ov}	Overshoot Factor		30			30		%
V_n	Equivalent Input Noise Voltage $f = 1kHz$, $R_S = 10\Omega$		38			38		nV/ \sqrt{Hz}
V_{O1}/V_{O2}	Cross Talk Attenuation		120			120		dB

TYPICAL CHARACTERISTICS

Figure 1 : Supply Current (each amplifier) versus Supply Voltage.

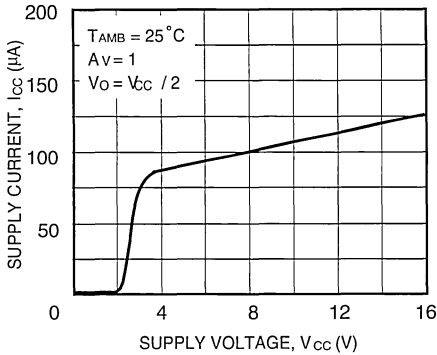


Figure 2 : Input Bias Current versus Free Air Temperature.

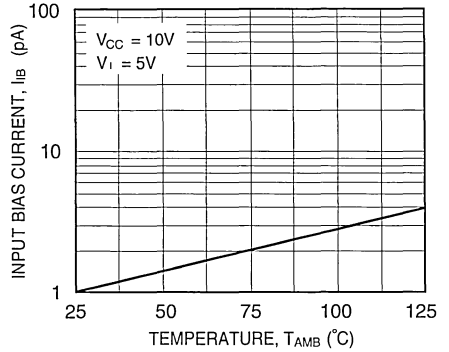


Figure 3a : High Level Output Voltage versus High Level Output Current.

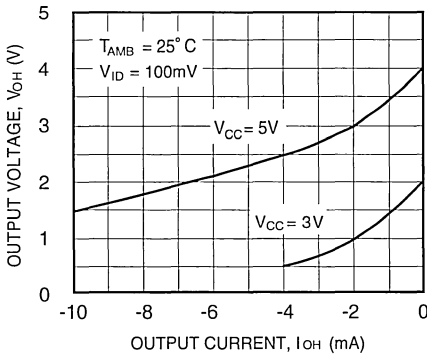


Figure 3b : High Level Output Voltage versus High Level Output Current.

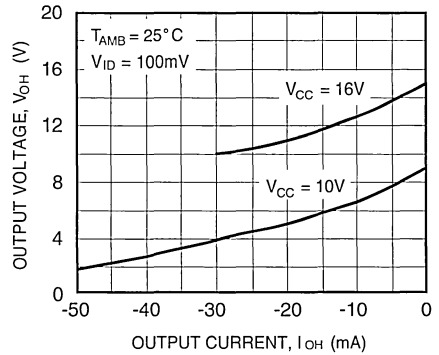


Figure 4a : Low Level Output Voltage versus Low Level Output Current.

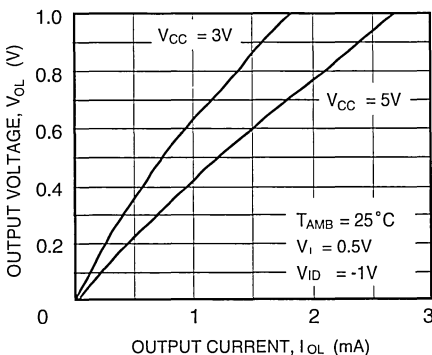
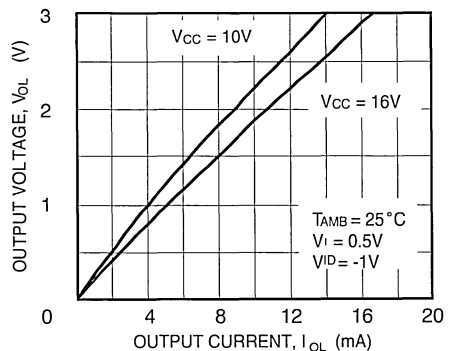


Figure 4b : Low Level Output Voltage versus Low Level Output Current.



TYPICAL CHARACTERISTICS (continued)

Figure 5 : Open Loop Frequency Response and Phase Shift.

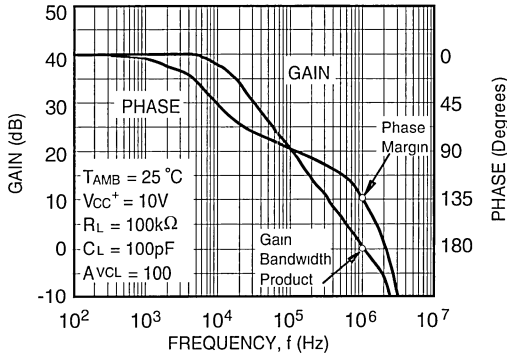


Figure 6 : Gain Bandwidth Product versus Supply Voltage.

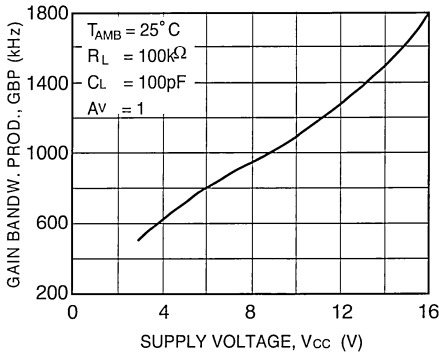


Figure 7 : Phase Margin versus Supply Voltage.

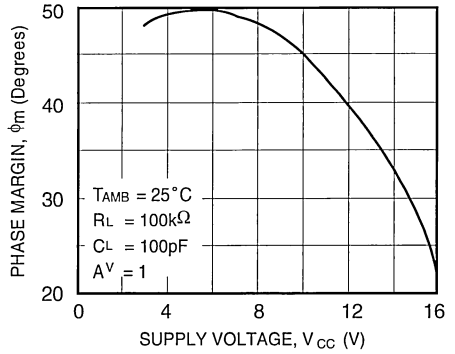


Figure 8 : Phase Margin versus Capacitive Load.

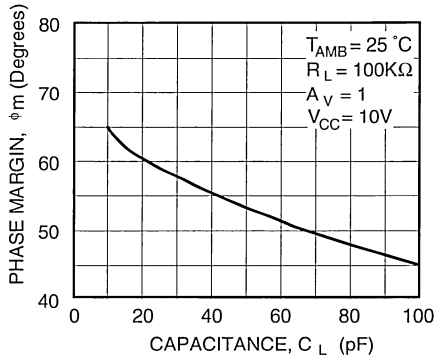
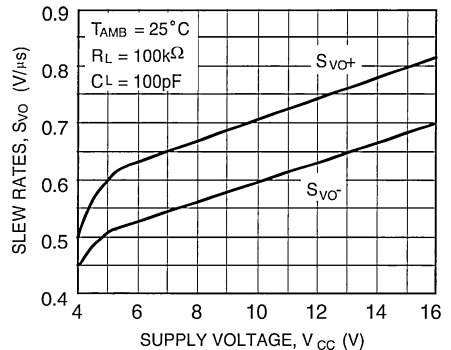
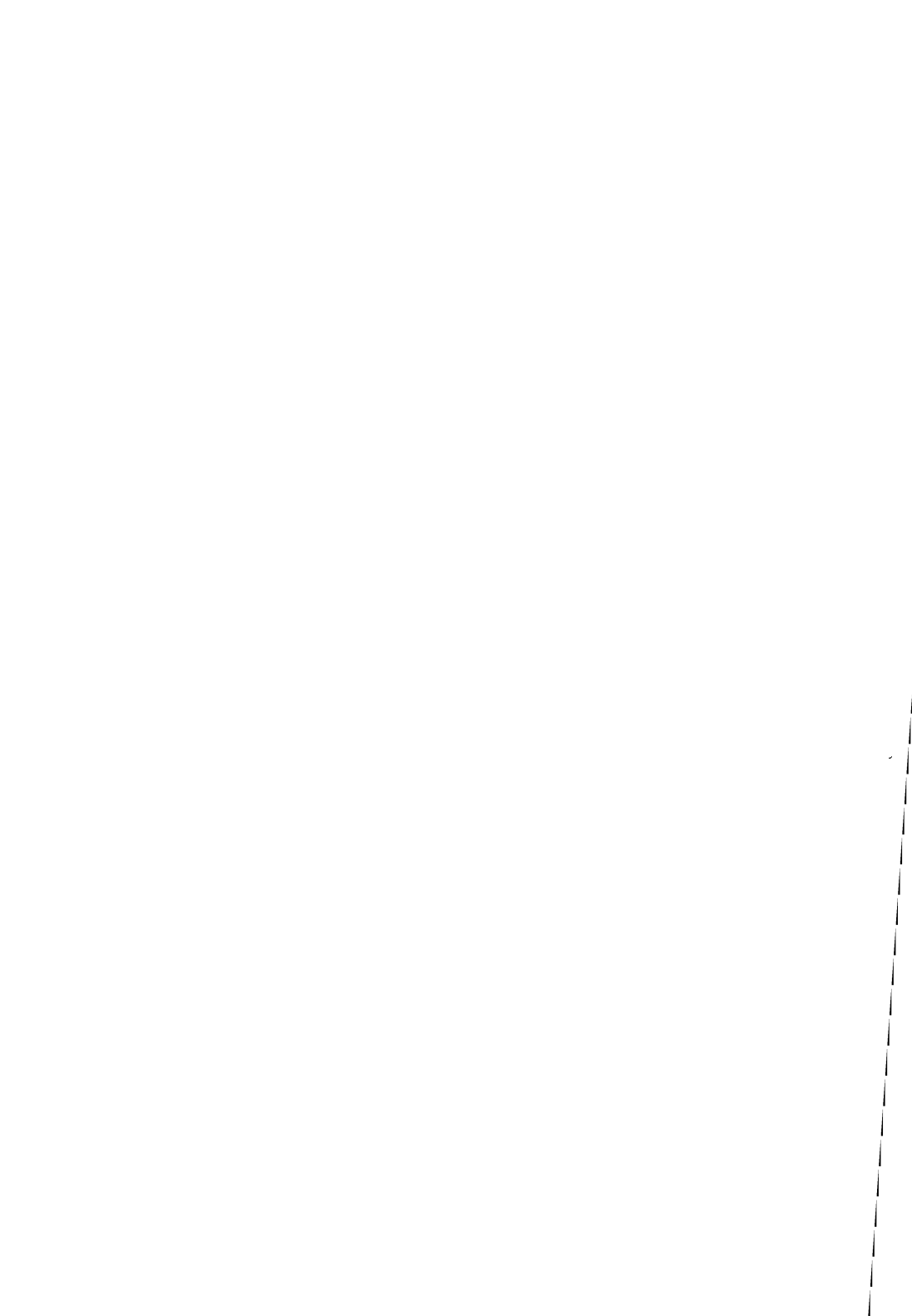


Figure 9 : Slew Rates versus Supply Voltage.



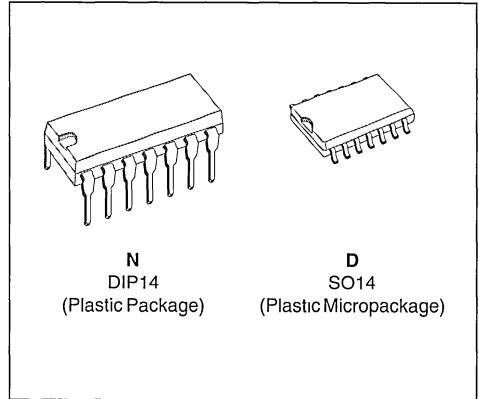
DATASHEETS

COMPARATORS



MICROPOWER QUAD CMOS VOLTAGE COMPARATORS

- EXTREMELY LOW SUPPLY CURRENT :
9 μ A TYP / COMPARATOR
- WIDE SINGLE SUPPLY RANGE (3V TO 16V)
OR DUAL SUPPLIES (± 1.5 V TO ± 8 V)
- EXTREMELY LOW INPUT BIAS CURRENT:
1pA TYP
- EXTREMELY LOW INPUT OFFSET CURRENT:
1pA TYP
- INPUT COMMON-MODE VOLTAGE RANGE
INCLUDES GND
- BUILT-IN ESD PROTECTION
- HIGH INPUT IMPEDANCE : 10¹² Ω TYP
- FAST RESPONSE TIME : 1.5 μ s TYP FOR
5mV OVERDRIVE
- PIN-TO-PIN AND FUNCTIONALLY COMPATI-
BLE WITH BIPOLAR LM339



DESCRIPTION

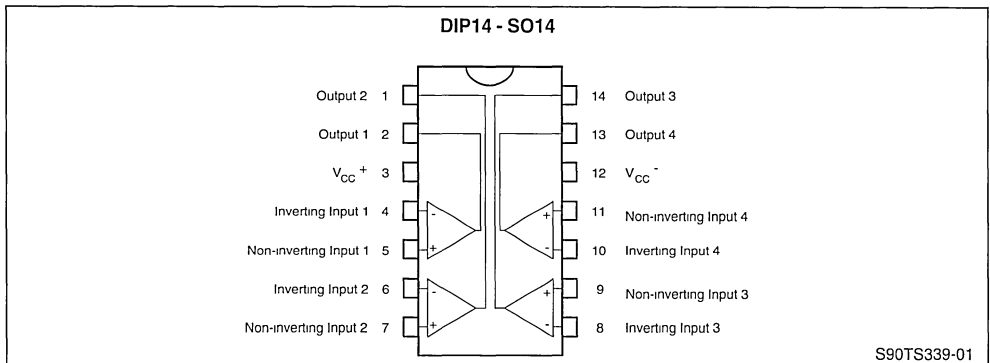
The TS339 is a micropower CMOS quad voltage comparator with extremely low consumption of 9 μ A typ / comparator (20 times less than bipolar LM339). Similar performances are offered by the quad micropower comparator TS3704 with a push-pull CMOS output. Thus response times remain similar to the LM339.

ORDER CODES

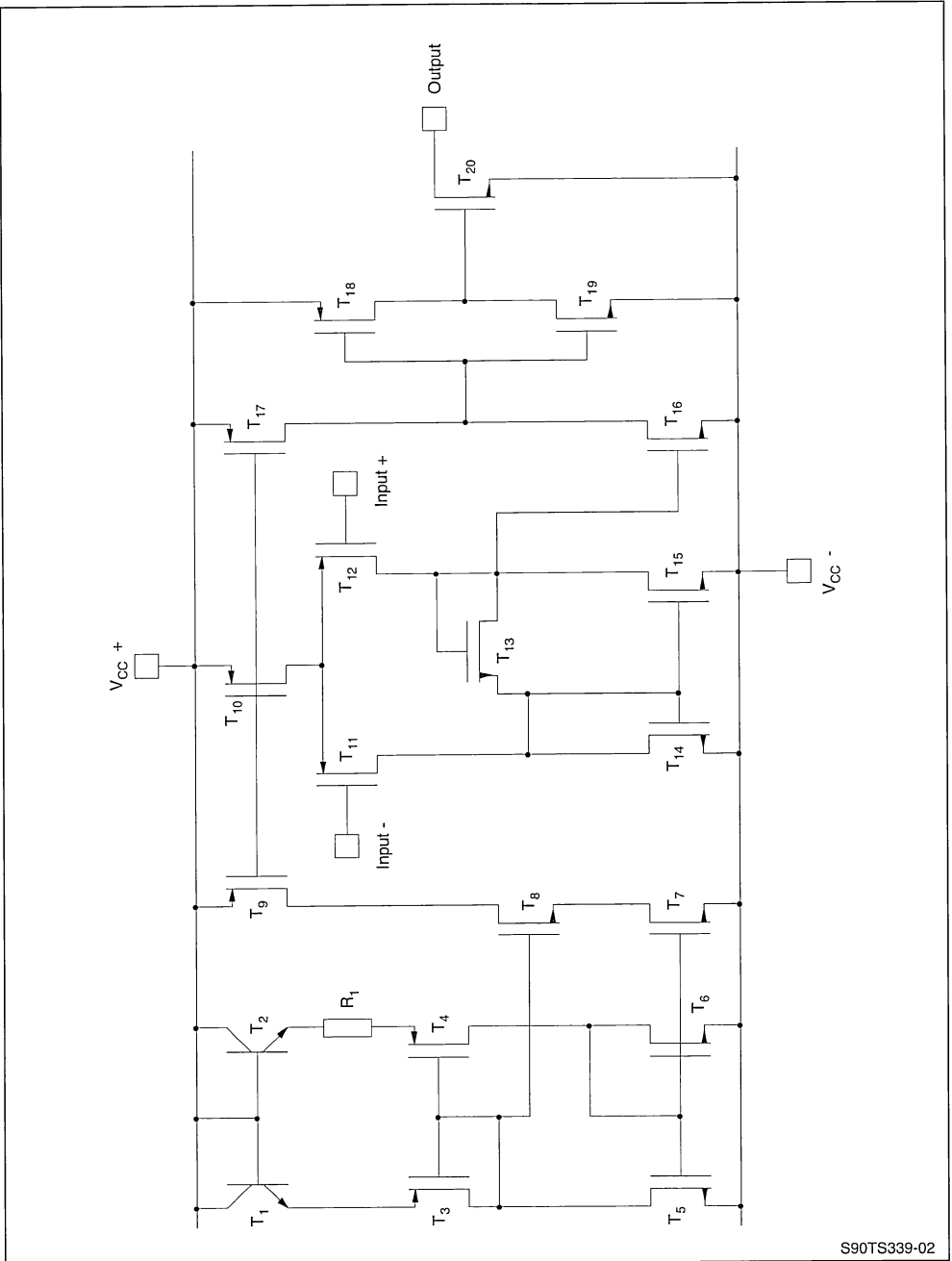
Part Number	Temperature Range	Package	
		N	D
TS339C	0°C to + 70°C	○	○
TS339I	- 40°C to + 105°C	○	○
TS339M	- 55°C to + 125°C	○	○

Example : TS339CN

PIN CONNECTIONS (Top view)



SCHEMATIC DIAGRAM (for 1/4 TS339)



S90TS339-02

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage (Note 1)	18	V
V_{id}	Differential Input Voltage (Note 2)	± 18	V
V_i	Input Voltage (Note 3)	18	V
V_o	Output Voltage	18	V
I_o	Output Current	20	mA
T_{oper}	Operating Free-Air Temperature Range	TS339C 0 to + 70 TS339I - 40 to + 105 TS339M - 55 to + 125	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	- 65 to + 150	$^{\circ}\text{C}$

- Notes : 1. All voltage values, except differential voltage, are with respect to network ground terminal
 2. Differential voltages are the non-inverting input terminal with respect to the inverting input terminal
 3. The magnitude of the input and the output voltages must never exceed the magnitude of the positive supply voltage
 4. Short circuit from outputs to V_{CC}^+ can cause excessive heating and eventual destruction.

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage Range	TS339C,I 3* to 16 TS339M 4 to 16	V
V_{ic}	Common Mode Input Voltage	0 to $V_{CC}^+ - 1.5$	V

* For selected devices only

ELECTRICAL CHARACTERISTICS

$V_{CC}^+ = 5V, V_{CC}^- = 0V, T_{AMB} = 25^{\circ}C$

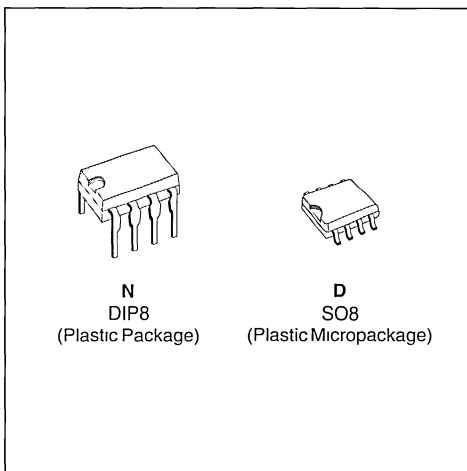
(unless otherwise specified)

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
V_{io}	Input Offset Voltage ($V_{IC} = V_{ICR\ Min}, V_{CC}^+ = 5V$ to 10V (note 1) $T_{Min} \leq T_{Amb} \leq T_{Max}$)		1.4	5 6.5	mV
I_{io}	Input Offset Current $V_{IC} = 2.5V$ $T_{Min} \leq T_{Amb} \leq T_{Max}$		1	300	pA
I_{ib}	Input Bias Current $V_{IC} = 2.5V$ $T_{Min} \leq T_{Amb} \leq T_{Max}$		1	600	pA
V_{ICR}	Input Common Mode Voltage Range $T_{Min} \leq T_{Amb} \leq T_{Max}$	0 to $V_{CC} - 1.2$ 0 to $V_{CC} - 1.5$			V
CMR	Common-mode Rejection Ratio ($V_{IC} = V_{ICR\ MIN}$)		75		dB
SVR	Supply Voltage Rejection Ratio ($V_{CC}^+ = +5V$ to +10V)		85		dB
I_{OH}	High Level Output Current ($V_{id} = 1V, V_{OH} = +5V$) $T_{Min} \leq T_{Amb} \leq T_{Max}$		2	40 1000	nA
V_{OL}	Low Level Output Voltage ($V_{id} = 1V, I_{OL} = 6mA$) $T_{Min} \leq T_{Amb} \leq T_{Max}$		350	400 650	mV
I_{CC}	Supply Current (4 comparators) No load - Outputs low $T_{Min} \leq T_{Amb} \leq T_{Max}$		36	80 100	μA
t_{PLH}	Response Time Low to High $V_{ic} = 0V, f = 10kHz, R_L = 5.1K\Omega, C_L = 15pF$, Overdrive = 5mV Overdrive = 10mV Overdrive = 20mV Overdrive = 40mV TTL Input		1.5 1.2 1.1 0.9 0.8		μs
t_{PHL}	Response Time High to Low $V_{ic} = 0V, f = 10kHz, R_L = 5.1K\Omega, C_L = 15pF$, Overdrive = 5mV Overdrive = 10mV Overdrive = 20mV Overdrive = 40mV TTL Input		2.9 2.0 1.3 0.9 0.1		μs
t_{THL}	Transition Time High to Low $f = 10kHz, C_L = 15pF, R_L = 5.1K\Omega$, Overdrive 50mV		25		ns

Note : 1.The specified offset voltage is the maximum value required to drive the output up to 4.5V or down to 0.3V.

LOW POWER DUAL CMOS VOLTAGE COMPARATORS

- WIDE SINGLE SUPPLY RANGE OR DUAL SUPPLIES 3V TO 16V OR $\pm 1.5V$ TO $\pm 8V$
- VERY LOW SUPPLY CURRENT :0.1mA/COMP INDEPENDENT OF SUPPLY VOLTAGE
- EXTREMELY LOW INPUT BIAS CURRENT: 1pA TYP
- EXTREMELY LOW INPUT OFFSET CURRENT: 1pA TYP
- LOW INPUT OFFSET VOLTAGE
- INPUT COMMON-MODE VOLTAGE RANGE INCLUDES GND
- LOW OUTPUT SATURATION VOLTAGE 150mV TYP
- OUTPUT COMPATIBLE WITH TTL, MOS AND CMOS
- BUILT-IN ESD PROTECTION
- HIGH INPUT IMPEDANCE $10^{12}\Omega$ TYP
- FAST RESPONSE TIME : 200ns TYP FOR TTL LEVEL INPUT STEP



DESCRIPTION

These devices consist of two independent precision voltage comparators, designed to operate with single or dual supplies.

These differential comparators use the SGS-THOMSON silicon lin MOS process giving them an excellent consumption-speed ratio.

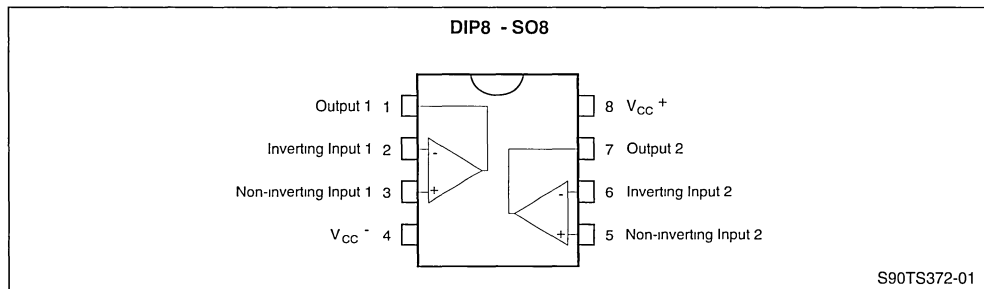
These devices are ideally suited for low consumption applications.

ORDER CODES

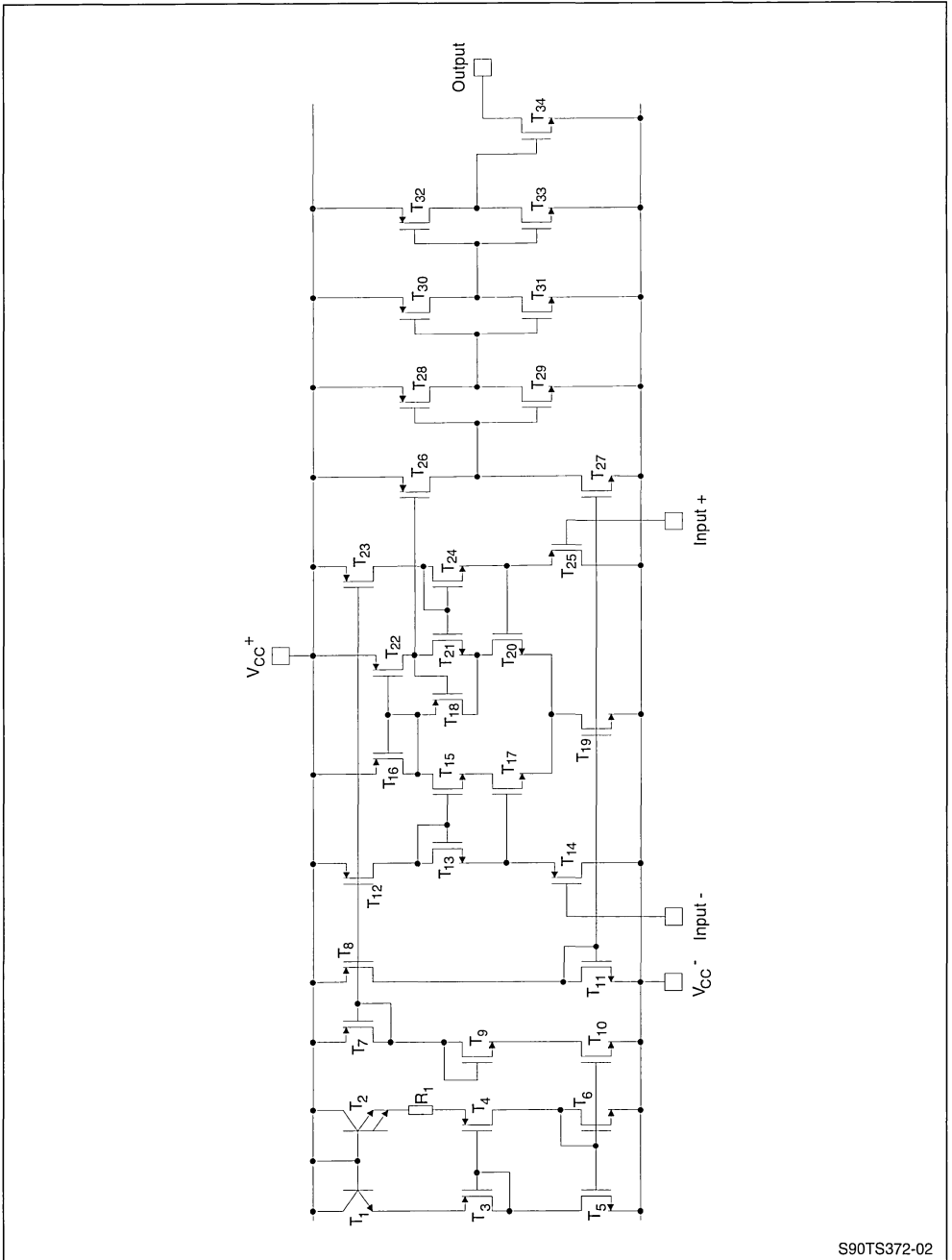
Part Number	Temperature Range	Package	
		N	D
TS372C	0°C to + 70°C	○	○
TS372I	- 40°C to + 105°C	○	○
TS372M	- 55°C to + 125°C	○	○

Example : TS372CN

PIN CONNECTIONS (Top view)



SCHEMATIC DIAGRAM (for 1/2 TS372)



S90TS372-02

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC} ⁺	Supply Voltage (Note 1)	18	V
V _{id}	Differential Input Voltage (Note 2)	± 18	V
V _i	Input Voltage (Note 3)	18	V
V _O	Output Voltage	18	V
I _O	Output Current	20	mA
	Duration of Output Short-Circuit to GND (Note 4)	Unlimited	
T _{oper}	Operating Free-Air Temperature Range	TS372C 0 to + 70 TS372I - 40 to + 105 TS372M - 55 to + 125	°C
T _{stg}	Storage Temperature Range	- 65 to + 150	°C

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC} ⁺	Supply Voltage Range	3 to 16	V

- Notes :
1. All voltage values, except differential voltage, are with respect to network ground terminal
 2. Differential voltages are the non-inverting input terminal with respect to the inverting input terminal
 3. The magnitude of the input and the output voltages must never exceed the magnitude of the positive supply voltage.
 4. Short circuit from outputs to V_{CC}⁺ can cause excessive heating and eventual destruction

ELECTRICAL CHARACTERISTICS AT SPECIFIED FREE-AIR TEMPERATURE, $V_{CC}^+ = 5V$

(unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit
V_{IO}	Input Offset Voltage ($V_{IC} = V_{ICR\ Min}$ - Note 1) $T_{AMB} = 25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		2	10 12	mV
I_{IO}	Input Offset Current (Note 1) $T_{AMB} = 25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		1	100 200	pA
I_{b}	Input Bias Current $T_{AMB} = 25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		1	150 300	pA
V_{ICR}	Common-mode Input Voltage Range $T_{AMB} = 25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$				V
I_{OH}	High Level Output Current ($V_{ID} = 1V$) $T_{AMB} = 25^{\circ}C$ $V_{OH} = 5V$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$ $V_{OH} = 1.5V$		0.1	1	nA μA
V_{OL}	Low Level Output Voltage ($V_{ID} = -1V$, $I_{OL} = 4mA$) $T_{AMB} = 25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		100	400 700	mV
I_{OL}	Low Level Output Current $T_{AMB} = 25^{\circ}C$, $V_{ID} = -1V$, $V_{OL} = 1.5V$	6	45		mA
I_{CC}	Supply Current (two comparators) $T_{AMB} = 25^{\circ}C$, $V_{ID} = -1V$, no load		0.3	0.75	mA

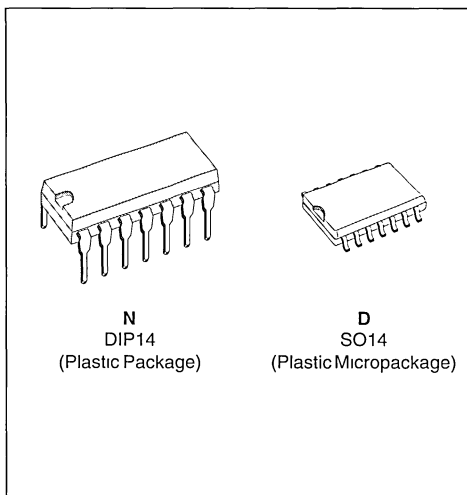
SWITCHING CHARACTERISTICS ($V_{CC}^+ = 5V$, $T_{AMB} = 25^{\circ}C$)

Symbol	Parameter	Min.	Typ.	Max.	Unit
t_{RE}	Response Time ($R_L = 5.1k\Omega$ connected to 5V, $C_L = 15pF$ - Note2) <ul style="list-style-type: none"> • 100mV input step with 5mV overdrive • TTL level input step 		600 200		ns

- Notes : 1 The offset voltage and offset current which are given, are the maximum values required to drive the output down to 400mV or up to 4V with $R_L = 10k\Omega$ to V_{CC}
 2. The response time which is specified is the interval between the input signal and the instant when the output signal crosses 1.4V

LOW POWER QUAD CMOS VOLTAGE COMPARATORS

- WIDE SINGLE SUPPLY RANGE OR DUAL SUPPLIES 3V TO 16V OR $\pm 1.5V$ TO $\pm 8V$
- VERY LOW SUPPLY CURRENT :0.1mA/COMP INDEPENDENT OF SUPPLY VOLTAGE
- EXTREMELY LOW INPUT BIAS CURRENT: 1pA TYP
- EXTREMELY LOW INPUT OFFSET CURRENT: 1pA TYP
- LOW INPUT OFFSET VOLTAGE
- INPUT COMMON-MODE VOLTAGE RANGE INCLUDES GND
- LOW OUTPUT SATURATION VOLTAGE 150mV TYP
- OUTPUT COMPATIBLE WITH TTL, MOS AND CMOS
- BUILT-IN ESD PROTECTION
- HIGH INPUT IMPEDANCE $10^{12}\Omega$ TYP
- FAST RESPONSE TIME : 200ns TYP FOR TTL LEVEL INPUT STEP



DESCRIPTION

These devices consist of four independent precision voltage comparators, designed to operate with single or dual supplies.

These differential comparators use the SGS-THOMSON silicon lin MOS process giving them an excellent consumption-speed ratio.

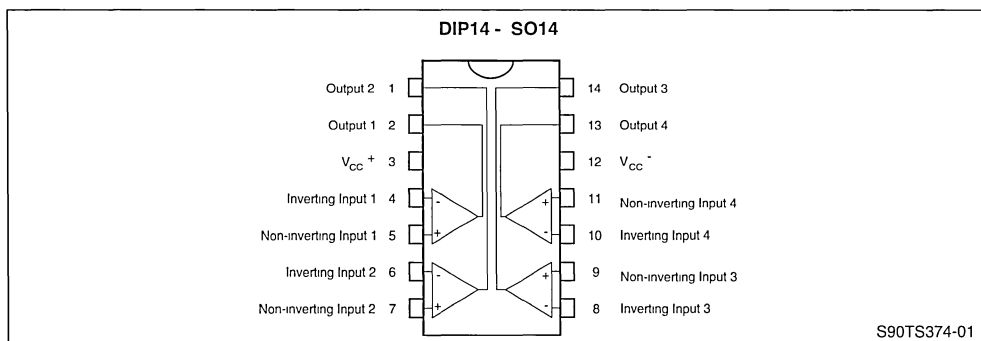
These devices are ideally suited for low consumption applications.

ORDER CODES

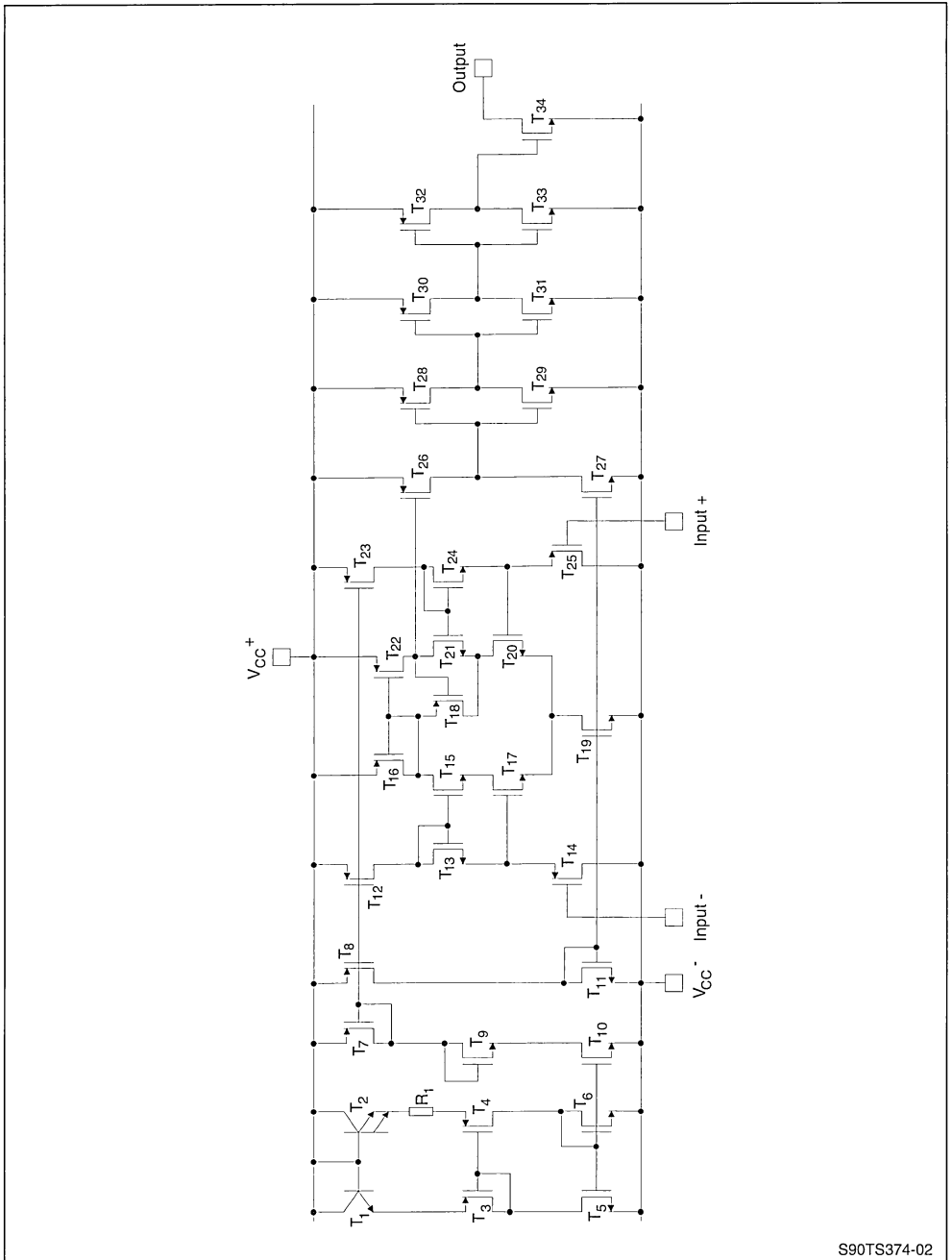
Part Number	Temperature Range	Package	
		N	D
TS374C	0°C to + 70°C	○	○
TS374I	- 40°C to + 105°C	○	○
TS374M	- 55°C to + 125°C	○	○

Example : TS374CN

PIN CONNECTIONS (Top view)



SCHEMATIC DIAGRAM (for 1/4 TS374)



S90TS374-02

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC} ⁺	Supply Voltage (Note 1)	18	V
V _{id}	Differential Input Voltage (Note 2)	± 18	V
V _i	Input Voltage (Note 3)	18	V
V _O	Output Voltage	18	V
I _O	Output Current	20	mA
	Duration of Output Short-Circuit to GND (Note 4)	Unlimited	
T _{oper}	Operating Free-Air Temperature Range	TS374C TS374I TS374M 0 to + 70 - 40 to + 105 - 55 to + 125	°C
T _{stg}	Storage Temperature Range	- 65 to + 150	°C

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC} ⁺	Supply Voltage Range	3 to 16	V

- Notes :
1. All voltage values, except differential voltage, are with respect to network ground terminal
 2. Differential voltages are the non-inverting input terminal with respect to the inverting input terminal
 3. The magnitude of the input and the output voltages must never exceed the magnitude of the positive supply voltage
 4. Short circuit from outputs to V_{CC}⁺ can cause excessive heating and eventual destruction

ELECTRICAL CHARACTERISTICS AT SPECIFIED FREE-AIR TEMPERATURE, $V_{CC}^+ = 5V$

(unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit
V_{IO}	Input Offset Voltage ($V_{IC} = V_{ICR\ Min}$ - Note 1) $T_{AMB} = 25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		2	10 12	mV
I_{IO}	Input Offset Current (Note 1) $T_{AMB} = 25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		1	100 200	pA
I_{IB}	Input Bias Current $T_{AMB} = 25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		1	150 300	pA
V_{ICR}	Common-mode Input Voltage Range $T_{AMB} = 25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	0 to $V_{CC} - 2$ 0 to $V_{CC} - 2.25$ 0 to $V_{CC} - 2.5$			V
I_{OH}	High Level Output Current ($V_{ID} = 1V$) $T_{AMB} = 25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		0.1	1	nA μA
V_{OL}	Low Level Output Voltage ($V_{ID} = -1V, I_{OL} = 4mA$) $T_{AMB} = 25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$		100	400 700	mV
I_{OL}	Low Level Output Current $T_{AMB} = 25^{\circ}C, V_{ID} = -1V, V_{OL} = 1.5V$	6	45		mA
I_{CC}	Supply Current (four comparators) $T_{AMB} = 25^{\circ}C, V_{ID} = -1V, \text{no load}$		0.6	1	mA

SWITCHING CHARACTERISTICS ($V_{CC}^+ = 5V, T_{AMB} = 25^{\circ}C$)

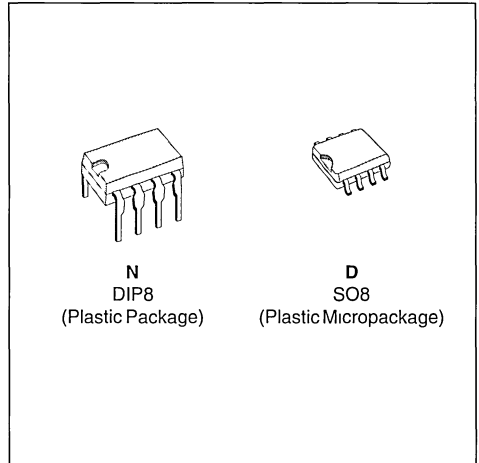
Symbol	Parameter	Min.	Typ.	Max.	Unit
t_{RE}	Response Time ($R_L = 5.1k\Omega$ connected to 5V, $C_L = 15pF$ - Note2) <ul style="list-style-type: none"> ● 100mV input step with 5mV overdrive ● TTL level input step 		600 200		ns

- Notes : 1 The offset voltage and offset current which are given, are the maximum values required to drive the output down to 400mV or up to 4V with $R_L = 10k\Omega$ to V_{CC}
 2 The response time which is specified is the interval between the input signal and the instant when the output signal crosses 1.4V.



MICROPOWER DUAL CMOS VOLTAGE COMPARATORS

- EXTREMELY LOW SUPPLY CURRENT :
9µA TYP / COMPARATOR
- WIDE SINGLE SUPPLY RANGE (3V TO 16V)
OR DUAL SUPPLIES ($\pm 1.5V$ TO $\pm 8V$)
- EXTREMELY LOW INPUT BIAS CURRENT:
1pA TYP
- EXTREMELY LOW INPUT OFFSET CURRENT:
1pA TYP
- INPUT COMMON-MODE VOLTAGE RANGE
INCLUDES GND
- BUILT-IN ESD PROTECTION
- HIGH INPUT IMPEDANCE : $10^{12}\Omega$ TYP
- FAST RESPONSE TIME : 2.5µs TYP FOR
5mV OVERDRIVE
- PIN-TO-PIN AND FUNCTIONALLY COMPATI-
BLE WITH BIPOLAR LM393



DESCRIPTION

The TS393 is a micropower CMOS dual voltage comparator with extremely low consumption of 9 µA typ / comparator (20 times less than bipolar LM393). Similar performances are offered by the dual micropower comparators TS3702 with a push-pull CMOS output.

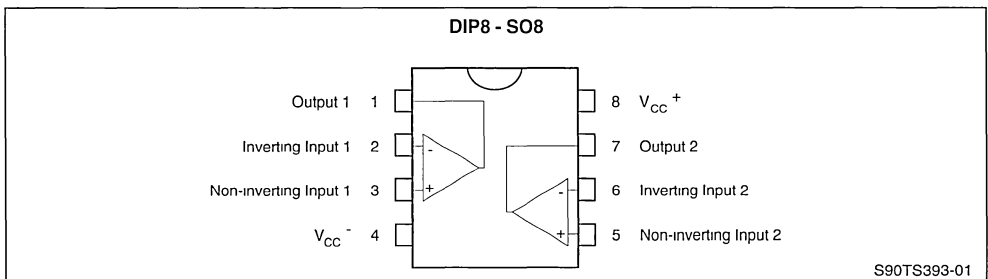
Thus response times remain similar to the LM393.

ORDER CODES

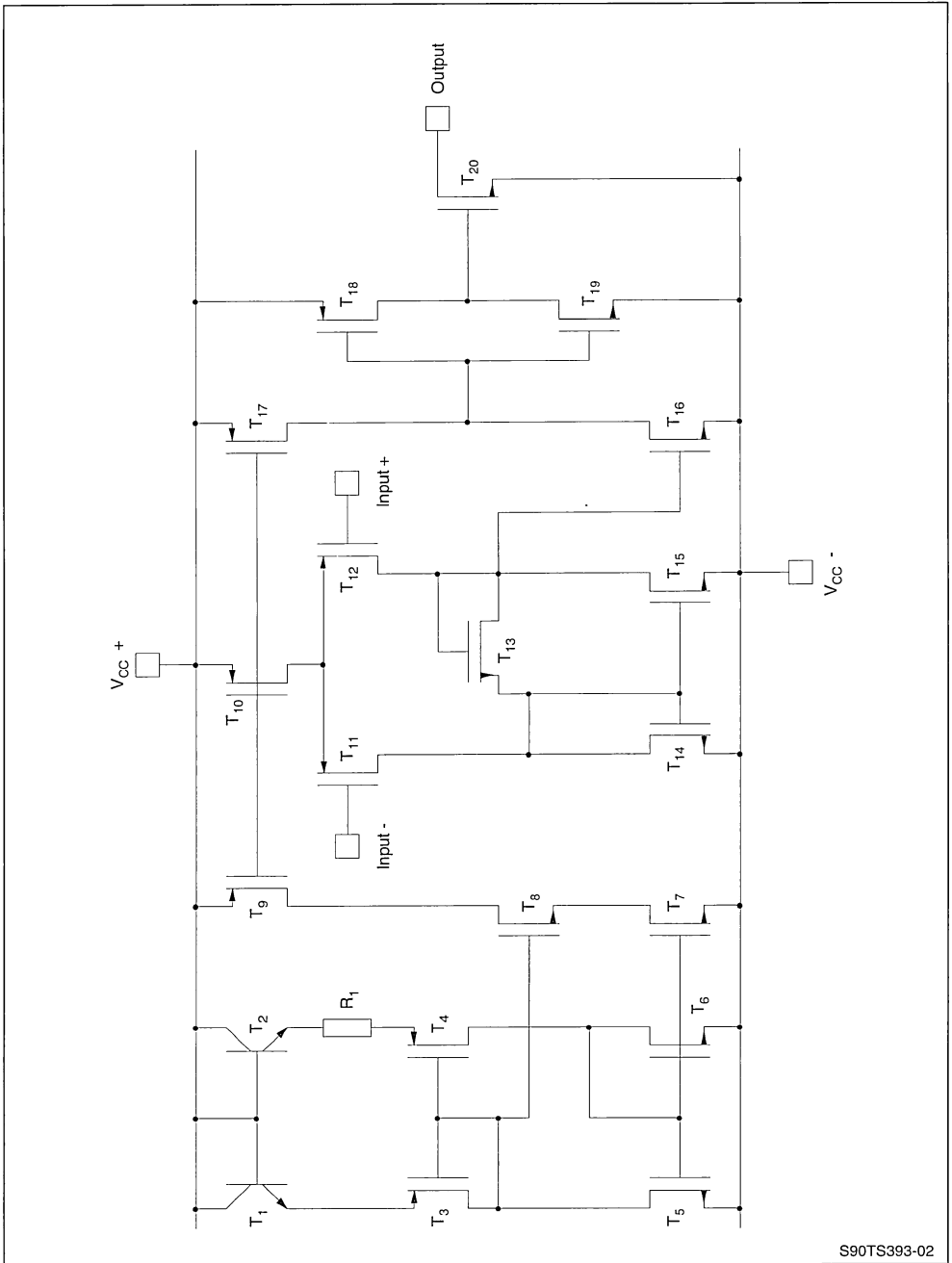
Part Number	Temperature Range	Package	
		N	D
TS393C	0°C to + 70°C	•	•
TS393I	- 40°C to + 105°C	•	•
TS393M	- 55°C to + 125°C	•	•

Example : TS393CN

PIN CONNECTIONS (Top view)



SCHEMATIC DIAGRAM (for 1/2 TS393)



S90TS393-02

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage (Note 1)	18	V
V_{id}	Differential Input Voltage (Note 2)	± 18	V
V_i	Input Voltage (Note 3)	18	V
V_O	Output Voltage	18	V
I_o	Output Current	20	mA
T_{oper}	Operating Free-Air Temperature Range	TS393C 0 to + 70 TS393I - 40 to + 105 TS393M - 55 to + 125	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	- 65 to + 150	$^{\circ}\text{C}$

- Notes : 1 All voltage values, except differential voltage, are with respect to network ground terminal
 2 Differential voltages are the non-inverting input terminal with respect to the inverting input terminal
 3 The magnitude of the input and the output voltages must never exceed the magnitude of the positive supply voltage
 4 Short circuit from outputs to V_{CC}^+ can cause excessive heating and eventual destruction

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage Range	TS393C,I 3* to 16 TS393M 4 to 16	V
V_{ic}	Common Mode Input Voltage	0 to $V_{CC}^+ - 1.5$	V

* For selected devices only

ELECTRICAL CHARACTERISTICS

$V_{CC}^+ = 5V$, $V_{CC}^- = 0V$, $T_{AMB} = 25^{\circ}C$

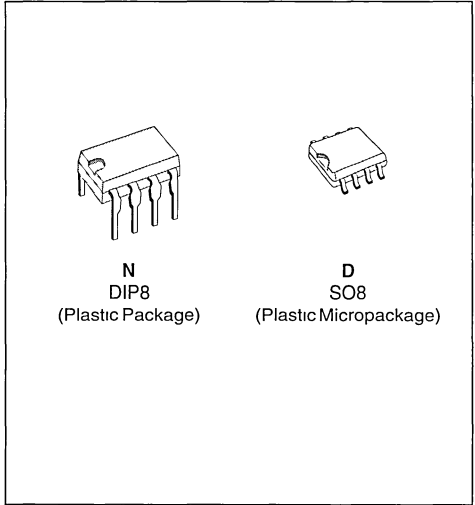
(unless otherwise specified)

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
V_{io}	Input Offset Voltage $V_{IC} = V_{ICR Min}$, $V_{CC}^+ = 5V$ to $10V$ (note 1) $T_{Min} \leq T_{Amb} \leq T_{Max}$		1.4	5 6.5	mV
I_{io}	Input Offset Current $V_{IC} = 2.5V$ $T_{Min} \leq T_{Amb} \leq T_{Max}$		1	300	pA
I_{ib}	Input Bias Current $V_{IC} = 2.5V$ $T_{Min} \leq T_{Amb} \leq T_{Max}$		1	600	pA
V_{ICR}	Input Common Mode Voltage Range $T_{Min} \leq T_{Amb} \leq T_{Max}$	0 to $V_{CC} - 1.2$ V 0 to $V_{CC} - 1.5$ V			V
CMR	Common-mode Rejection Ratio ($V_{IC} = V_{ICRMIN}$)		71		dB
SVR	Supply Voltage Rejection Ratio ($V_{CC}^+ = +5V$ to $+10V$)		80		dB
I_{OH}	High Level Output Current $V_{id} = 1V$, $V_{OH} = +5V$ $T_{Min} \leq T_{Amb} \leq T_{Max}$		2	40 1000	nA
V_{OL}	Low Level Output Voltage $V_{id} = -1V$, $I_{OL} = 6mA$ $T_{Min} \leq T_{Amb} \leq T_{Ma}$		350	400 650	mV
I_{CC}	Supply Current (2 comparators) No load - Outputs low $T_{Min} \leq T_{Amb} \leq T_{Ma}$		18	40 50	μA
t_{PLH}	Response Time Low to High $V_{ic} = 0V$, $f = 10kHz$, $R_L = 5.1K\Omega$, $C_L = 15 pF$, Overdrive 5mV Overdrive 10mV Overdrive 20mV Overdrive 40mV TTL Input		1.5 1.2 1.0 0.8 0.7		μs
t_{PHL}	Response Time High to Low $V_{ic} = 0V$, $f = 10kHz$, $R_L = 5.1K\Omega$, $C_L = 15 pF$, Overdrive 5mV Overdrive 10mV Overdrive 20mV Overdrive 40mV TTL Input		2.7 2.0 1.3 0.9 0.16		μs

Note : 1 The specified offset voltage is the maximum value required to drive the output up to 4.5V or down to 0.3V

MICROPOWER DUAL CMOS VOLTAGE COMPARATORS

- PUSH-PULL CMOS OUTPUT (NO EXTERNAL PULL-UP RESISTOR REQUIRED)
- EXTREMELY LOW SUPPLY CURRENT : 9µA TYP / COMPARATOR
- WIDE SINGLE SUPPLY RANGE (3V TO 16V) OR DUAL SUPPLIES (± 1.5V TO ± 8V)
- EXTREMELY LOW INPUT BIAS CURRENT: 1pA TYP
- EXTREMELY LOW INPUT OFFSET CURRENT: 1pA TYP
- INPUT COMMON-MODE VOLTAGE RANGE INCLUDES GND
- BUILT-IN ESD PROTECTION
- HIGH INPUT IMPEDANCE : $10^{12}\Omega$ TYP
- FAST RESPONSE TIME : 2.5µs TYP FOR 5mV OVERDRIVE
- PIN-TO-PIN AND FUNCTIONALLY COMPATIBLE WITH BIPOLAR LM393



DESCRIPTION

The TS3702 is a micropower CMOS dual voltage comparator with extremely low consumption of 9 µA typ / comparator (20 times less than bipolar LM393). The push-pull CMOS output stage allows power and space saving by eliminating the external pull-up resistor required by usual open-collector output comparators.

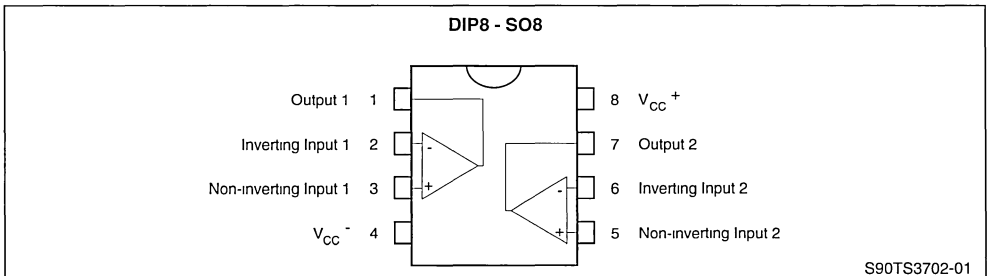
Thus response times remain similar to the LM393.

ORDER CODES

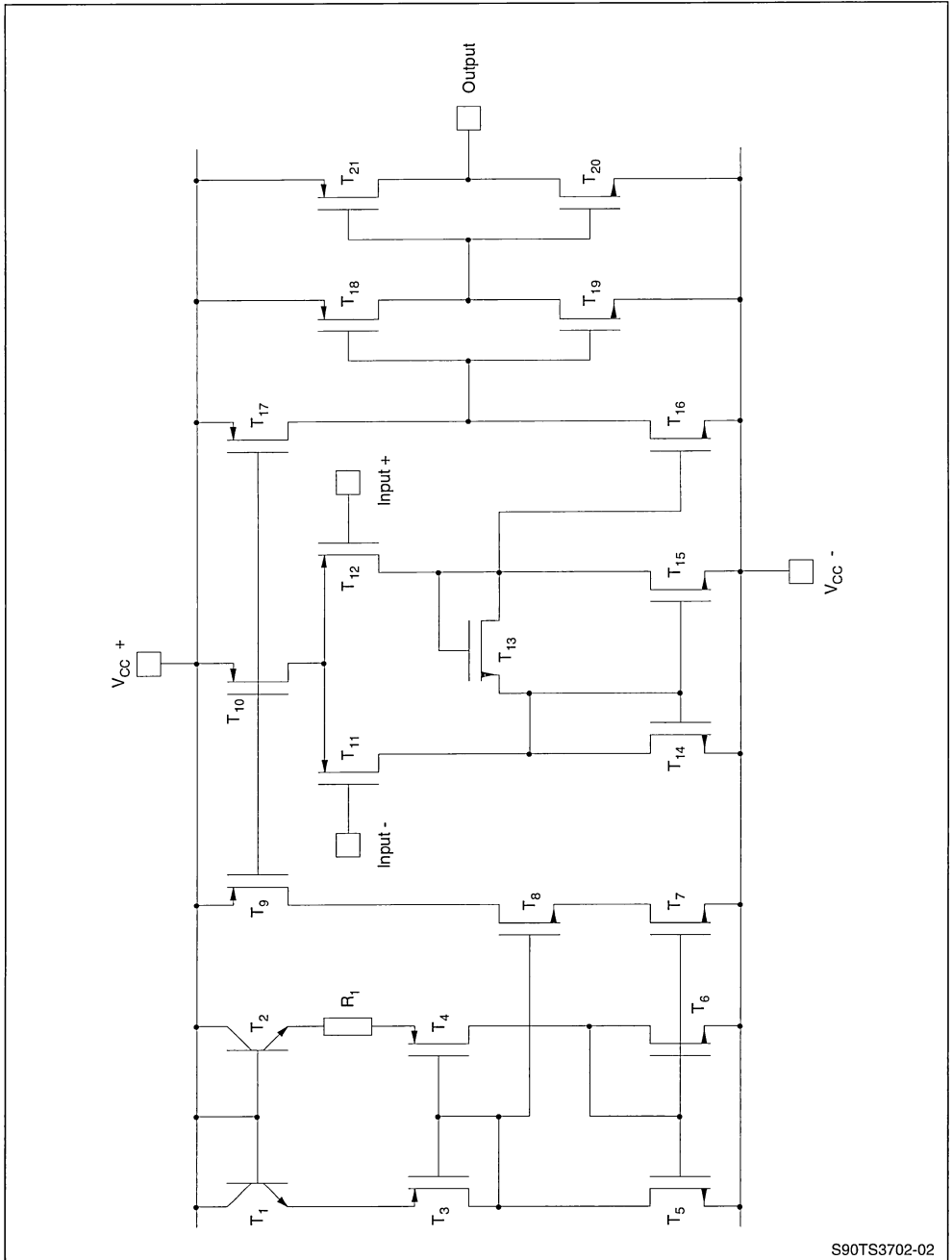
Part Number	Temperature Range	Package	
		N	D
TS3702C	0°C to + 70°C	●	●
TS3702I	- 40°C to + 105°C	●	●
TS3702M	- 55°C to + 125°C	●	●

Example : TS3702CN

PIN CONNECTIONS (Top view)



SCHEMATIC DIAGRAM (for 1/2 TS3702)



S90TS3702-02

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage (Note 1)	16	V
V_{id}	Differential Input Voltage (Note 2)	± 16	V
V_I	Input Voltage (Note 3)	16	V
V_O	Output Voltage	16	V
I_O	Output Current	20	mA
T_{oper}	Operating Free-Air Temperature Range	TS3702C 0 to + 70 TS3702I - 40 to + 105 TS3702M - 55 to + 125	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	- 65 to + 150	$^{\circ}\text{C}$

- Notes :
1. All voltage values, except differential voltage, are with respect to network ground terminal
 2. Differential voltages are the non-inverting input terminal with respect to the inverting input terminal
 3. The magnitude of the input and the output voltages must never exceed the magnitude of the positive supply voltage.
 4. Short circuit from outputs to V_{CC}^+ can cause excessive heating and eventual destruction

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage Range	TS3702C,I 3* to 14 TS3702M 4 to 14	V
V_{IC}	Common Mode Input Voltage	0 to $V_{CC}^+ - 1.5$	V

* For selected devices only

ELECTRICAL CHARACTERISTICS

$V_{CC}^+ = 5V$, $V_{CC}^- = 0V$, $T_{AMB} = 25^{\circ}C$
 (unless otherwise specified)

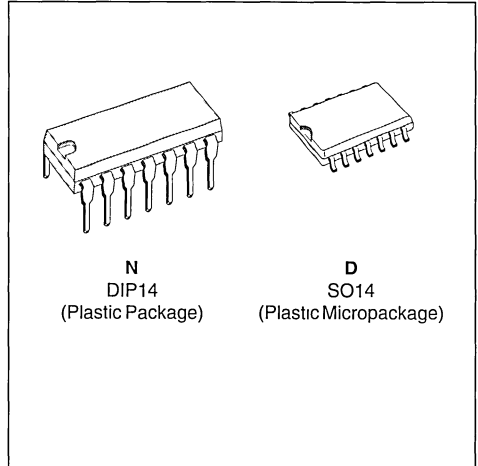
Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
V_{io}	Input Offset Voltage $V_{IC} = V_{ICR\ Min}$, $V_{CC}^+ = 5V$ to $10V$ (note 1) $T_{Min} \leq T_{Amb} \leq T_{Max}$		1.2	5 6.5	mV
I_{io}	Input Offset Current $V_{IC} = 2.5V$ $T_{Min} \leq T_{Amb} \leq T_{Max}$		1	300	pA
I_{ib}	Input Bias Current $V_{IC} = 2.5V$ $T_{Min} \leq T_{Amb} \leq T_{Max}$		1	600	pA
V_{ICR}	Input Common Mode Voltage Range $T_{Min} \leq T_{Amb} \leq T_{Max}$	0 to $V_{CC} - 1.2$ V 0 to $V_{CC} - 1.5$ V			V
CMR	Common-mode Rejection Ratio ($V_{IC} = V_{ICR\ MIN}$)		82		dB
SVR	Supply Voltage Rejection Ratio ($V_{CC}^+ = +5V$ to $+10V$)		90		dB
V_{OH}	High Level Output Voltage $V_{id} = 1V$, $I_{OH} = -4mA$ $T_{Min} \leq T_{Amb} \leq T_{Max}$	4.5 4.3	4.7		V
V_{OL}	Low Level Output Voltage $V_{id} = -1V$, $I_{OL} = 4mA$ $T_{Min} \leq T_{Amb} \leq T_{Max}$		220	300 375	mV
I_{CC}	Supply Current (2 comparators) No load - Outputs low $T_{Min} \leq T_{Amb} \leq T_{Max}$		18	40 50	μA
t_{PLH}	Response Time Low to High $V_{ic} = 0V$, $f = 10kHz$, $C_L = 50pF$, Overdrive = 5mV Overdrive = 10mV Overdrive = 20mV Overdrive = 40mV TTL Input		1.9 1.5 1.2 1.0 0.8		μs
t_{PHL}	Response Time High to Low $V_{ic} = 0V$, $f = 10kHz$, $C_L = 50pF$, Overdrive = 5mV Overdrive = 10mV Overdrive = 20mV Overdrive = 40mV TTL Input		3.0 2.2 1.5 1.0 0.17		μs
t_f	Full time $f = 10kHz$, $C_L = 50pF$, Overdrive 50mV		30		ns

Note : 1.The specified offset voltage is the maximum value required to drive the output up to 4.5V or down to 0.3V.



MICROPOWER QUAD CMOS VOLTAGE COMPARATORS

- PUSH-PULL CMOS OUTPUT (NO EXTERNAL PULL-UP RESISTOR REQUIRED)
- EXTREMELY LOW SUPPLY CURRENT : 9µA TYP / COMPARATOR
- WIDE SINGLE SUPPLY RANGE (3V TO 16V) OR DUAL SUPPLIES ($\pm 1.5V$ TO $\pm 8V$)
- EXTREMELY LOW INPUT BIAS CURRENT: 1pA TYP
- EXTREMELY LOW INPUT OFFSET CURRENT: 1pA TYP
- INPUT COMMON-MODE VOLTAGE RANGE INCLUDES GND
- BUILT-IN ESD PROTECTION
- HIGH INPUT IMPEDANCE : $10^{12}\Omega$ TYP
- FAST RESPONSE TIME : 2.5µs TYP FOR 5mV OVERDRIVE
- PIN-TO-PIN AND FUNCTIONALLY COMPATIBLE WITH BIPOLAR LM339



DESCRIPTION

The TS3704 is a micropower CMOS quad voltage comparator with extremely low consumption of 9µA typ / comparator (20 times less than bipolar LM339). The push-pull CMOS output stage allows power and space saving by eliminating the external pull-up resistor required by usual open-collector output comparators.

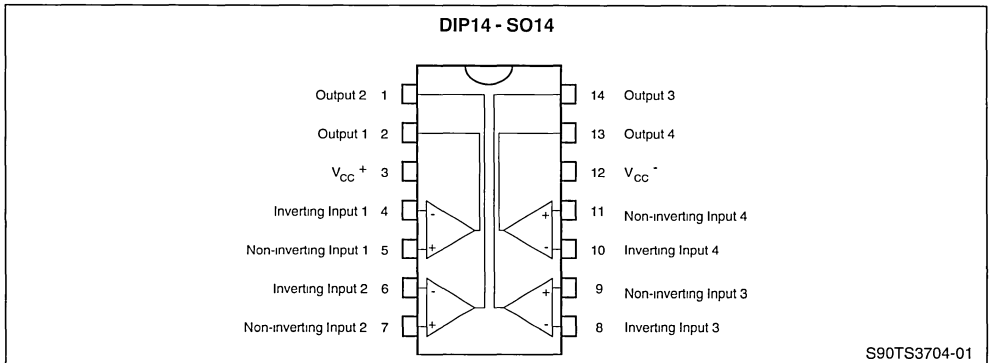
Thus response times remain similar to the LM339.

ORDER CODES

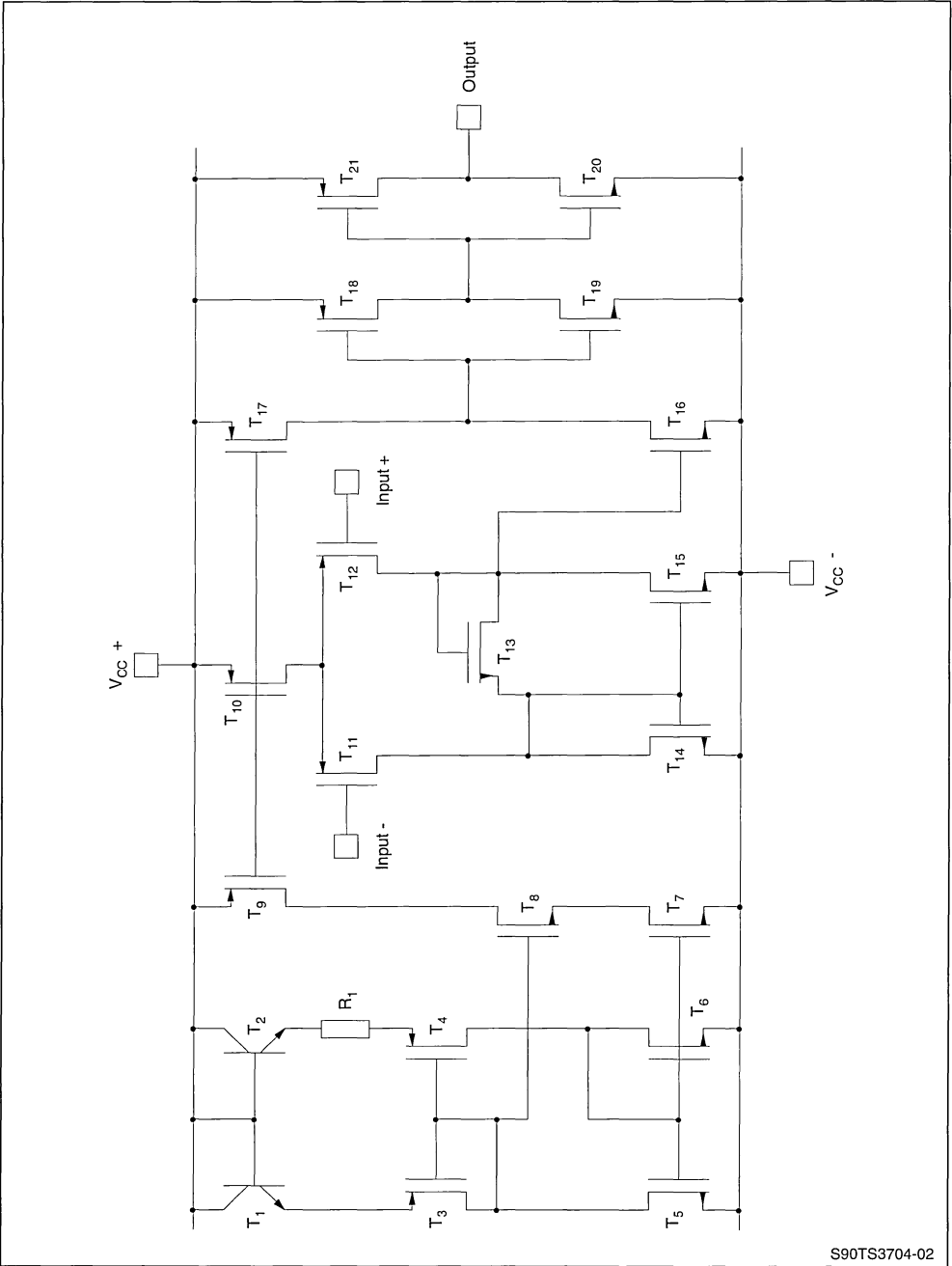
Part Number	Temperature Range	Package	
		N	D
TS3704C	0°C to + 70°C	•	•
TS3704I	- 40°C to + 105°C	•	•
TS3704M	- 55°C to + 125°C	•	•

Example : TS3704CN

PIN CONNECTIONS (Top view)



SCHEMATIC DIAGRAM (for 1/4 TS3704)



S90TS3704-02

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage (Note 1)	16	V
V_{id}	Differential Input Voltage (Note 2)	± 16	V
V_i	Input Voltage (Note 3)	16	V
V_O	Output Voltage	16	V
I_O	Output Current	20	mA
T_{oper}	Operating Free-Air Temperature Range	TS3704C 0 to + 70 TS3704I - 40 to + 105 TS3704M - 55 to + 125	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	- 65 to + 150	$^{\circ}\text{C}$

- Notes : 1. All voltage values, except differential voltage, are with respect to network ground terminal
 2. Differential voltages are the non-inverting input terminal with respect to the inverting input terminal
 3. The magnitude of the input and the output voltages must never exceed the magnitude of the positive supply voltage.
 4. Short circuit from outputs to V_{CC}^+ can cause excessive heating and eventual destruction

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}^+	Supply Voltage Range	TS3704C,I 3* to 14 TS3704M 4 to 14	V
V_{ic}	Common Mode Input Voltage	0 to $V_{CC}^+ - 1.5$	V

* For selected devices only

ELECTRICAL CHARACTERISTICS

$V_{CC}^+ = 5V$, $V_{CC}^- = 0V$, $T_{AMB} = 25^\circ C$
 (unless otherwise specified)

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
V_{io}	Input Offset Voltage $V_{IC} = V_{ICR\ Min}$, $V_{CC}^+ = 5V$ to $10V$ (note 1) $T_{Min} \leq T_{Amb} \leq T_{Max}$		1.2	5 6.5	mV
I_{io}	Input Offset Current $V_{ic} = 2.5V$ $T_{Min} \leq T_{Amb} \leq T_{Max}$		1	300	pA
I_{ib}	Input Bias Current $V_{ic} = 2.5V$ $T_{Min} \leq T_{Amb} \leq T_{Max}$		1	600	pA
V_{ICR}	Input Common Mode Voltage Range $T_{Min} \leq T_{Amb} \leq T_{Max}$	0 to $V_{CC} - 1.2$ V 0 to $V_{CC} - 1.5$ V			V
CMR	Common-mode Rejection Ratio ($V_{IC} = V_{ICRMIN}$)		78		dB
SVR	Supply Voltage Rejection Ratio ($V_{CC}^+ = +5V$ to $+10V$)		92		dB
V_{OH}	High Level Output Current $V_{id} = 1V$, $I_{OH} = -4mA$ $T_{Min} \leq T_{Amb} \leq T_{Max}$	4.5 4.3	4.7		V
V_{OL}	Low Level Output Current $V_{id} = -1V$, $I_{OL} = 4mA$ $T_{Min} \leq T_{Amb} \leq T_{Max}$		234	300 375	mV
I_{CC}	Supply Current (4 comparators) No load - Outputs low $T_{Min} \leq T_{Amb} \leq T_{Max}$		36	80 100	μA
t_{PLH}	Response time low to high $V_{ic} = 0V$, $f = 10kHz$, $C_L = 50pF$, Overdrive = 5mV Overdrive = 10 mV Overdrive = 20mV Overdrive = 40mV TTL Input		1.3 1.1 0.95 0.9 0.8		μs
t_{PHL}	Response time high to low $V_{ic} = 0V$, $f = 10kHz$, $C_L = 50pF$, Overdrive = 5mV Overdrive = 10mV Overdrive = 20mV Overdrive = 40mV TTL Input		2.3 1.7 1.2 0.9 0.17		μs
t_f	Fall time $f = 10kHz$, $C_L = 50pF$, Overdrive 50mV		30		ns

Note: 1. The specified offset voltage is the maximum value required to drive the output up to 4.5V or down to 0.3V.

DATASHEETS

TIMERS

LOW POWER SINGLE CMOS TIMERS

- VERY LOW POWER CONSUMPTION :
100 μ A typ at $V_{CC} = 5V$
- HIGH MAXIMUM ASTABLE FREQUENCY
2.7MHz
- PIN-TO-PIN AND FUNCTIONALLY COMPATIBLE WITH BIPOLAR NE555
- VOLTAGE RANGE : +2V to +18V
- HIGH OUTPUT CURRENT CAPABILITY
- SUPPLY CURRENT SPIKES REDUCED DURING OUTPUT TRANSITIONS
- HIGH INPUT IMPEDANCE : $10^{12} \Omega$
- OUTPUT COMPATIBLE WITH TTL, CMOS AND LOGIC MOS

DESCRIPTION

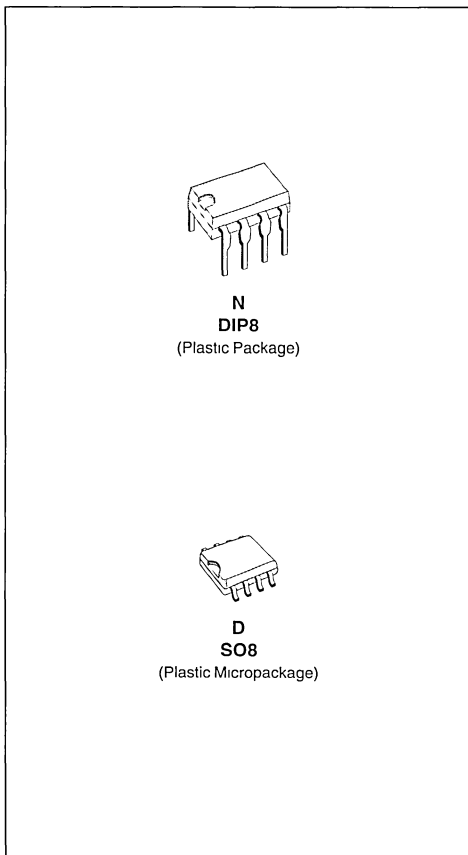
The TS555 is a single CMOS timer which offers very low consumption ($I_{CC(TYP)} TS555 = 100\mu A$, $I_{CC(TYP)} NE555 = 3mA$) and high frequency ($f_{(MAX)} TS555 = 2.7 MHz$ - $f_{(MAX)} NE555 = 0.1 MHz$). Thus, either in Monostable or Astable mode, timing remains very accurate.

The TS555 provides reduced supply current spikes during output transitions, which enables the use of lower decoupling capacitors compared to those required by bipolar NE555.

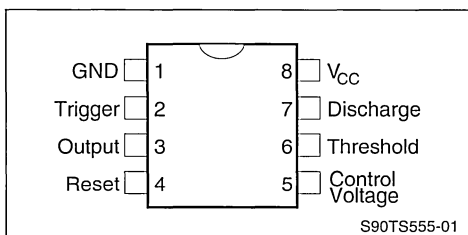
Timing capacitors can also be minimized due to high input impedance ($10^{12} \Omega$).

ORDER CODES

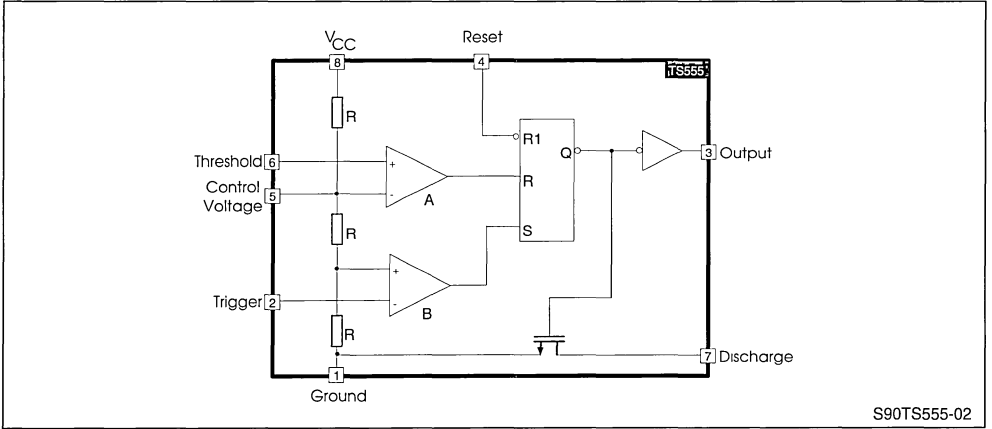
Part Number	Temperature Range	Package	
		N	D
TS555C	0 to +70°C	○	○
TS555I	-40 to +105°C	○	○
TS555M	-55 to +125°C	○	○
Examples : TS555CD , TS555IN			



PIN CONNECTION (top view)



BLOCK DIAGRAM



S90TS555-02

FUNCTION TABLE

RESET	TRIGGER	THRESHOLD	OUTPUT
Low	x	x	Low
High	Low	x	High
High	High	High	Low
High	High	Low	Previous State

- LOW** ↔ Level Voltage ≤ Min voltage specified
- HIGH** ↔ Level Voltage ≥ Max voltage specified
- X** ↔ Irrelevant

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	+18	V
T _J	Junction Temperature	+150	°C

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
T _{OPER}	Operating Temperature Range TS555C TS555I TS555M	0 to +70 -40 to +105 -55 to +125	°C
T _{STG}	Storage Temperature Range	-65 to +150	°C

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	+2 to +16	V

STATIC ELECTRICAL CHARACTERISTICS

V_{CC} = +2V , T_{AMB} = +25°C , Reset to V_{CC}

(Unless otherwise specified)

Symbol	Parameter	TS555C-TS555I-TS555M			UNIT
		Min	Typ	Max	
I _{CC}	Supply Current (no load, High and Low States) T _{AMB} = + 25°C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	- -	65 -	200 200	μA
V _{CL}	Control Voltage T _{AMB} = + 25°C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	1.2 1.1	1.3 -	1.4 1.5	V
V _{DIS}	Discharge Saturation Voltage (I _{DIS} = 1mA) T _{AMB} = + 25°C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	- -	0.05 -	0.2 0.25	V
V _{OL}	Low Level Output Voltage (I _{SINK} = 1mA) T _{AMB} = + 25°C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	- -	0.1 -	0.3 0.35	V
V _{OH}	High Level Output Voltage (I _{SOURCE} = -0.3mA) T _{AMB} = + 25°C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	1.5 1.5	1.9 -	- -	V
V _{TRIG}	Trigger Voltage T _{AMB} = + 25°C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	0.4 0.3	0.67 -	0.95 1.05	V
I _{TRIG}	Trigger Current	-	10	-	pA
I _{TH}	Threshold Current	-	10	-	pA
V _{RESET}	Reset Voltage T _{AMB} = + 25°C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	0.4 0.3	1.1 -	1.5 2.0	V
I _{RESET}	Reset Current	-	10	-	pA
I _{DIS}	Discharge Pin Leakage Current	-	1	100	nA

STATIC ELECTRICAL CHARACTERISTICS (continued)

V_{CC} = +5V , T_{AMB} = +25°C , Reset to V_{CC}
 (Unless otherwise specified)

Symbol	Parameter	TS555C-TS555I-TS555M			Unit
		Min	Typ	Max	
I _{CC}	Supply Current (no load, High and Low States) T _{AMB} = + 25°C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	- -	110 -	250 250	μA
V _{CL}	Control Voltage T _{AMB} = + 25°C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	2.9 2.8	3.3 -	3.8 3.9	V
V _{DIS}	Discharge Saturation Voltage (I _{DIS} = 10mA) T _{AMB} = + 25°C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	- -	0.2 -	0.3 0.35	V
V _{OL}	Low Level Output Voltage (I _{SINK} = 8mA) T _{AMB} = + 25°C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	- -	0.3 -	0.6 0.8	V
V _{OH}	High Level Output Voltage (I _{SOURCE} = -2mA) T _{AMB} = + 25°C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	4.4 4.4	4.6 -	- -	V
V _{TRIG}	Trigger Voltage T _{AMB} = + 25°C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	1.36 1.26	1.67 -	1.96 2.06	V
I _{TRIG}	Trigger Current	-	10	-	pA
I _{TH}	Threshold Current	-	10	-	pA
V _{RESET}	Reset Voltage T _{AMB} = + 25°C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	0.4 0.3	1.1 -	1.5 2.0	V
I _{RESET}	Reset Current	-	10	-	pA
I _{DIS}	Discharge Pin Leakage Current	-	1	100	nA

STATIC ELECTRICAL CHARACTERISTICS (continued)

$V_{CC} = +12V$, $T_{AMB} = +25^{\circ}C$, Reset to V_{CC}
(Unless otherwise specified)

Symbol	Parameter	TS555C-TS555I-TS555M			UNIT
		Min	Typ	Max	
I_{CC}	Supply Current (no load, High and Low States) $T_{AMB} = +25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	- -	170 -	400 400	μA
V_{CL}	Control Voltage $T_{AMB} = +25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	7.4 7.3	8 -	8.6 8.7	V
V_{DIS}	Discharge Saturation Voltage ($I_{DIS} = 80mA$) $T_{AMB} = +25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	- -	0.9 -	1.6 2.0	V
V_{OL}	Low Level Output Voltage ($I_{SINK} = 50mA$) $T_{AMB} = +25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	- -	1.2 -	2 2.8	V
V_{OH}	High Level Output Voltage ($I_{SOURCE} = -10mA$) $T_{AMB} = +25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	10.5 10.5	11 -	- -	V
V_{TRIG}	Trigger Voltage $T_{AMB} = +25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	3.2 3.1	4 -	4.8 4.9	V
I_{TRIG}	Trigger Current	-	10	-	μA
I_{TH}	Threshold Current	-	10	-	μA
V_{RESET}	Reset Voltage $T_{AMB} = +25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	0.4 0.3	1.1 -	1.5 2.0	V
I_{RESET}	Reset Current	-	10	-	μA
I_{DIS}	Discharge Pin Leakage Current	-	1	100	nA

DYNAMIC ELECTRICAL CHARACTERISTICS

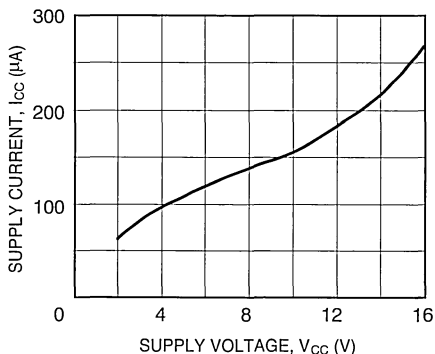
$T_{AMB} = +25^{\circ}\text{C}$, Reset to V_{CC}
(Unless otherwise specified)

Symbol	Parameter	TS555C-TS555I-TS555M			Unit
		Min	Typ	Max	
	Timing Accuracy (Monostable) - $R = 10\text{ k}\Omega$, $C = 0.1\mu\text{F}$ - (Note 1) $V_{CC} = +2\text{V}$ $V_{CC} = +5\text{V}$ $V_{CC} = +12\text{V}$	- - -	1 2 4	- - -	%
	Timing Shift with supply voltage variations (Monostable) $R = 10\text{ k}\Omega$, $C = 0.1\mu\text{F}$, $V_{CC} = +5\text{V} \pm 1\text{V}$		0.38	-	%/V
	Timing Shift with temperature $T_{MIN} \leq T_{AMB} \leq T_{MAX}$, $V_{CC} = +5\text{V}$	-	75	-	ppm/°C
fmax	Maximum astable frequency $R_A = 470\Omega$, $R_B = 200\Omega$, $C = 200\text{ pF}$, $V_{CC} = +5\text{V}$	-	2.7	-	MHz
	Astable frequency accuracy (Note 2) $R_A = R_B = 1\text{ k}\Omega$ to $100\text{ k}\Omega$, $C = 0.1\mu\text{F}$ $V_{CC} = +5\text{V}$ $V_{CC} = +12\text{V}$	- -	3 3	- -	%
	Timing Shift with supply voltage variations (Astable mode) $R_A = R_B = 1\text{ k}\Omega$ to $100\text{ k}\Omega$, $C = 0.1\mu\text{F}$, $V_{CC} = 5$ to $+12\text{V}$	-	0.1	-	%/V
t_r	Output Rise Time ($V_{CC} = +5\text{V}$, $C_{LOAD} = 10\text{ pF}$)	-	25	-	ns
t_f	Output Fall Time ($V_{CC} = +5\text{V}$, $C_{LOAD} = 10\text{ pF}$)	-	20	-	ns
t_{PD}	Trigger Propagation Delay ($V_{CC} = +5\text{V}$)	-	100	-	ns
t_{RPW}	Minimum Reset Pulse Width ($V_{TRIG} = +5\text{V}$)	-	350	-	ns

Notes : 1. See Figure 1
2. See Figure 2

TYPICAL CHARACTERISTICS

Figure 1 : Supply Current (each timer) versus Supply Voltage.



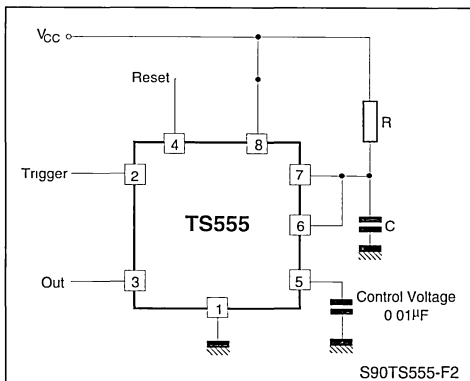
S90TS555-F1

APPLICATION INFORMATION

MONOSTABLE OPERATION

In the monostable mode, the timer functions as a one-shot. Referring to figure 2 the external capacitor is initially held discharged by a transistor inside the timer.

Figure 2.



S90TS555-F2

The circuit triggers on a negative-going input signal when the level reaches 1/3 V_{CC}. Once triggered, the

circuit remains in this state until the set time has elapsed, even if it is triggered again during this interval. The duration of the output HIGH state is given by $t = 1.1 R \times C$.

Notice that since the charge rate and the threshold level of the comparator are both directly proportional to supply voltage, the timing interval is independent of supply. Applying a negative pulse simultaneously to the Reset terminal (pin 4) and the Trigger terminal (pin 2) during the timing cycle discharges the external capacitor and causes the cycle to start over. The timing cycle now starts on the positive edge of the reset pulse. During the time the reset pulse is applied, the output is driven to its LOW state.

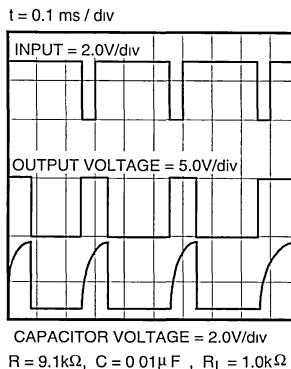
When a negative trigger pulse is applied to pin 2, the flip-flop is set, releasing the short circuit across the external capacitor and driving the output HIGH. The voltage across the capacitor increases exponentially with the time constant $\tau = R \times C$.

When the voltage across the capacitor equals 2/3 V_{CC}, the comparator resets the flip-flop which then discharges the capacitor rapidly and drives the output to its LOW state.

Figure 3 shows the actual waveforms generated in this mode of operation.

When Reset is not used, it should be tied high to avoid any possible or false triggering.

Figure 3.



S90TS555-F3

ASTABLE OPERATION

When the circuit is connected as shown in figure 4 (pin 2 and 6 connected) it triggers itself and free runs as a multivibrator. The external capacitor charges through R_A and R_B and discharges through R_B only. Thus the duty cycle may be precisely set by the ratio of these two resistors.

In the astable mode of operation, C charges and discharges between $1/3 V_{CC}$ and $2/3 V_{CC}$. As in the triggered mode, the charge and discharge times and therefore frequency, are independent of the supply voltage.

Figure 5 shows actual waveforms generated in this mode of operation.

The charge time (output HIGH) is given by :

$$t_1 = 0.693 (R_A + R_B) C$$

and the discharge time (output LOW) by :

$$t_2 = 0.693 (R_B) C$$

Thus the total period T is given by :

$$T = t_1 + t_2 = 0.693 (R_A + 2R_B) C$$

The frequency of oscillation is then :

$$f = \frac{1}{T} = \frac{1.44}{(R_A + 2R_B)C}$$

$$\text{The duty cycle is given by : } D = \frac{R_B}{R_A + 2R_B}$$

Figure 4.

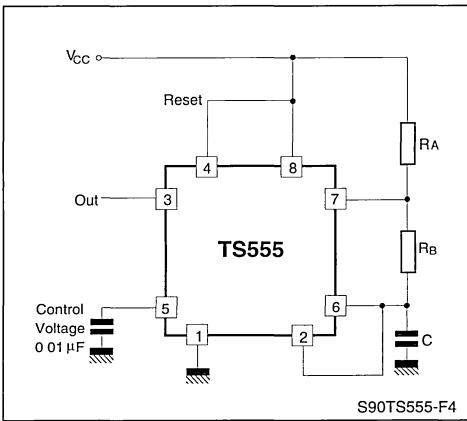
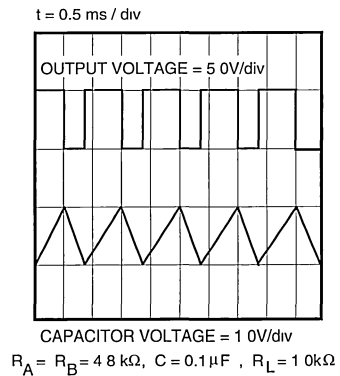


Figure 5.



LOW POWER DUAL CMOS TIMERS

- VERY LOW POWER CONSUMPTION :
100 μ A typ / TIMER AT $V_{CC} = 5V$
- HIGH MAXIMUM ASTABLE FREQUENCY
2.7MHz
- PIN-TO-PIN AND FUNCTIONALLY COMPATIBLE WITH BIPOLAR NE556
- VOLTAGE RANGE : +2V TO +18V
- HIGH OUTPUT CURRENT CAPABILITY
- SUPPLY CURRENT SPIKES REDUCED DURING OUTPUT TRANSITIONS
- HIGH INPUT IMPEDANCE : $10^{12}\Omega$
- OUTPUT COMPATIBLE WITH TTL,CMOS AND LOGIC MOS

DESCRIPTION

The TS556 is a dual CMOS timer which offers very low consumption ($I_{CC(TYP)}$ TS556 = 200 μ A $I_{CC(TYP)}$ NE556 = 6mA) and high frequency ($f_{(MAX)}$ TS556 = 2.7MHz - $f_{(MAX)}$ NE556 = 0.1MHz) Thus, either in Monostable or Astable mode, timing remains very accurate.

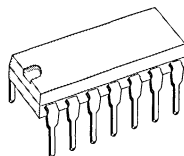
The TS556 provides reduced supply current spikes during output transitions, which enables the use of lower decoupling capacitors compared to those required by bipolar NE556.

Timing capacitors can also be minimized due to high input impedance ($10^{12}\Omega$).

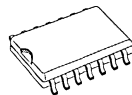
ORDER CODES

Part Number	Temperature Range	Package	
		N	D
TS556C	0 to +70°C	○	○
TS556I	-40 to +105°C	○	○
TS556M	-55 to +125°C	○	○

Examples : TS556CD , TS556IN

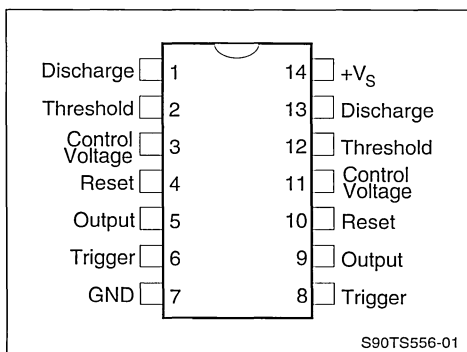


N
DIP14
(Plastic Package)

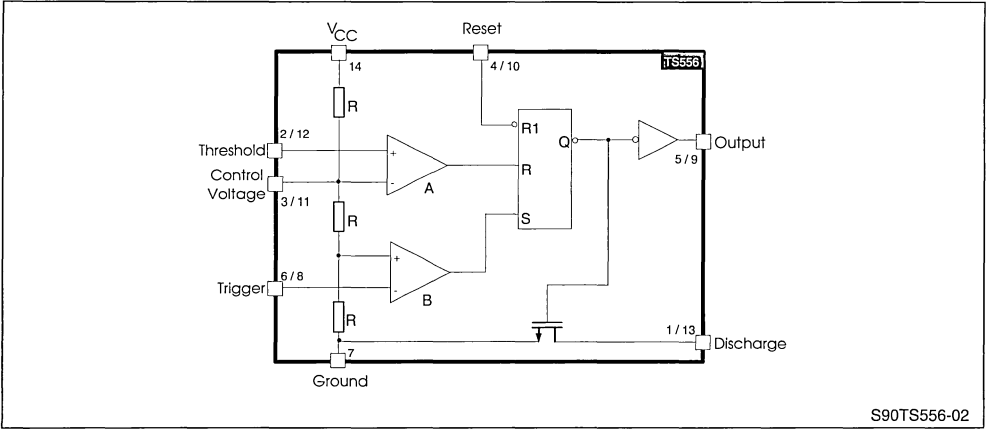


D
SO14
(Plastic Micropackage)

PIN CONNECTION (top view)



BLOCK DIAGRAM (1/2 TS556)



FUNCTION TABLE

RESET	TRIGGER	THRESHOLD	OUTPUT
Low	x	x	Low
High	Low	x	High
High	High	High	Low
High	High	Low	Previous State

- LOW** ↔ Level Voltage ≤ Min voltage specified
- HIGH** ↔ Level Voltage ≥ Max voltage specified
- X** ↔ Irrelevant

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	+18	V
T _J	Junction Temperature	+150	°C

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
T _{OPER}	Operating Temperature Range TS556C TS556I TS556M	0 to +70 -40 to +105 -55 to +125	°C
T _{STG}	Storage Temperature Range	-65 to +150	°C

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	+2 to +16	V

STATIC ELECTRICAL CHARACTERISTICS

V_{CC} = +2V , T_{AMB} = +25°C , Reset to V_{CC}

(Unless otherwise specified)

Symbol	Parameter	TS556C-TS556I-TS556M			Unit
		Min	Typ	Max	
I _{CC}	Supply Current (no load, High and Low States) T _{AMB} = + 25 °C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	- -	130 -	400 400	μ A
V _{CL}	Control Voltage T _{AMB} = + 25 °C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	1.2 1.1	1.3 -	1.4 1.5	V
V _{DIS}	Discharge Saturation Voltage (I _{DIS} = 1mA) T _{AMB} = + 25 °C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	- -	0.05 -	0.2 0.25	V
V _{OL}	Low Level Output Voltage (I _{SINK} = 1mA) T _{AMB} = + 25 °C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	- -	0.1 -	0.3 0.35	V
V _{OH}	High Level Output Voltage (I _{SOURCE} = - 0.3 mA) T _{AMB} = + 25 °C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	1.5 1.5	1.9 -	- -	V
V _{TRIG}	Trigger Voltage T _{AMB} = + 25 °C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	0.4 0.3	0.67 -	0.95 1.05	V
I _{TRIG}	Trigger Current	-	10	-	pA
I _{TH}	Threshold Current	-	10	-	pA
V _{RESET}	Reset Voltage T _{AMB} = + 25 °C T _{MIN} ≤ T _{AMB} ≤ T _{MAX}	0.4 0.3	1.1 -	1.5 2.0	V
I _{RESET}	Reset Current	-	10	-	pA
I _{DIS}	Discharge Pin Leakage Current	-	1	100	nA

STATIC ELECTRICAL CHARACTERISTICS (continued)

$V_{CC} = +5V$, $T_{AMB} = +25^{\circ}C$, Reset to V_{CC}
(Unless otherwise specified)

Symbol	Parameter	TS556C-TS556I-TS556M			Unit
		Min	Typ	Max	
I_{CC}	Supply Current (no load, High and Low States) $T_{AMB} = +25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	- -	220 -	500 500	μA
V_{CL}	Control Voltage $T_{AMB} = +25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	2.9 2.8	3.3 -	3.8 3.9	V
V_{DIS}	Discharge Saturation Voltage ($I_{DIS} = 10mA$) $T_{AMB} = +25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	- -	0.2 -	0.3 0.35	V
V_{OL}	Low Level Output Voltage ($I_{SINK} = 8mA$) $T_{AMB} = +25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	- -	0.3 -	0.6 0.8	V
V_{OH}	High Level Output Voltage ($I_{SOURCE} = -2mA$) $T_{AMB} = +25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	4.4 4.4	4.6 -	- -	V
V_{TRIG}	Trigger Voltage $T_{AMB} = +25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	1.36 1.26	1.67 -	1.96 2.06	V
I_{TRIG}	Trigger Current	-	10	-	μA
I_{TH}	Threshold Current	-	10	-	μA
V_{RESET}	Reset Voltage $T_{AMB} = +25^{\circ}C$ $T_{MIN} \leq T_{AMB} \leq T_{MAX}$	0.4 0.3	1.1 -	1.5 2.0	V
I_{RESET}	Reset Current	-	10	-	μA
I_{DIS}	Discharge Pin Leakage Current	-	1	100	nA

STATIC ELECTRICAL CHARACTERISTICS (continued)

$V_{CC} = +12V$, $T_{AMB} = +25^{\circ}C$, Reset to V_{CC}
(Unless otherwise specified)

Symbol	Parameter	TS556C - TS556I - TS556M			Unit
		Min	Typ	Max	
I_{CC}	Supply Current (no load, High and Low States) $T_{AMB} = +25^{\circ}C$ $T_{MIN} T_{AMB} T_{MAX}$	- -	340 -	800 800	μA
V_{CL}	Control Voltage $T_{AMB} = +25^{\circ}C$ $T_{MIN} T_{AMB} T_{MAX}$	7.4 7.3	8 -	8.6 8.7	V
V_{DIS}	Discharge Saturation Voltage ($I_{DIS} = 80mA$) $T_{AMB} = +25^{\circ}C$ $T_{MIN} T_{AMB} T_{MAX}$	- -	0.9 -	1.6 2.0	V
V_{OL}	Low Level Output Voltage ($I_{SINK} = 50mA$) $T_{AMB} = +25^{\circ}C$ $T_{MIN} T_{AMB} T_{MAX}$	- -	1.2 -	2 2.8	V
V_{OH}	High Level Output Voltage ($I_{SOURCE} = -10mA$) $T_{AMB} = +25^{\circ}C$ $T_{MIN} T_{AMB} T_{MAX}$	10.5 10.5	11 -	- -	V
V_{TRIG}	Trigger Voltage $T_{AMB} = +25^{\circ}C$ $T_{MIN} T_{AMB} T_{MAX}$	3.2 3.1	4 -	4.8 4.9	V
I_{TRIG}	Trigger Current	-	10	-	μA
I_{TH}	Threshold Current	-	10	-	μA
V_{RESET}	Reset Voltage $T_{AMB} = +25^{\circ}C$ $T_{MIN} T_{AMB} T_{MAX}$	0.4 0.3	1.1 -	1.5 2.0	V
I_{RESET}	Reset Current	-	10	-	μA
I_{DIS}	Discharge Pin Leakage Current	-	1	100	nA

DYNAMIC ELECTRICAL CHARACTERISTICS

T_{AMB} = +25°C , Reset to V_{CC}

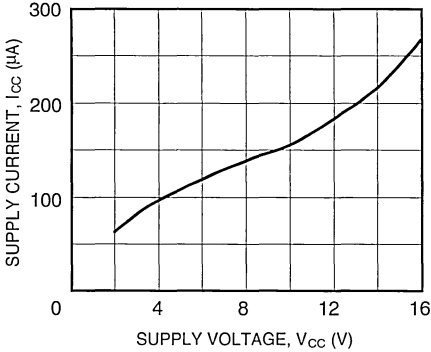
(Unless otherwise specified)

Symbol	Parameter	TS556C-TS556I-TS556M			Unit
		Min	Typ	Max	
	Timing Accuracy (Monostable) - R = 10 kΩ , C = 0.1 μF - (Note 1) V _{CC} = +2V V _{CC} = +5V V _{CC} = +12V	- - -	1 2 4	- - -	%
	Timing Shift with supply voltage variations (Monostable) R = 10 kΩ , C = 0.1μF, V _{CC} = +5V +/-1V	-	0.38	-	%/V
	Timing Shift with temperature T _{MIN} ≤ T _{AMB} ≤ T _{MAX} , V _{CC} = +5V	-	75	-	ppm/°C
f _{max}	Maximum astable frequency R _A = 470Ω , R _B = 200Ω, C = 200 pF , V _{CC} = +5V	-	2.7	-	MHz
	Astable frequency accuracy - (Note 2) R _A = R _B = 1kΩ to 100kΩ, C = 0.1μF V _{CC} = +5V V _{CC} = +12V	- -	3 3	- -	%
	Timing Shift with supply voltage variations (Astable mode) R _A = R _B = 1kΩ to 100kΩ, C = 0.1μF, V _{CC} = +5 to +12V	-	0.1	-	%/V
t _r	Output Rise Time (V _{CC} = +5V, C _{LOAD} = 10pF)	-	25	-	ns
t _f	Output Fall Time (V _{CC} = +5V, C _{LOAD} = 10pF)	-	20	-	ns
t _{PD}	Trigger Propagation Delay (V _{CC} = +5V)	-	100	-	ns
t _{RPW}	Minimum Reset Pulse Width (V _{TRIG} = +5V)	-	350	-	ns

- Notes : 1. See Figure 1
2. See Figure 2

TYPICAL CHARACTERISTICS

Figure 1 : Supply Current (each timer) versus Supply Voltage.



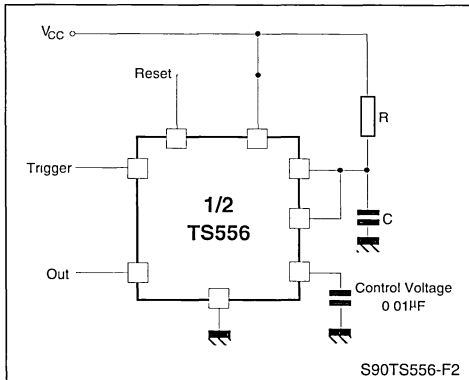
S90TS556-F1

APPLICATION INFORMATION

MONOSTABLE OPERATION

In the monostable mode, the timer functions as a one-shot. Referring to figure 2 the external capacitor is initially held discharged by a transistor inside the timer.

Figure 2.



S90TS556-F2

The circuit triggers on a negative-going input signal when the level reaches 1/3 V_{CC}. Once triggered, the

circuit remains in this state until the set time has elapsed, even if it is triggered again during this interval. The duration of the output HIGH state is given by $t = 1.1 R \times C$.

Notice that since the charge rate and the threshold level of the comparator are both directly proportional to supply voltage, the timing interval is independent of supply. Applying a negative pulse simultaneously to the Reset terminal (pin 4 or 10) and the Trigger terminal (pin 6 or 8) during the timing cycle discharges the external capacitor and causes the cycle to start over. The timing cycle now starts on the positive edge of the reset pulse. During the time the reset pulse is applied, the output is driven to its LOW state.

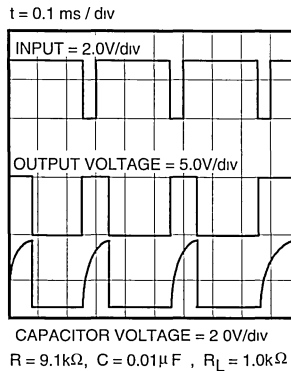
When a negative trigger pulse is applied to the trigger terminal, the flip-flop is set, releasing the short circuit across the external capacitor and driving the output HIGH. The voltage across the capacitor increases exponentially with the time constant $\tau = R \times C$.

When the voltage across the capacitor equals 2/3 V_{CC}, the comparator resets the flip-flop which then discharges the capacitor rapidly and drives the output to its LOW state.

Figure 3 shows the actual waveforms generated in this mode of operation.

When Reset is not used, it should be tied high to avoid any possible or false triggering.

Figure 3.



S90TS556-F3

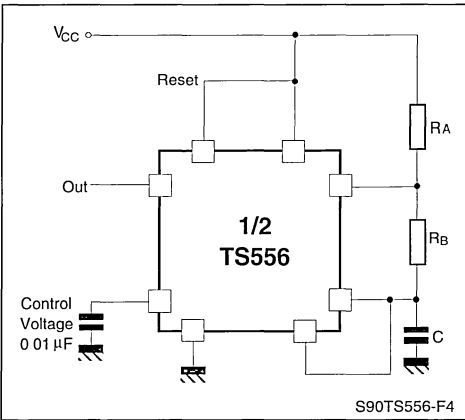
ASTABLE OPERATION

When the circuit is connected as shown in figure 4, it triggers itself and free runs as a multivibrator. The external capacitor charges through R_A and R_B and discharges through R_B only. Thus the duty cycle may be precisely set by the ratio of these two resistors.

In the astable mode of operation, C charges and discharges between $1/3 V_{CC}$ and $2/3 V_{CC}$. As in the triggered mode, the charge and discharge times and therefore frequency, are independent of the supply voltage.

Figure 5 shows actual waveforms generated in this mode of operation.

Figure 4.



The charge time (output HIGH) is given by :

$$t_1 = 0.693 (R_A + R_B) C$$

and the discharge time (output LOW) by :

$$t_2 = 0.693 (R_B) C$$

Thus the total period T is given by :

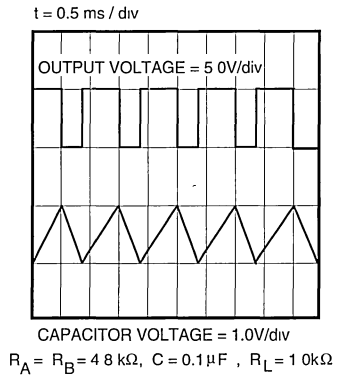
$$T = t_1 + t_2 = 0.693 (R_A + 2R_B) C$$

The frequency of oscillation is then :

$$f = \frac{1}{T} = \frac{1.44}{(R_A + 2R_B)C}$$

The duty cycle is given by : $D = \frac{R_B}{R_A + 2R_B}$

Figure 5.



S90TS556-F5

RELIABILITY REPORT

RELIABILITY REPORT

1. RELIABILITY TEST DESCRIPTION

1.A - ELECTRICAL TESTS (Die oriented tests)

Static life test :

This test was performed to point out die problems connected to the superficial contamination and to the layout structure.

Test conditions :

- $V_{CC} = +10\text{ V}$
- $T_{AMB} = 125^{\circ}\text{C}$
- Package = plastic DIL or SO (see Fig1 page 145)

1.B - ENVIRONMENTAL TESTS (Package oriented tests)

To evaluate the moisture resistance and thermomechanical behaviour, we have performed a reliability characterization including the following tests:

- Thermal Humidity with Bias (T.H.B.)
- Pressure Cooker Test (PRESSURE POT)
- Temperature Cycling -65 +150 °C

PERIOD: Year 90

Results are given for all standard linear products

2. ELECTRICAL RELIABILITY TEST RESULTS

TEST CONDITIONS	TIME	SAMPLE SIZE	REJECTS
LIFE TEST : $V_{CC} = +10\text{ V}$ $T_{AMB} = 125^{\circ}\text{C}$	168H	830	0
	1000H	580	0
	2000H	360	0

3. ENVIRONMENTAL RELIABILITY TEST RESULTS

BIASED MOISTURE LIFE TEST

TEST CONDITIONS	TIME	SAMPLE SIZE	REJECTS
PLASTIC DIL 85°C 85% R.H.	1000H	330	0
SO PACKAGE 85°C 85% R.H.	1000H	450	0

TEST	TEST CONDITIONS	SAMPLE SIZE	FAILURE	NOTE
PRESSURE POT	$T_{AMB} = 121^{\circ}\text{C}$ $P = 2,08\text{ ATM}$ $T = 168\text{ H}$	5852	0	1
		4249	0	2
TEMPERATURE CYCLING	1000 cycles ($T_{AMB} = -65^{\circ}\text{C}$ to $+150^{\circ}\text{C}$) 10 min. at extreme temperatures, 5 min. max. transfer time.	550	0	1
		1148	0	2

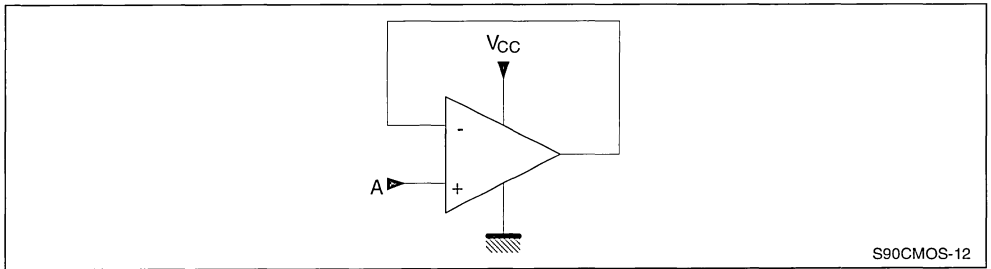
Notes : 1. Plastic DIL Package
2. SO Package

4. FAILURE RATE CALCULATION AT :

- $T_J \text{ max} = 125^\circ\text{C}$ (observed value and at 60% CL)
 $\lambda = 0.9 \times 10^{-6} \text{F/H}$
- $T_J = 55^\circ\text{C}$ (at 60 % CL) and $EA = 0.7 \text{ eV}$
 $\lambda = 6.5 \text{ FITS}$

5. CIRCUIT CONFIGURATION FOR RELIABILITY TESTS

Figure 1 : HTB and THB Life Test
 For 50% "A" Connected to V_{CC}
 For 50% "A" Connected to $0V$
 $V_{CC} = +10V$



When a low number of samples has been employed (as during homologation tests) and when a proper confidence level is required in order to estimate a correct λ value we suggest accepting a value C' obtained by table 2 instead of $C = \text{number of failures employed in previous formula (1)}$.

The new value for λ will be :

$$\lambda = \frac{C' \text{ (extracted by table 2)}}{N \times T}$$

Table 2.

NUMBER OF FAILURES	CONFIDENCE LEVEL					
	50%	60%	70%	80%	90%	95%
0	0.693	0.916	1.20	1.66	2.305	2.99
1	1.678	2.022	2.439	2.99	3.89	4.74
2	2.674	3.12	3.615	4.28	5.30	6.30
3	3.672	4.16	4.762	5.50	6.70	7.75
4	4.671	5.25	5.891	6.70	8.00	9.15
5	5.67	6.30	7.005	7.90	9.25	10.50
6	6.669	7.35	8.111	9.10	10.55	11.85
7	7.669	8.40	9.209	10.25	11.75	13.15
8	8.669	9.45	10.30	11.40	13.00	14.45
9	9.668	10.50	11.38	12.50	14.20	15.70
10	10.66	11.55	12.47	13.65	15.40	16.95

APPENDIX : FAILURE RATE CALCULATION

Reliability evaluation of a device means also failure rate (λ) evaluation, both during infant mortality and useful life.

The reliability test used for failure rate evaluation is H.T.R.B.

In its simple form the failure rate is:

$$\lambda = \frac{C}{N \times T}$$

Where :

λ = Failure rate (at a given temperature)

C = Number of failures

N = Number of tested devices

T = Number of test hours

To determine failure rate at other temperature an acceleration factor F must be used.

F is determined, for a given thermal activation energy EA, by the Arrhenius relationship as :

$$F(T_1, T_2) = \text{EXP} \left[-\frac{EA}{K} \left(\frac{1}{T_1} - \frac{1}{T_2} \right) \right]$$

Where :

EA = Thermal activation energy (eV)

K = Boltzmann's constant (8.63×10^{-5} eV/°K)

T = Absolute temperature in °K

Then

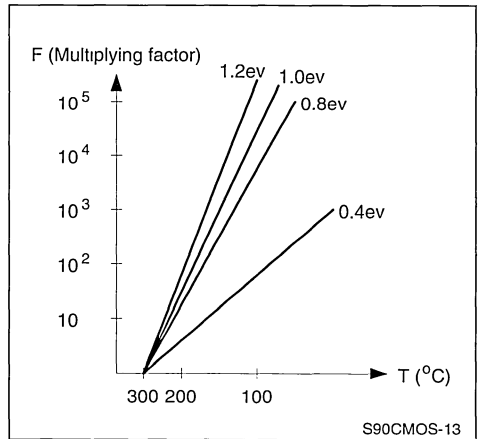
$$\lambda(T_1) = F(T_1, T_2) \times \lambda(T_2)$$

Where :

$T_1 < T_2$

Fig. 2 shows temperature derating curves and multiplying factors for temperature reduction. The various lines correspond to the activation energies associated with the different failure mechanisms involved.

Figure 2 : Arrhenius plot.



TAPE AND REEL SPECIFICATION

TAPE AND REEL PACKING SPECIFICATION FOR SOIC

1 - PURPOSE :

This specification is formulated to provide dimensions, tolerances and characteristics about tape and reel necessary to surface mount components such that they may be automatically placed. This specification covers taping for active surface mount components in SOIC package type.

2 - REFERENCE DOCUMENTS

- 2 - 1 . "EIA 481-A"
- 2 - 2 . "IEC 286-3"
- 2 - 3 . "Special customer request"

3 - GENERAL

- 3 - 1 . Reel material = Plastic antistatic or conductive
- 3 - 2 . Cavity tape material = Black conductive (less than $10^5 \Omega$ per square)
- 3 - 3 . Cover tape material = Transparent antistatic (less than $10^{10} \Omega$ per square) or conductive (less than $10^5 \Omega$ per square)

4 - QUANTITY AND DIMENSIONS

All drawings dimensions are in millimeters.

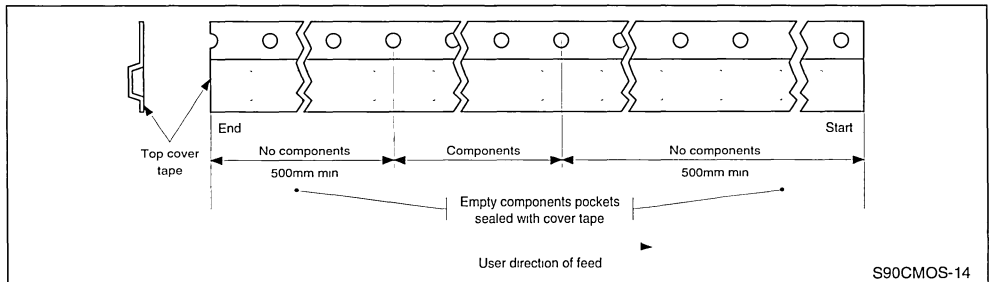
- 4 - 1 . QUANTITY AND DIMENSIONS - See table 1

Table 1.

PACKAGE	TAPE WIDTH (mm)	QTY / REEL
SO8	12	2500
SO14	16	2500
SO16 (narrow)	16	2500

4 - 2 . LEADER AND TRAINER

Figure 1.

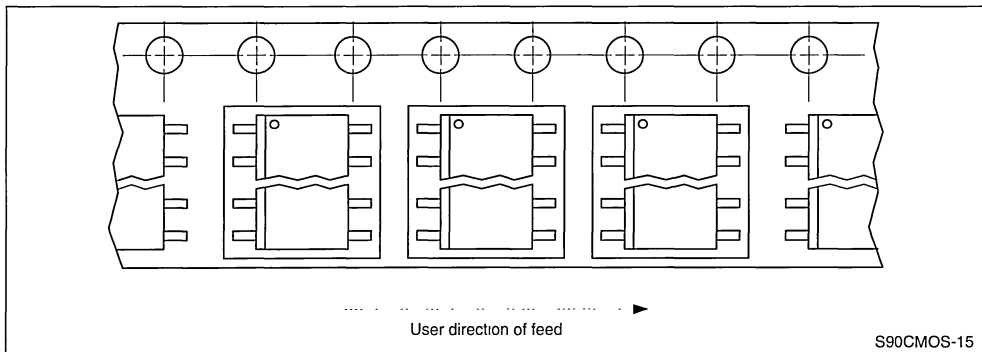


TAPE AND REEL SPECIFICATION

The trailer end of the tape carrier is secured to the reel.
The devices are oriented with the terminals facing to the bottom of the carrier pocket.

4 - 3 . DEVICES ORIENTATION

Figure 2.



The devices are oriented in the carrier pocket with pin number 1 adjacent to the sprocket holes.

4 - 4 .OVERALL REEL DIMENSIONS

Figure 3.

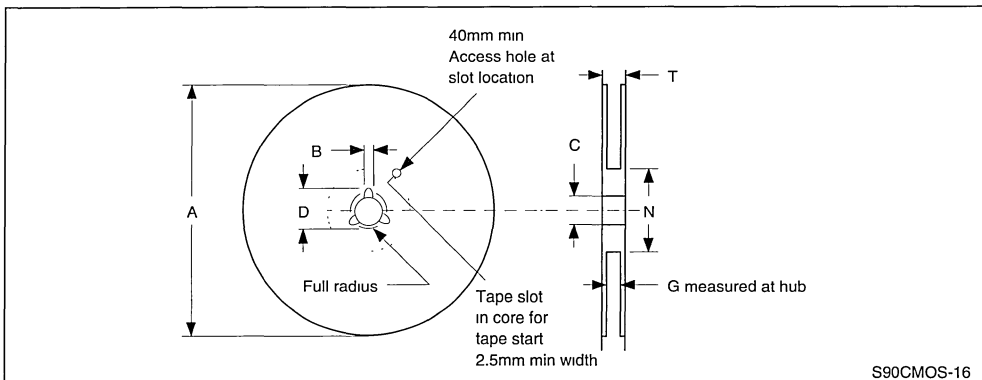
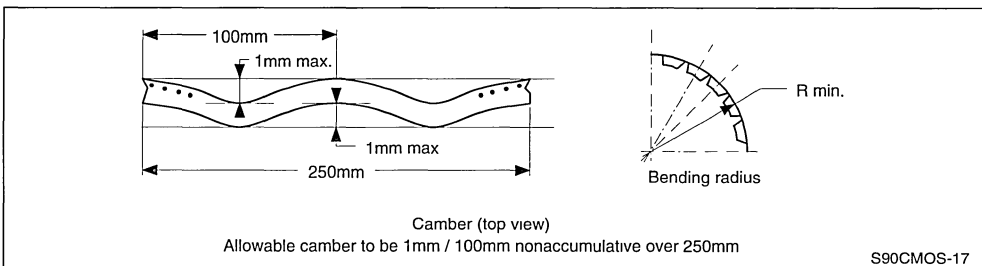


Figure 4.



4 - 4 .OVERALL REEL DIMENSIONS (continued)

Table 2.

Tape Size	A max	B min	C	D min	N min	G	T max	R min
12 mm	330	1.5	13 ± 0.2	20.2	50	12.4 +2/-0	18.4	30
16 mm	330	1.5	13 ± 0.2	20.2	50	12.4 +2/-0	22.4	40

4 - 5 . CARRIER POCKET DIMENSIONS

Figure 5.

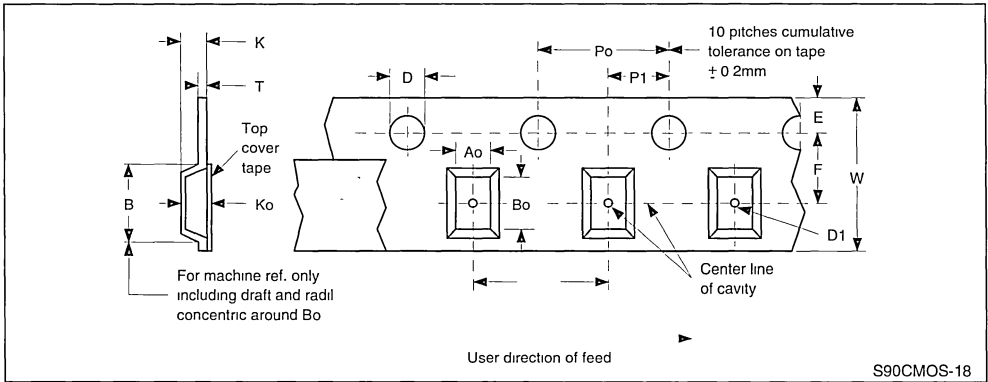


Table 3.

Tape Size	D	E	P _O	T	A _O	B _O	K _O
12 / 16mm	1.5 +0.1/0	1.75 ± 0.1	4 ± 0.1	0.4	See note		

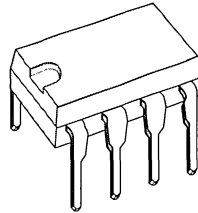
Table 4.

Tape Size	B ₁ max	D ₁ min	F	K max	P ₁	W
12mm	8.2	1.5	5.5 ± 0.05	4.5	2 ± 0.05	12 ± 0.3
16mm	12.1	1.5	7.5 ± 0.1	6.5	2 ± 0.1	16 ± 0.3

Note A_o, B_o and K_o are determined by components size. The clearance between the component and the carrier pocket is :
 a - 0.05 mm minimum to 0.65 mm maximum for 12 mm tape
 b - 0.05 mm minimum to 0.90 mm maximum for 16 mm tape

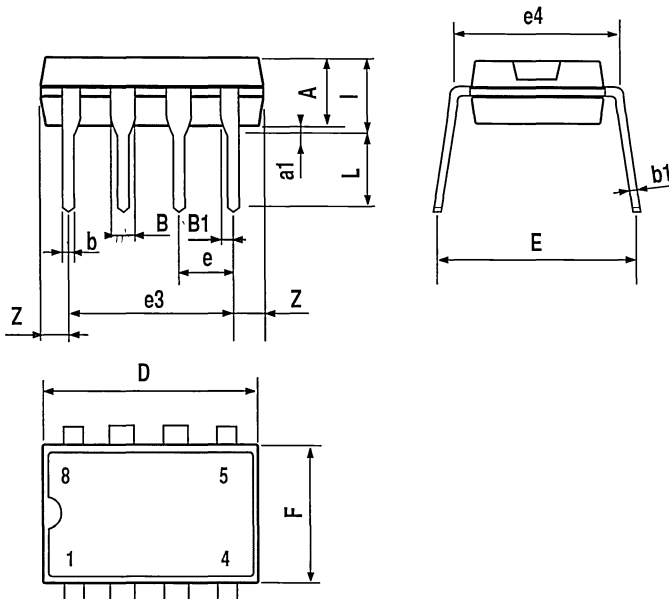
PACKAGES

OUTLINE AND MECHANICAL DATA



Plastic DIP8

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A		3.32			0.131	
a1	0.51			0.020		
B	1.15		1.65	0.045		0.065
b	0.356		0.55	0.014		0.022
b1	0.204		0.304	0.008		0.012
D			10.92			0.430
E	7.95		9.75	0.313		0.384
e		2.54			0.100	
e3		7.62			0.300	
e4		7.62			0.300	
F			6.6			0.260
I			5.08			0.200
L	3.18		3.81	0.125		0.150
Z			1.52			0.060

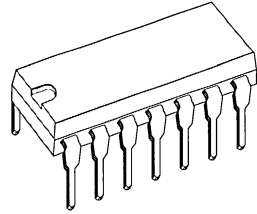


P001W



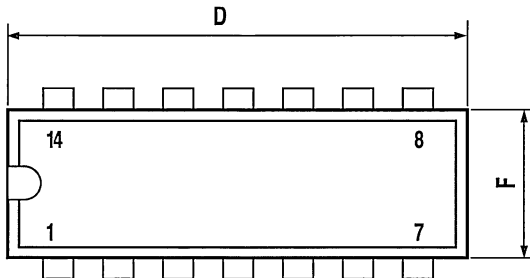
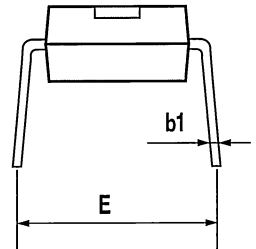
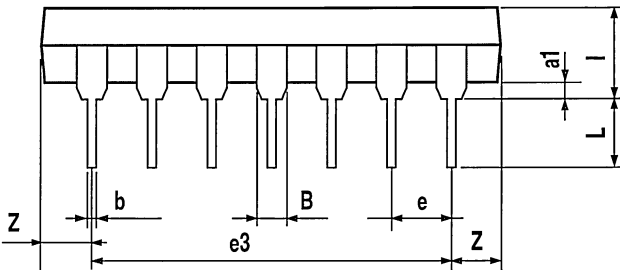
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OUTLINE AND MECHANICAL DATA



Plastic PDIP14

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
l			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100

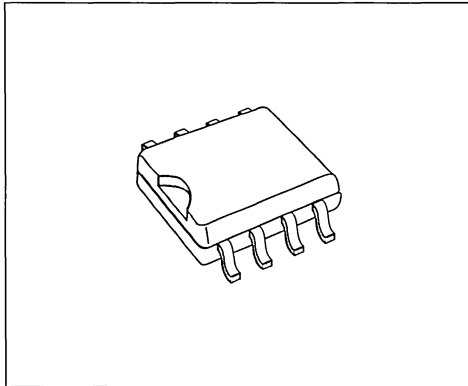


P001A

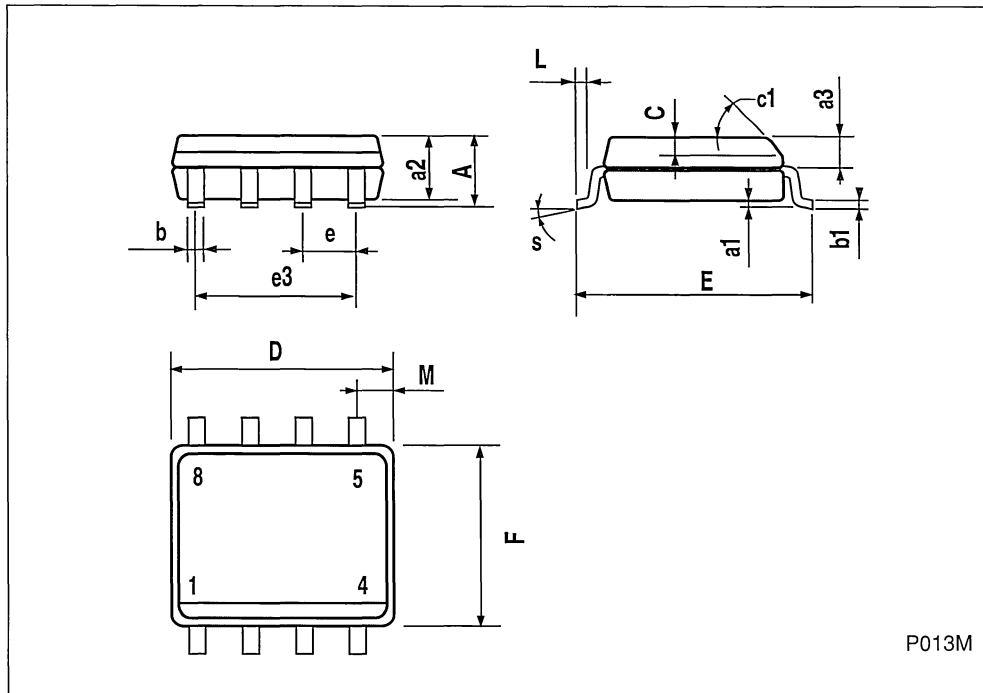
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45° (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8° (max.)					



OUTLINE AND MECHANICAL DATA

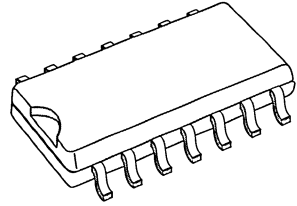


SO8



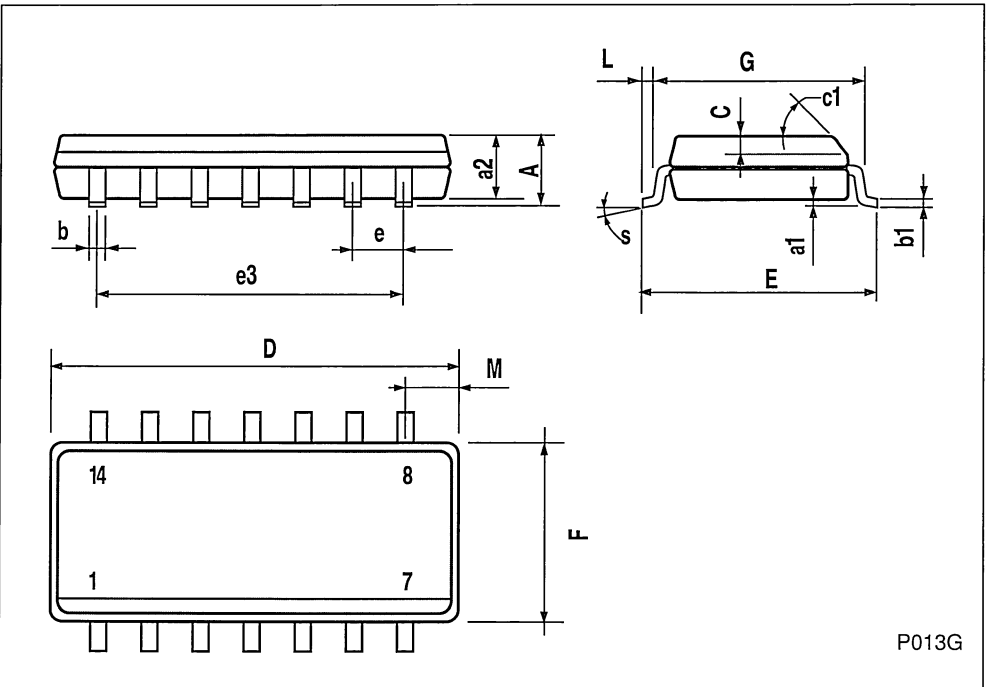
P013M

OUTLINE AND MECHANICAL DATA



SO14

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



P013G

EUROPE

DENMARK

2730 HERLEV

Herlev Torv, 4
Tel (45-42) 94 85 33
Telex 35411
Telefax (45-42) 948694

FINLAND

LOHJA SF-08150

Karjalankatu, 2
Tel (358-12) 155 11
Telefax (358-12) 155 66

FRANCE

94253 GENTILLY Cedex

7 - avenue Gallieni - BP 93
Tel (33-1) 47 40 75 75
Telex 632570 STMHQ
Telefax (33-1) 47 40 79 10

67000 STRASBOURG

20, Place des Halles
Tel (33) 88 75 50 66
Telefax (33) 88 22 29 32

GERMANY

6000 FRANKFURT

Gutleutstrasse 322
Tel (49-69) 237492-3
Telex 176997 689
Telefax (49-69) 231957
Teletex 6997689-STVBP

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Neukeferloh Technopark
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Telex 528211
Telefax (49-89) 4605454
Teletex 897107=STDISTR

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Telex 175118418
Telefax 5118418 CSFBEH
Telefax (49-511) 6151243

5202 HENNEF

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Telefax (49-2242) 84181

8500 NÜRNBERG 20

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Tel (49-911) 59893-0
Telex 626243
Telefax (49-911) 5980701

7000 STUTTGART 31

Mittlerer Pfad 2-4
Tel (49-711) 13968-0
Telex 721718
Telefax (49-711) 8661427

ITALY

20090 ASSAGO (MI)

V.le Milanofiori - Strada 4 - Palazzo A/4/A
Tel (39-2) 89213 1 (10 linee)
Telex 330131 - 330141 SGSAGR
Telefax (39-2) 8250449

40033 CASALECCHIO DI RENO (BO)

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Telex 512442
Telefax (39-51) 591305

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Via A. Torlonia, 15
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Telex 620653 SGSATE I
Telefax (39-6) 8444474

NETHERLANDS

5652 AR EINDHOVEN

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Telex: 51186
Telefax (31-40) 528835

SPAIN

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Tel (34-3) 4143300-4143361
Telefax (34-3) 2021461

28027 MADRID

Calle Albacete, 5
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Telex 46033 TCCEE
Telefax (34-1) 4031134

SWEDEN

S-16421 KISTA

Borgarfjordsgatan, 13 - Box 1094
Tel (46-8) 7939220
Telex 12078 THSWS
Telefax (46-8) 7504950

SWITZERLAND

1218 GRAND-SACONNEX (GENEVA)

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Telex 415493 STM CH
Telefax (41-22) 7984869

UNITED KINGDOM and EIRE

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Planar House, Parkway
Globe Park
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Telex 847458
Telefax (44-628) 890391

AMERICAS**BRAZIL****05413 SÃO PAULO**

R Henrique Schaumann 286-CJ33
Tel (55-11) 883-5455
Telex (391)11-37988 "UMBR BR"
Telefax (55-11) 282-2367

U.S.A.

NORTH & SOUTH AMERICAN
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FOR RF AND MICROWAVE
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OFFICE IN THE U.S.A

PENNSYLVANIA

Montgomeryville - (215) 361-6400

ASIA / PACIFIC**AUSTRALIA****NSW 2027 EDGECLIFF**

Suite 211, Edgecliff centre
203-233, New South Head Road
Tel (61-2) 327 39 22
Telex 071 126911 TCAUS
Telefax (61-2) 327 61 76

HONG KONG**WANCHAI**

22nd Floor - Hopewell centre
183 Queen's Road East
Tel (852-5) 8615788
Telex 60955 ESGIES HX
Telefax (852-5) 8656589

INDIA**NEW DELHI 110001**

Liaison Office
62, Upper Ground Floor
World Trade Centre
Barakhamba Lane
Tel (91-11) 3715191
Telex 031-66816 STMI IN
Telefax (91-11) 3715192

MALAYSIA**PULAU PINANG 10400**

4th Floor - Suite 4-03
Bangunan FOP-123D Jalan Anson
Tel (04) 379735
Telefax (04) 379816

KOREA**SEOUL 121**

8th floor Shinwon Building
823-14, Yuksam-Dong
Kang-Nam-Gu
Tel (82-2) 553-0399
Telex SGSKOR K29998
Telefax (82-2) 552-1051

SINGAPORE**SINGAPORE 2056**

28 Ang Mo Kio - Industrial Park 2
Tel (65) 4821411
Telex RS 55201 ESGIES
Telefax (65) 4820240

TAIWAN**TAIPEI**

12th Floor
325, Section 1 Tun Hua South Road
Tel (886-2) 755-4111
Telex 10310 ESGIE TW
Telefax (886-2) 755-4008

JAPAN**TOKYO 108**

Nisseki - Takanawa Bld 4F
2-18-10 Takanawa
Minato-Ku
Tel (81-3) 3280-4121
Telefax (81-3) 3280-4131

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